Computer Architecture

Lecture 10b: Memory Latency

Prof. Onur Mutlu
ETH Zürich

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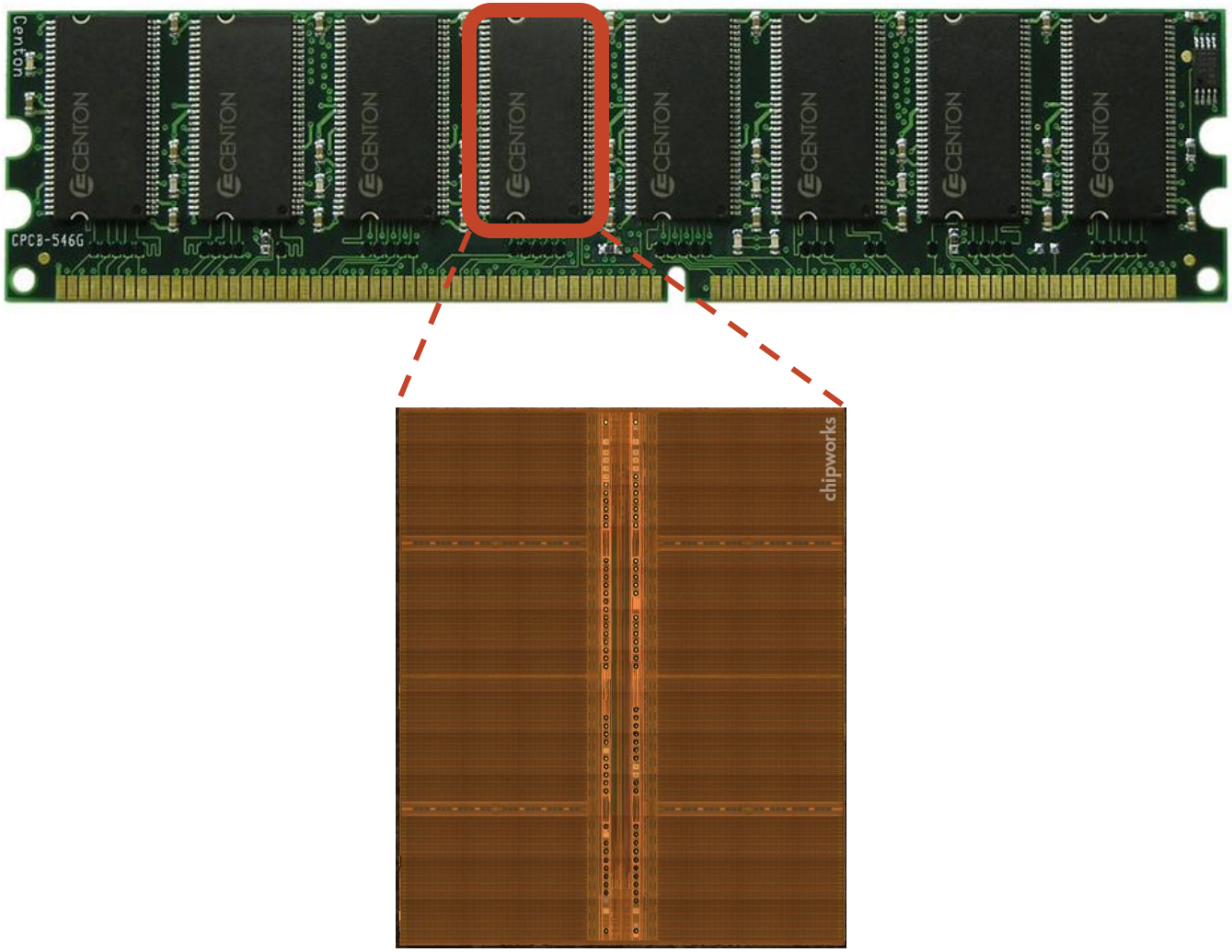
DRAM Memory: A Low-Level Perspective

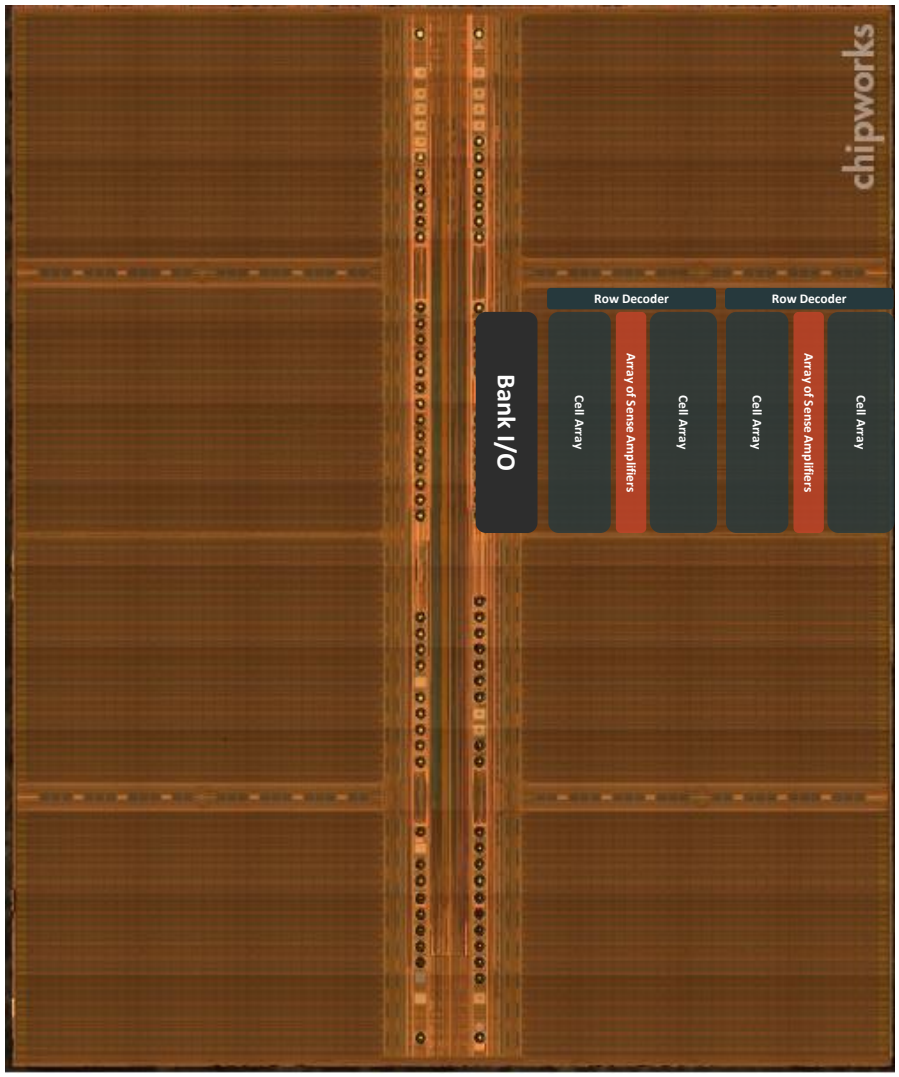
DRAM Module and Chip



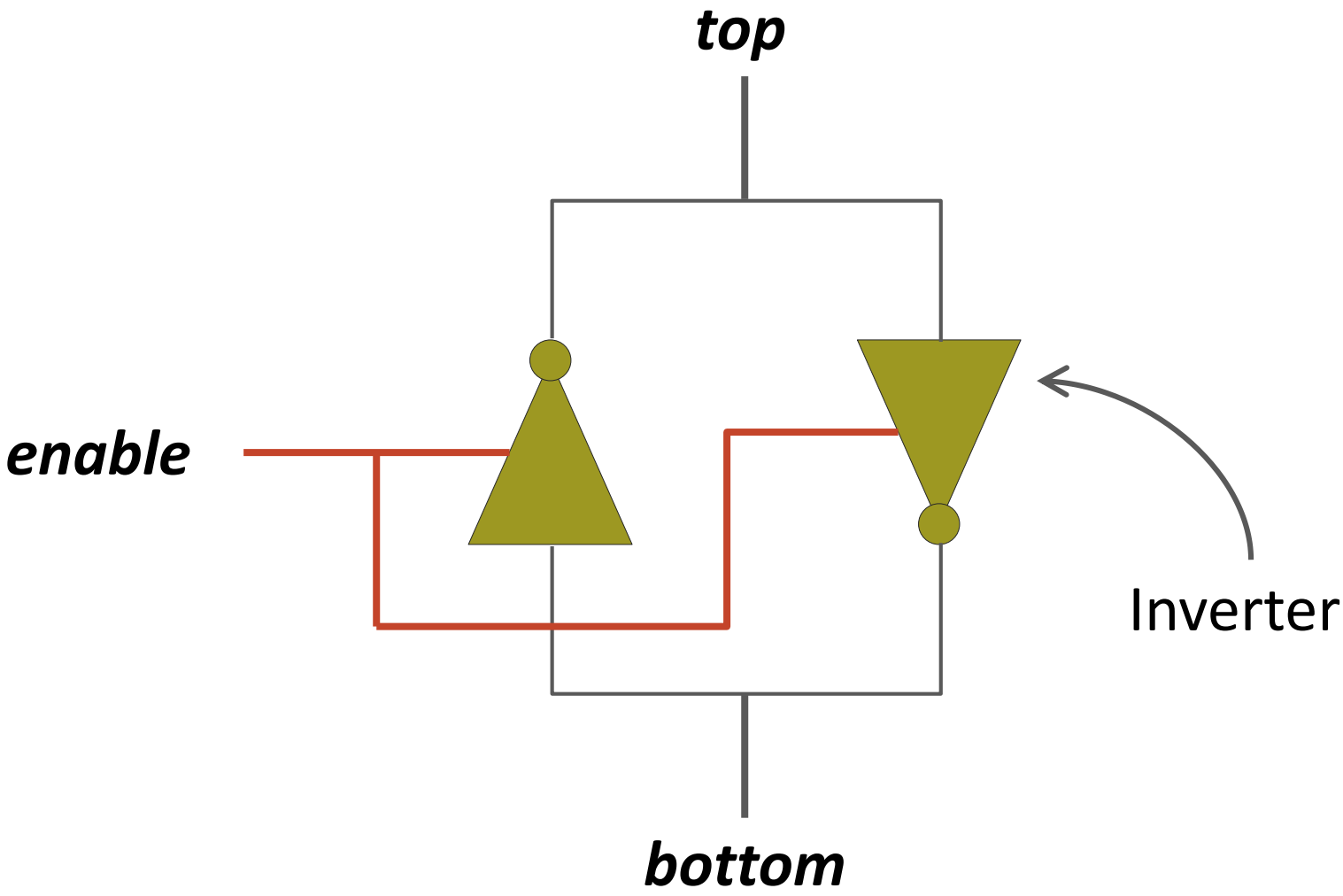
Goals

- Cost
- Latency
- Bandwidth
- Parallelism
- Power
- Energy
- Reliability
- …

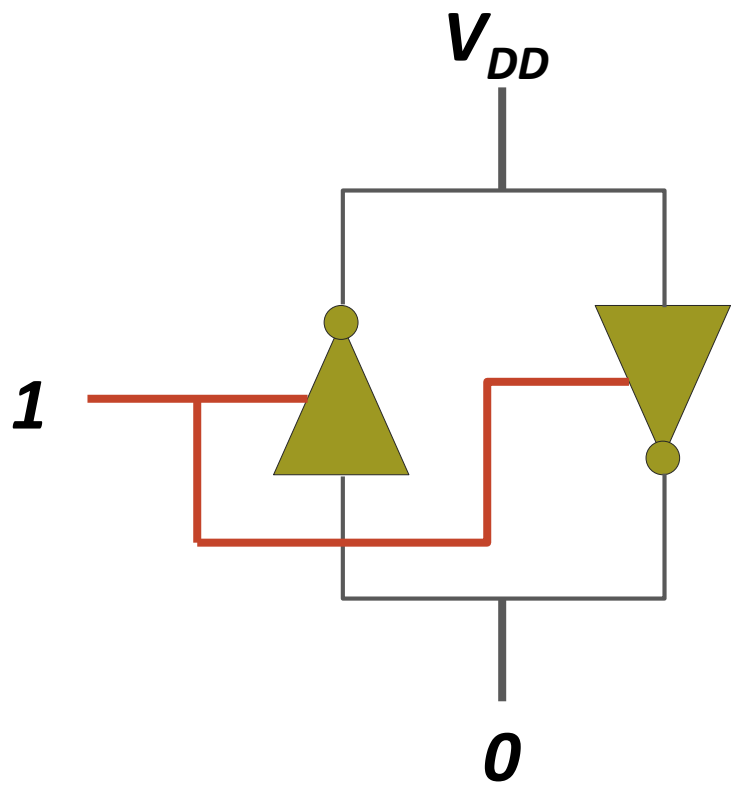
DRAM Chip


chipworks
Row Decoder
Row Decoder
Bank I/O
Cell Array
Array of Sense Amplifiers
Cell Array
Cell Array
Array of Sense Amplifiers
Cell Array

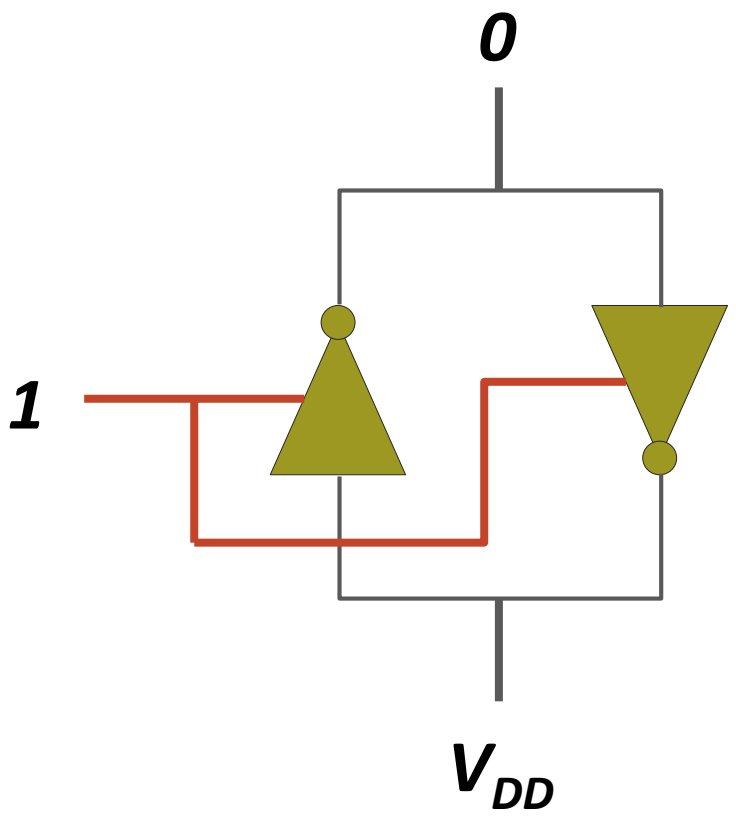
Sense Amplifier



Sense Amplifier – Two Stable States

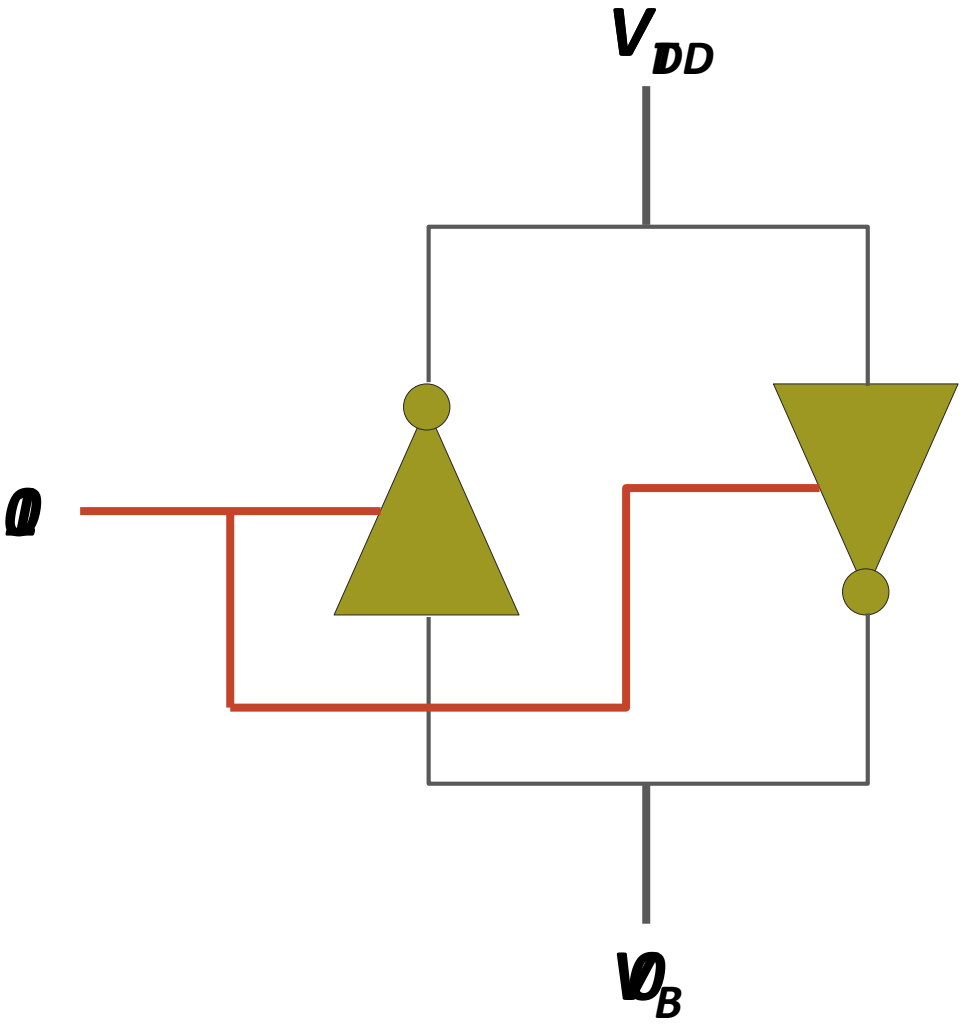


Logical “1”



Logical “0”

Sense Amplifier Operation

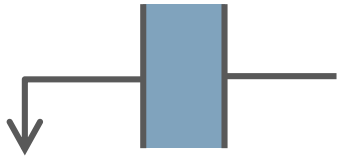


$V_T > V_B$

DRAM Cell – Capacitor

Empty State

Logical “0”

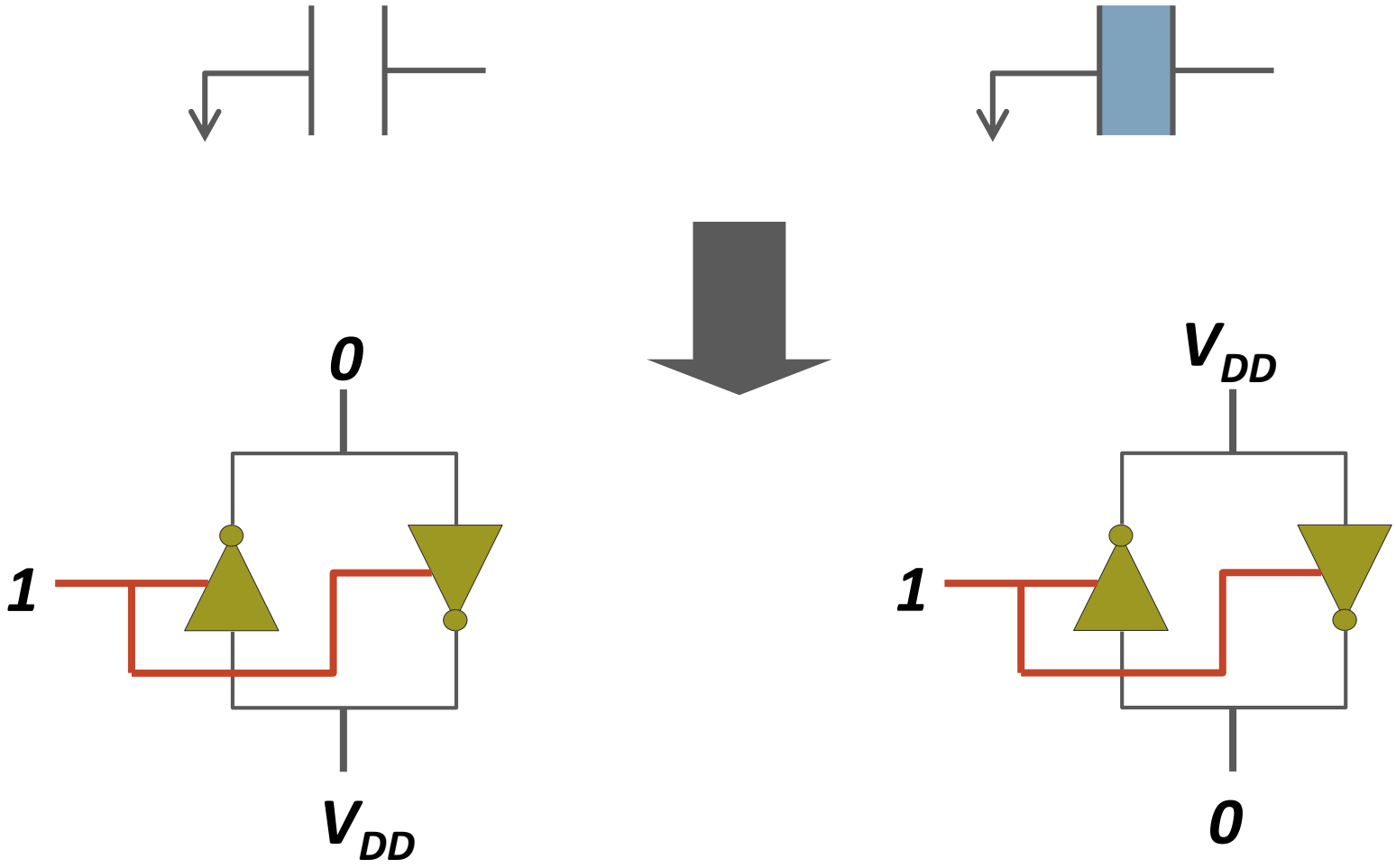


Fully Charged State

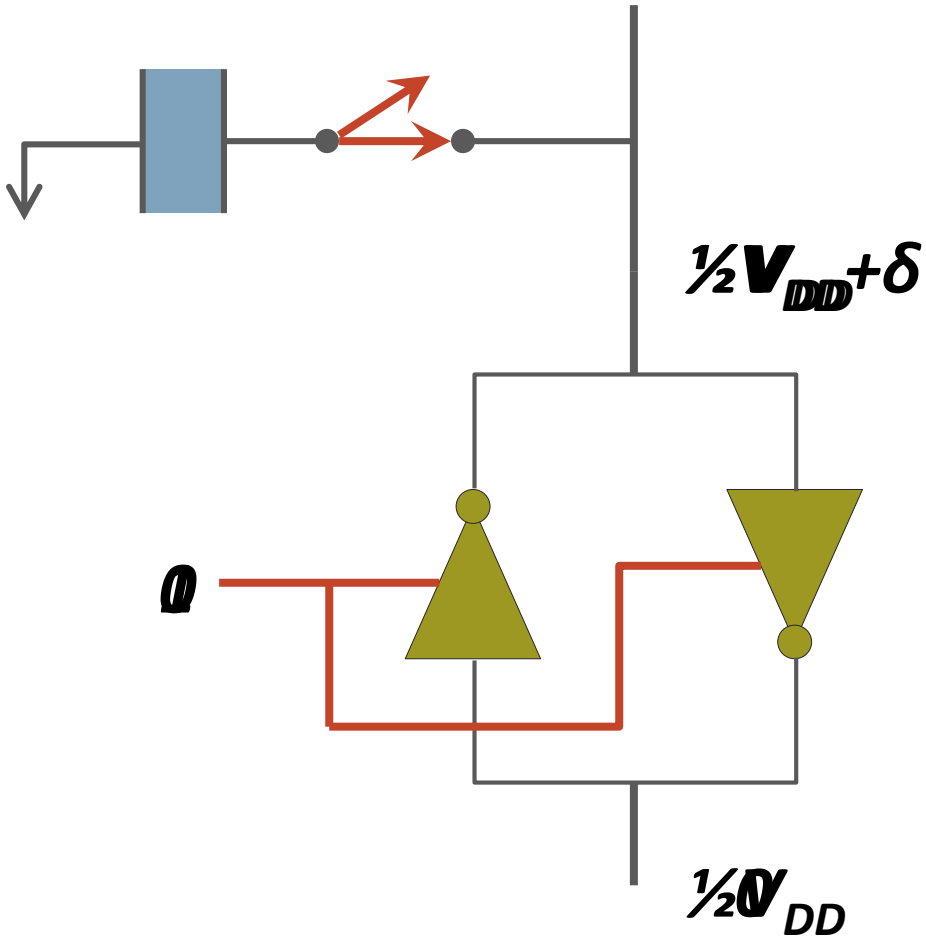
Logical “1”

1. Small – Cannot drive circuits
2. Reading destroys the state

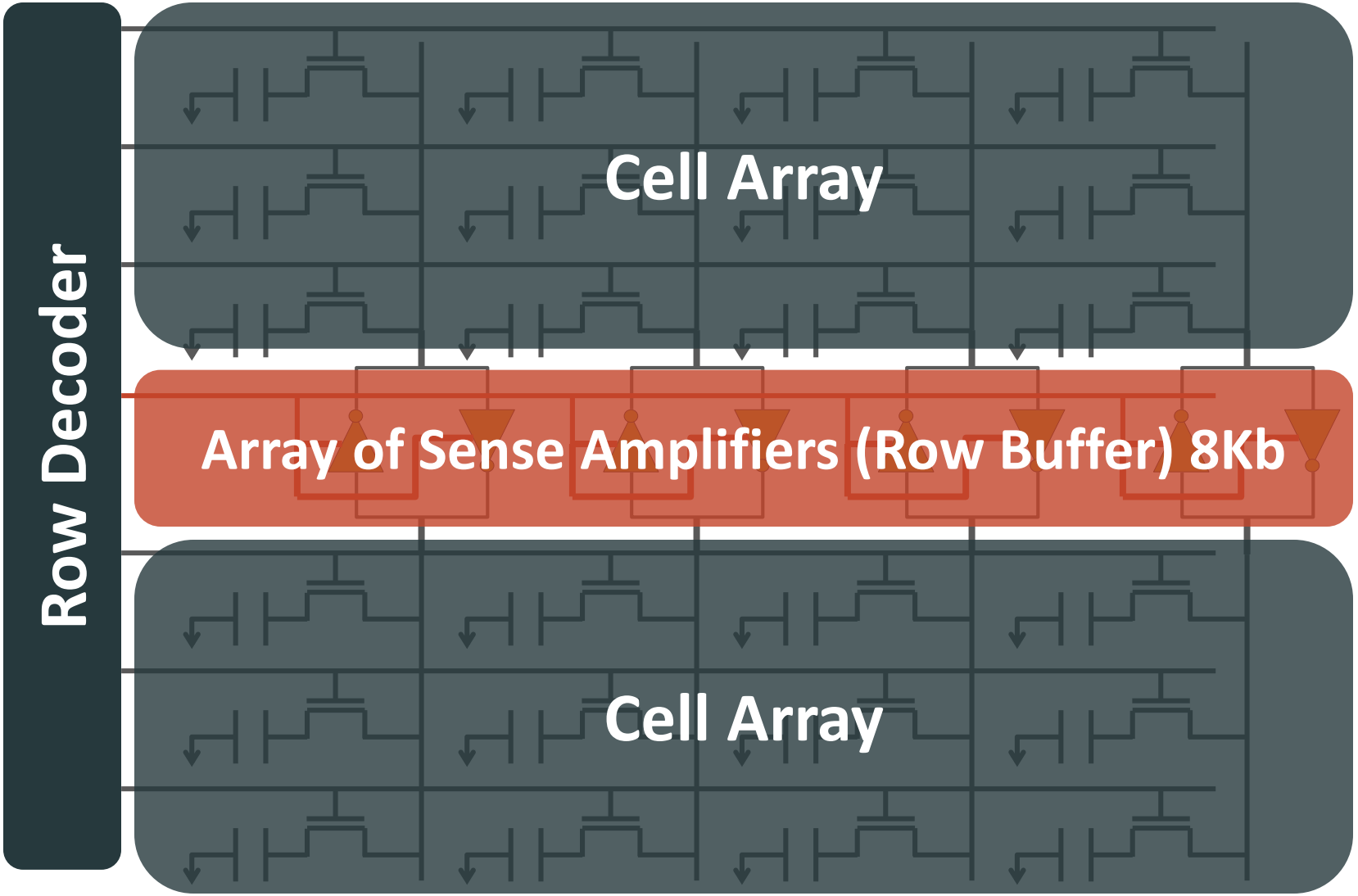
Capacitor to Sense Amplifier



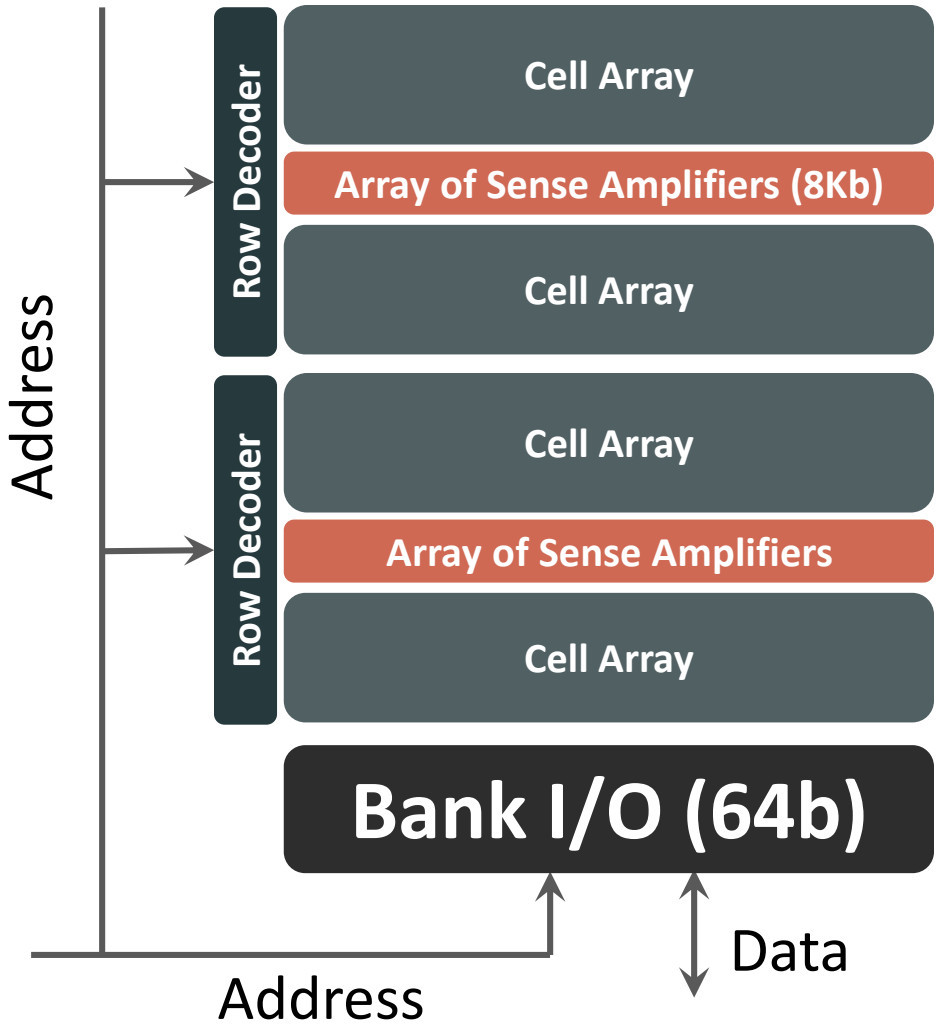
DRAM Cell Operation



DRAM Subarray – Building Block for DRAM Chip

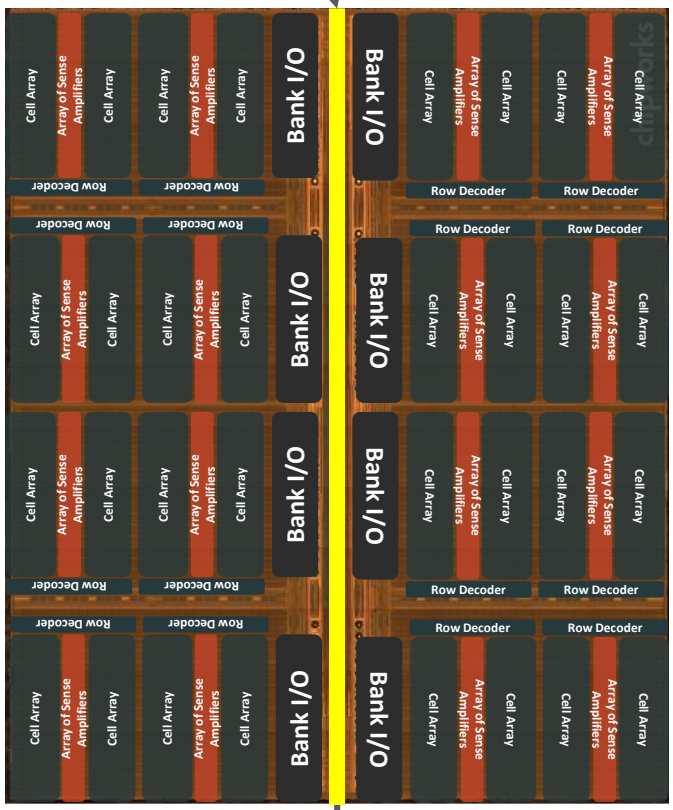


DRAM Bank


Row Decoder
Cell Array
Array of Sense Amplifiers (8Kb)
Cell Array
Row Decoder
Cell Array
Array of Sense Amplifiers
Cell Array
Address
Bank I/O (64b)
Data
Address

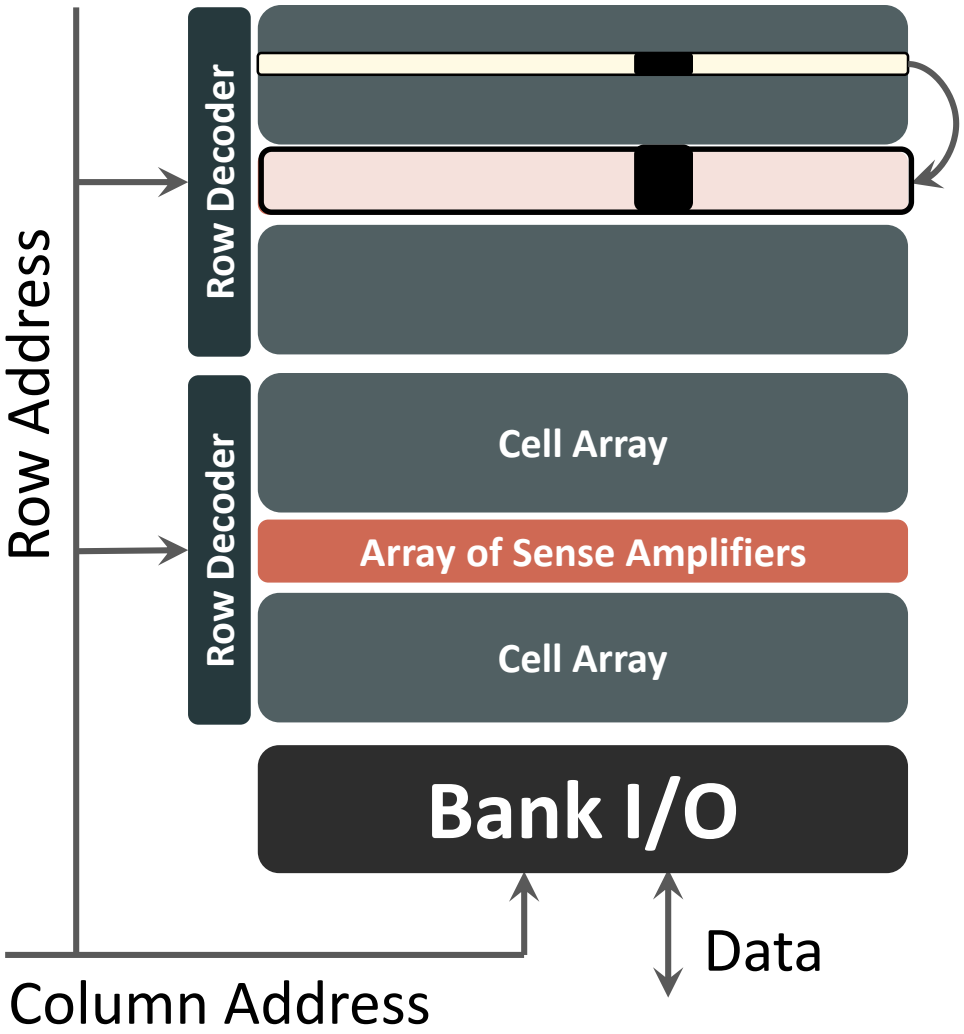
DRAM Chip

Shared internal bus



Memory channel - 8bits

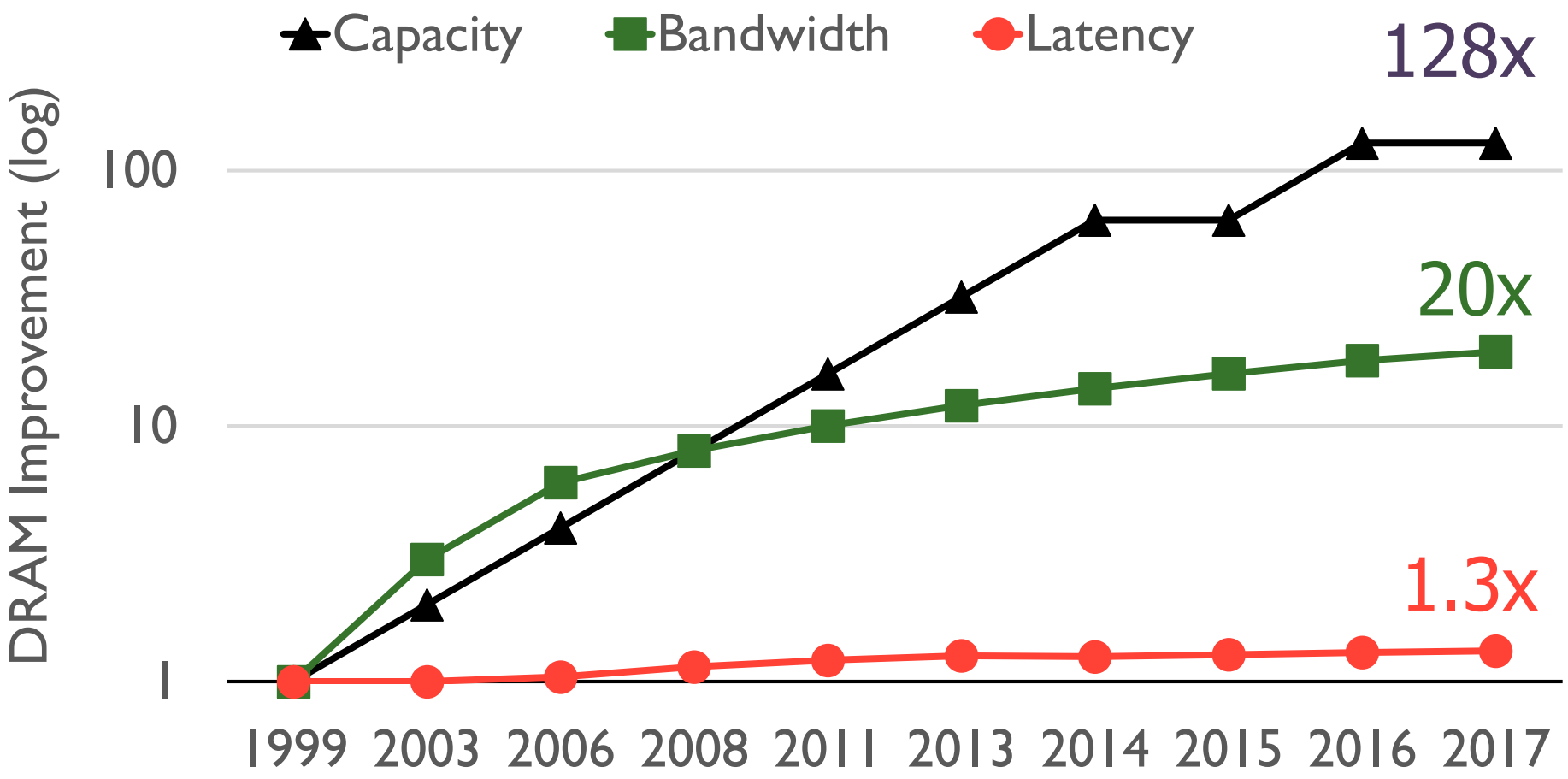
DRAM Operation



1. `ACTIVATE` Row
2. `READ/WRITE` Column
3. `PRECHARGE`

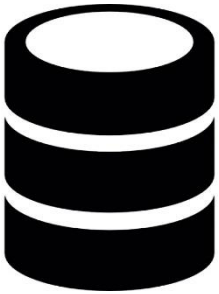
Memory Latency: Fundamental Tradeoffs

Review: Memory Latency Lags Behind



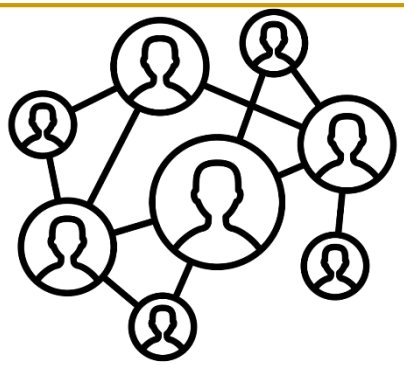
Memory latency remains almost constant

DRAM Latency Is Critical for Performance



In-memory Databases

[Mao+, EuroSys'12;
Clapp+ (**Intel**), IISWC'15]

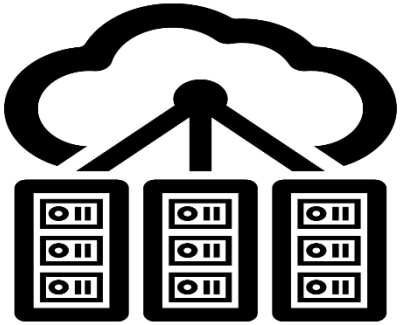


Graph/Tree Processing

[Xu+, IISWC'12; Umuroglu+, FPL'15]

In-Memory Data Analytics

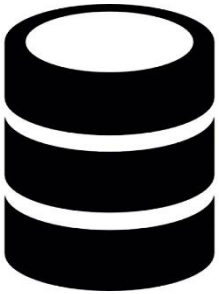
[Clapp+ (**Intel**), IISWC'15;
Awan+, BDCloud'15]



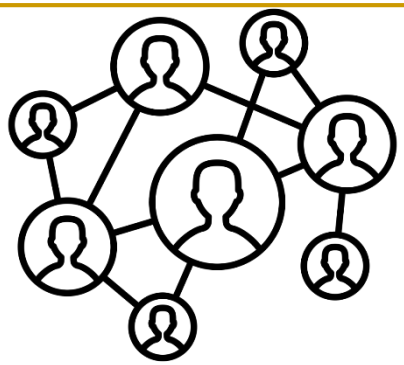
Datacenter Workloads

[Kanev+ (**Google**), ISCA'15]

DRAM Latency Is Critical for Performance



In-memory Databases

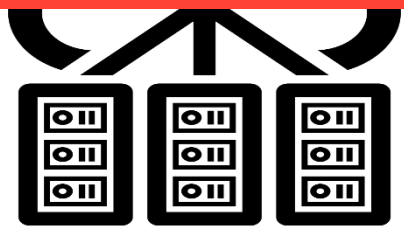


Graph/Tree Processing

Long memory latency → performance bottleneck

In-Memory Data Analytics

[Clapp+ (**Intel**), IISWC'15; Awan+, BDCloud'15]



Datacenter Workloads

[Kanev+ (**Google**), ISCA'15]

The Memory Latency Problem

- High memory latency is a significant limiter of system performance and energy-efficiency
- It is becoming increasingly so with higher memory contention in multi-core and heterogeneous architectures
  - Exacerbating the bandwidth need
  - Exacerbating the QoS problem
- It increases processor design complexity due to the mechanisms incorporated to tolerate memory latency

Retrospective: Conventional Latency Tolerance Techniques

- Caching [initially by Wilkes, 1965]
  - Widely used, simple, effective, but inefficient, passive
  - Not all applications/phases exhibit temporal or spatial locality
- Prefetching [initially in IBM 360/91, 1967]

None of These Fundamentally Reduce Memory Latency

ongoing research effort

- Out-of-order execution [initially by Tomasulo, 1967]
  - Tolerates cache misses that cannot be prefetched
  - Requires extensive hardware resources for tolerating long latencies

Two Major Sources of Latency Inefficiency

- Modern DRAM is not designed for low latency
  - Main focus is cost-per-bit (capacity)
- Modern DRAM latency is determined by worst case conditions and worst case devices
  - Much of memory latency is unnecessary

Our Goal: Reduce Memory Latency at the Source of the Problem

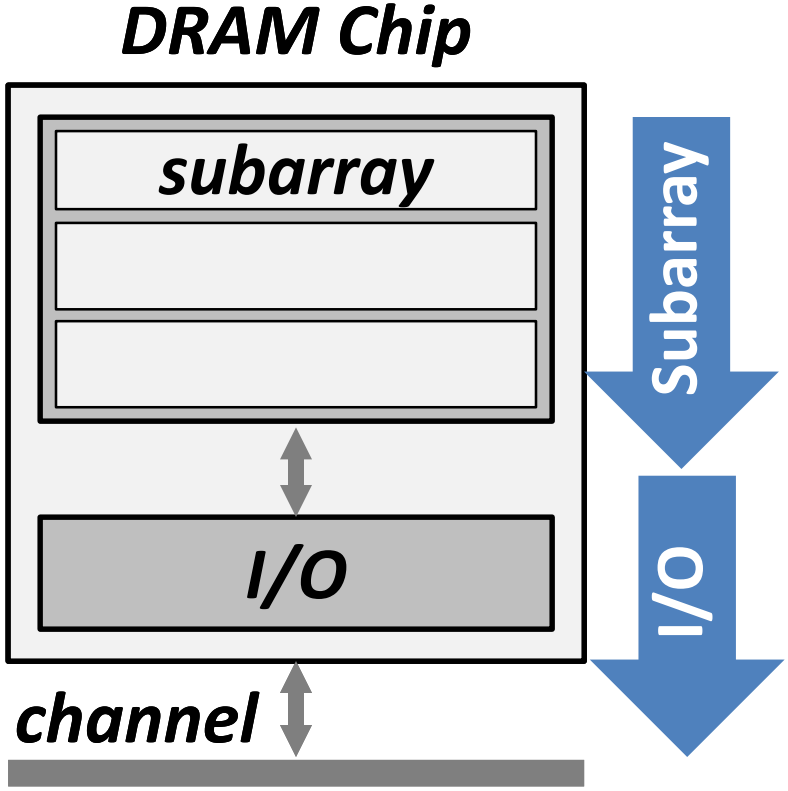
What Causes the Long Memory Latency?

Why the Long Memory Latency?

- Reason 1: Design of DRAM Micro-architecture
  - Goal: Maximize capacity/area, not minimize latency
- Reason 2: "One size fits all" approach to latency specification
  - Same latency parameters for all temperatures
  - Same latency parameters for all DRAM chips
  - Same latency parameters for all parts of a DRAM chip
  - Same latency parameters for all supply voltage levels
  - Same latency parameters for all application data
  - …

Tiered Latency DRAM

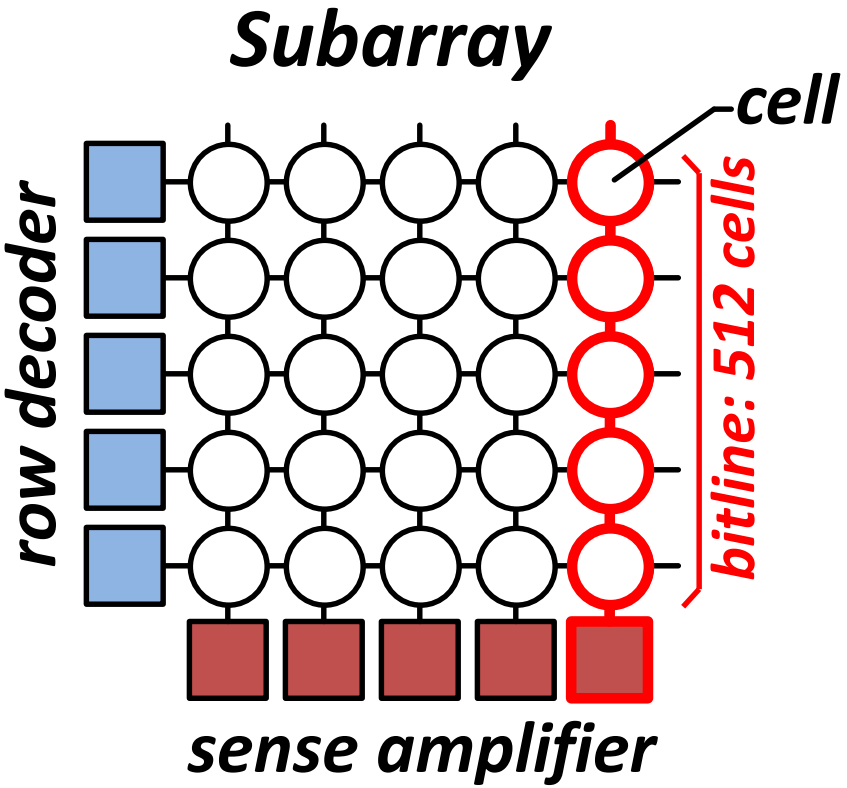
What Causes the Long Latency?

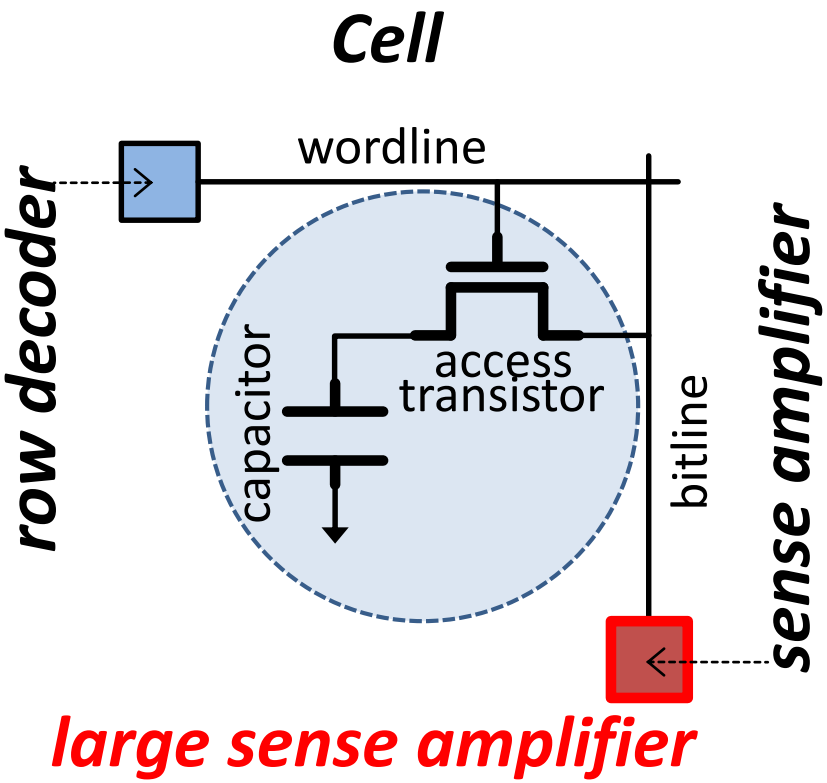


DRAM Latency = Subarray Latency + I/O Latency

Dominant

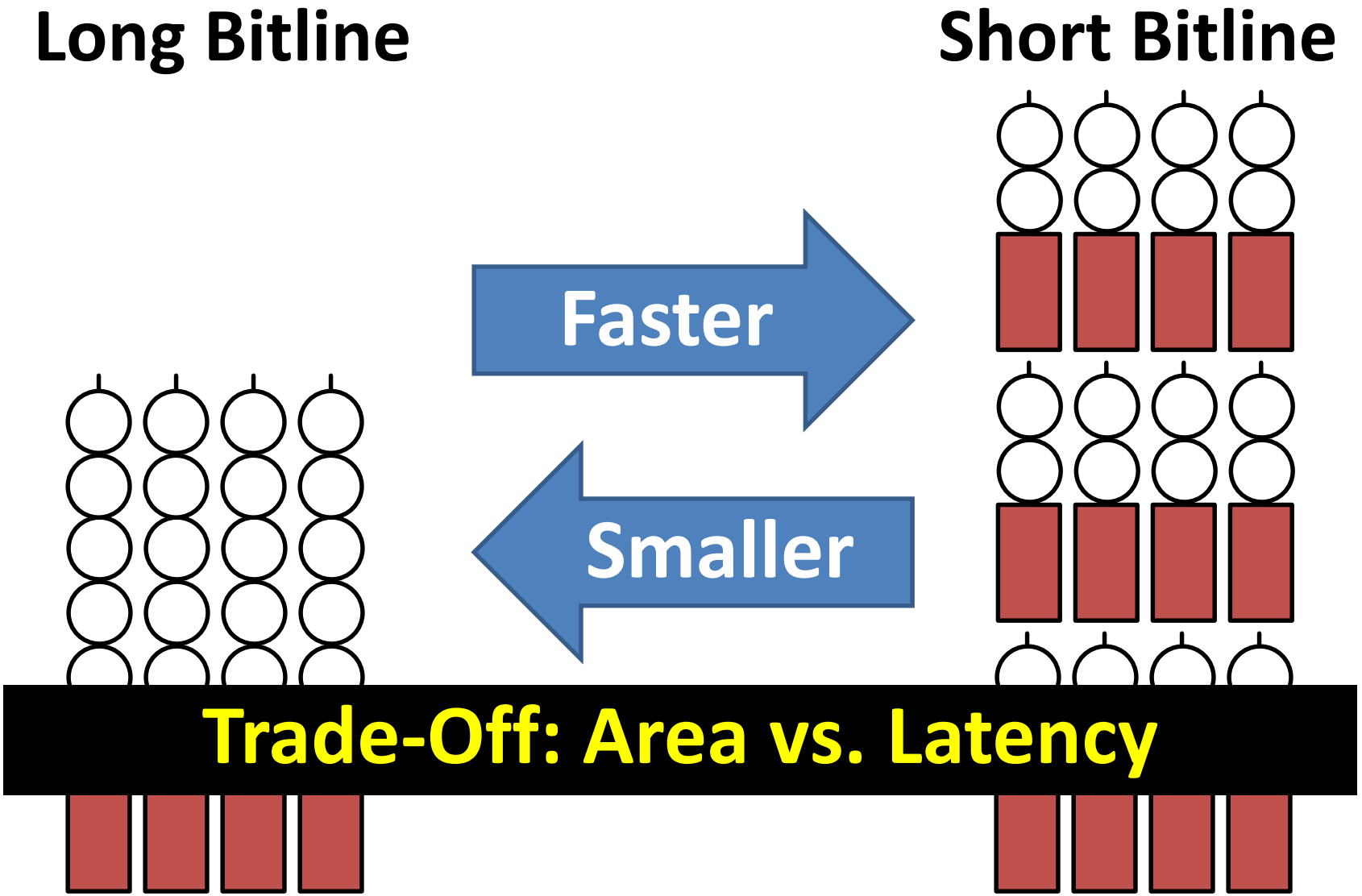
Why is the Subarray So Slow?





- **Long bitline**
  - **Amortizes sense amplifier cost → Small area**
  - **Large bitline capacitance → High latency & power**

Trade-Off: Area (Die Size) vs. Latency



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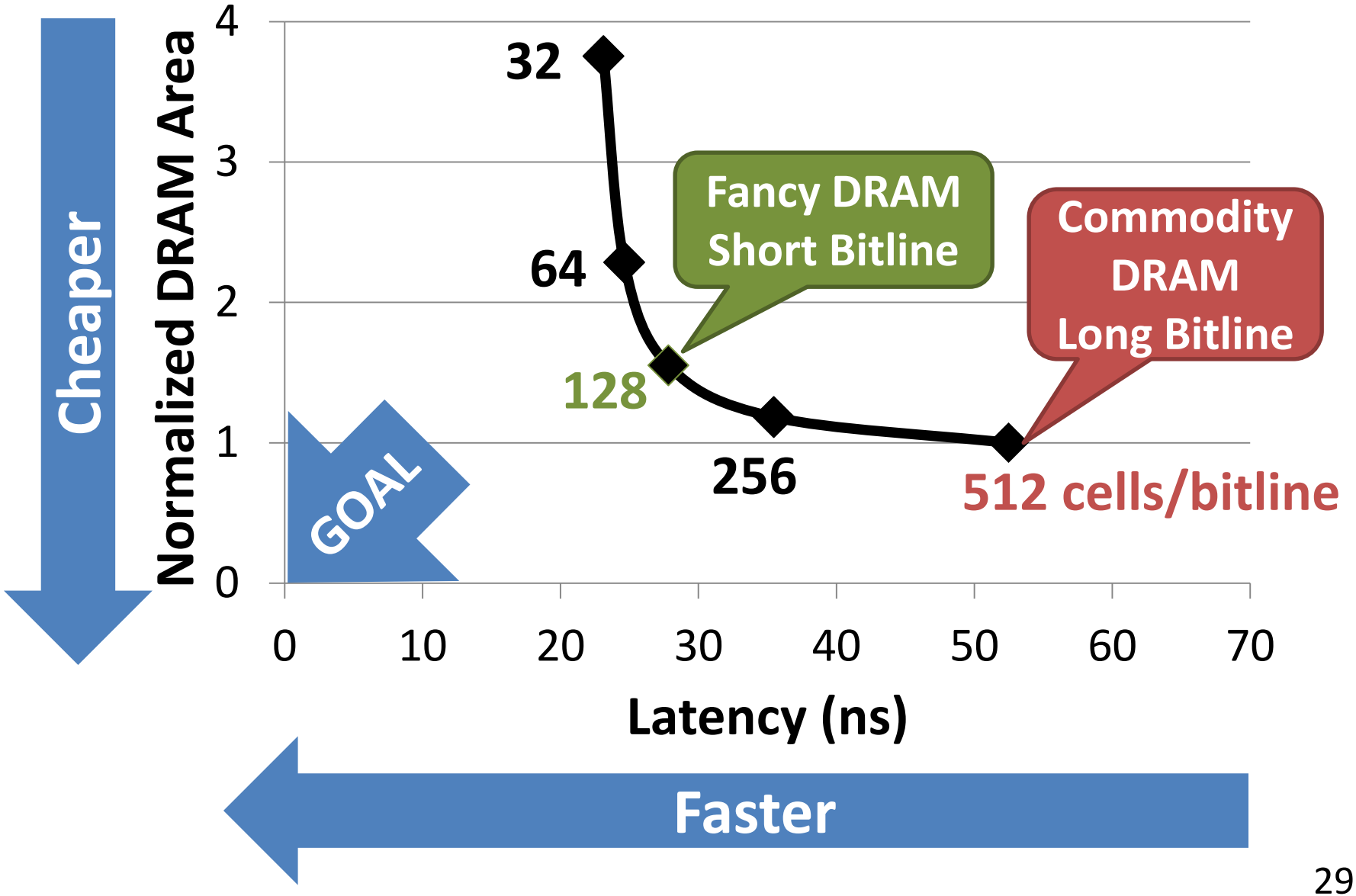
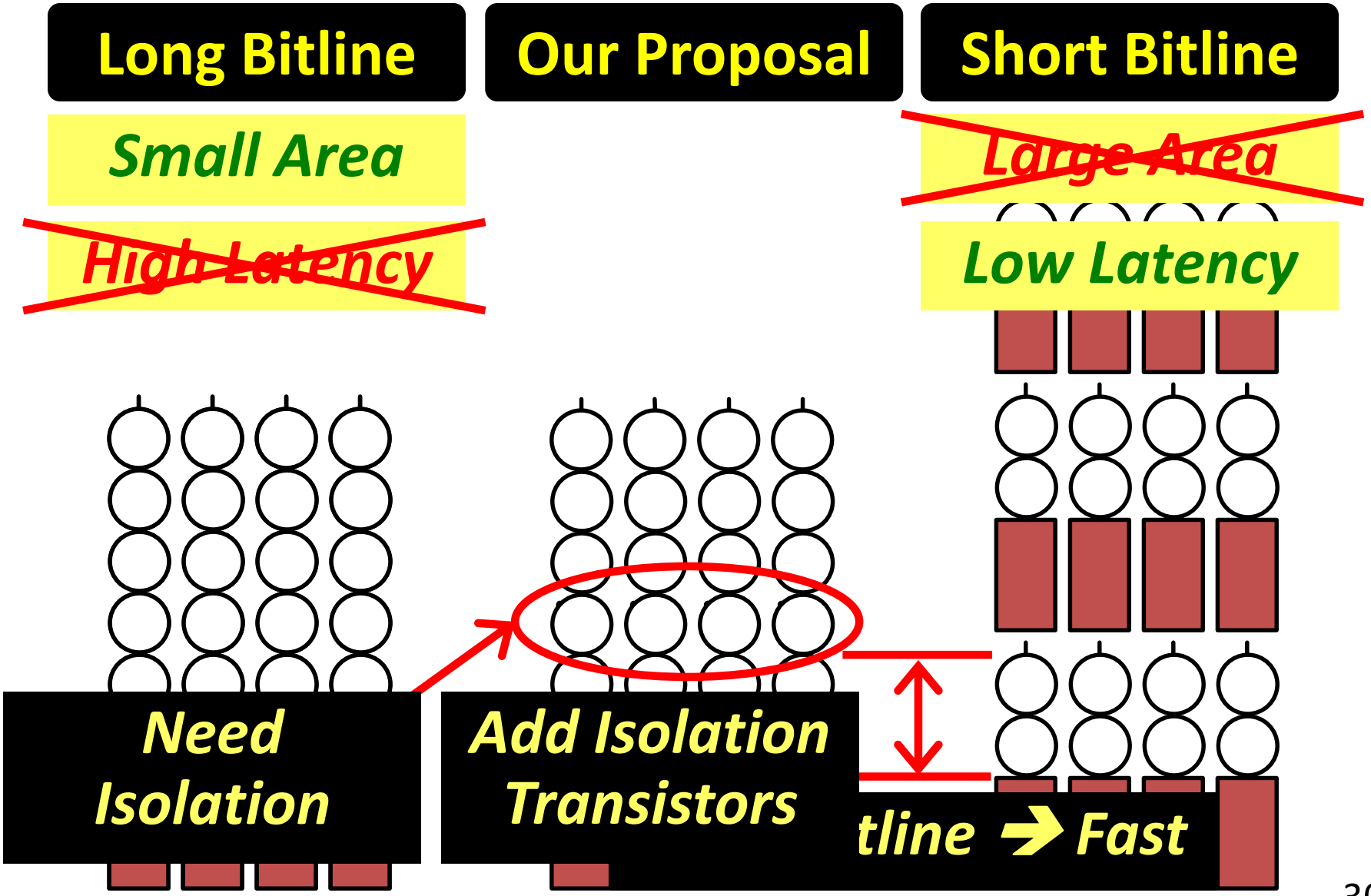
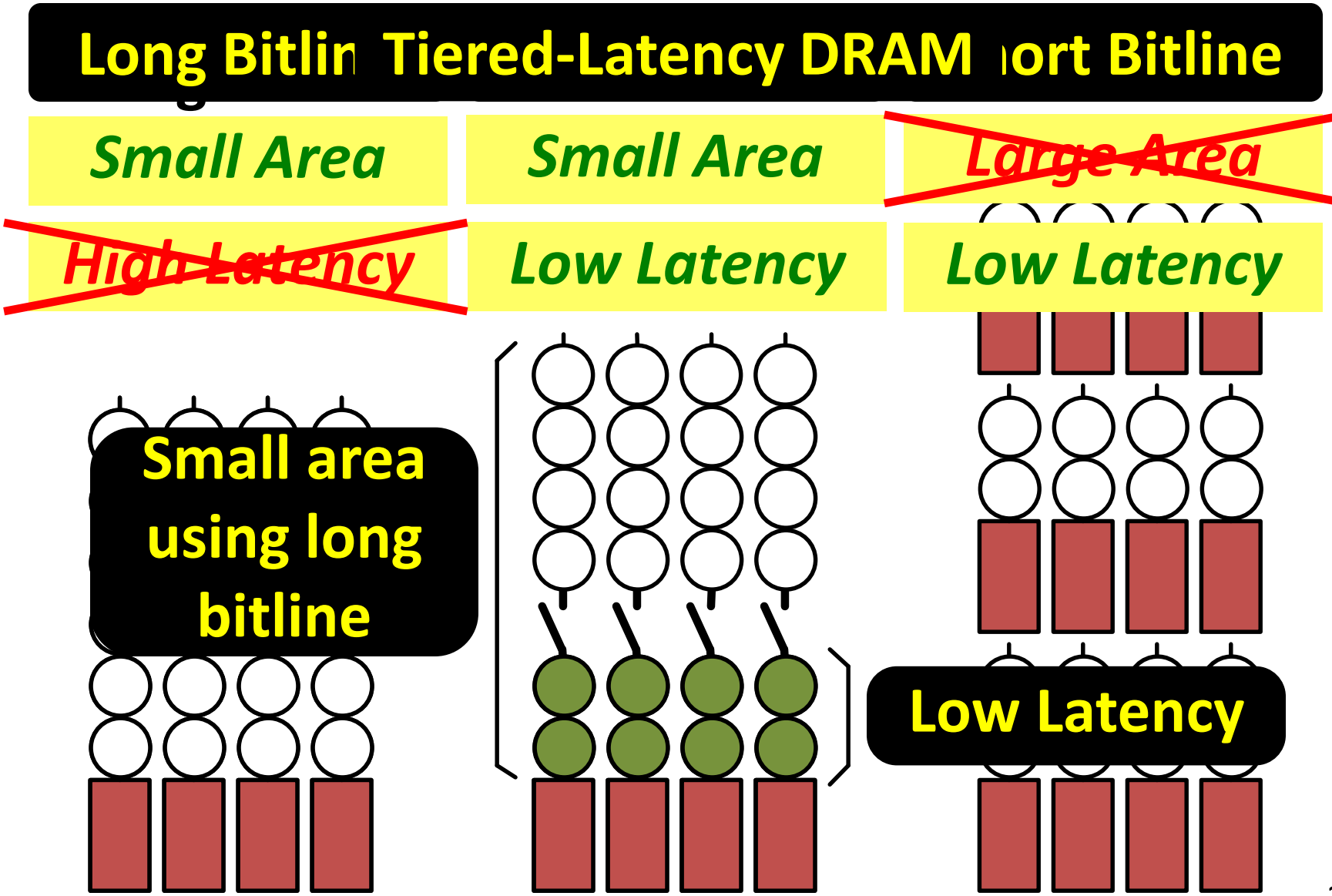


Approximating the Best of Both Worlds



Approximating the Best of Both Worlds

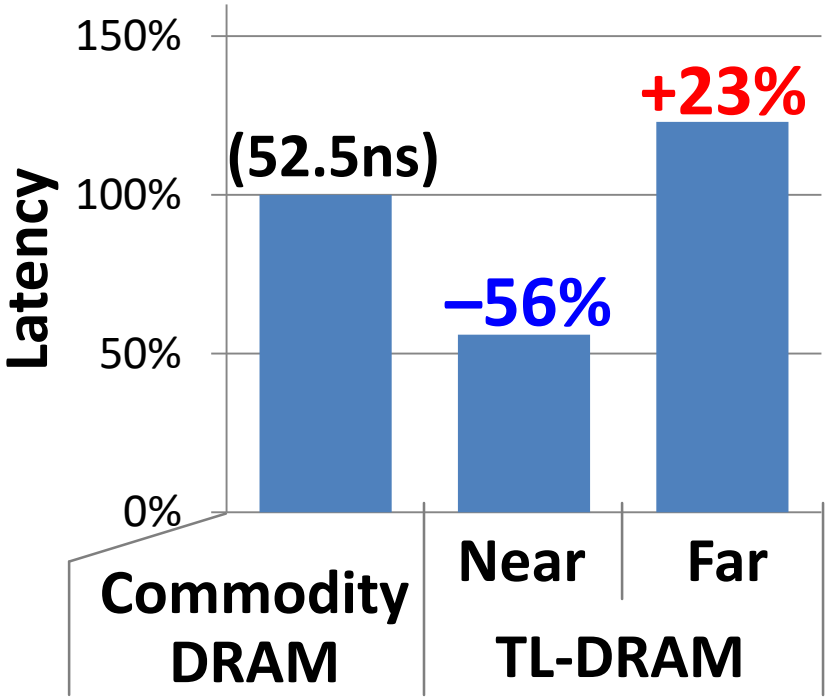


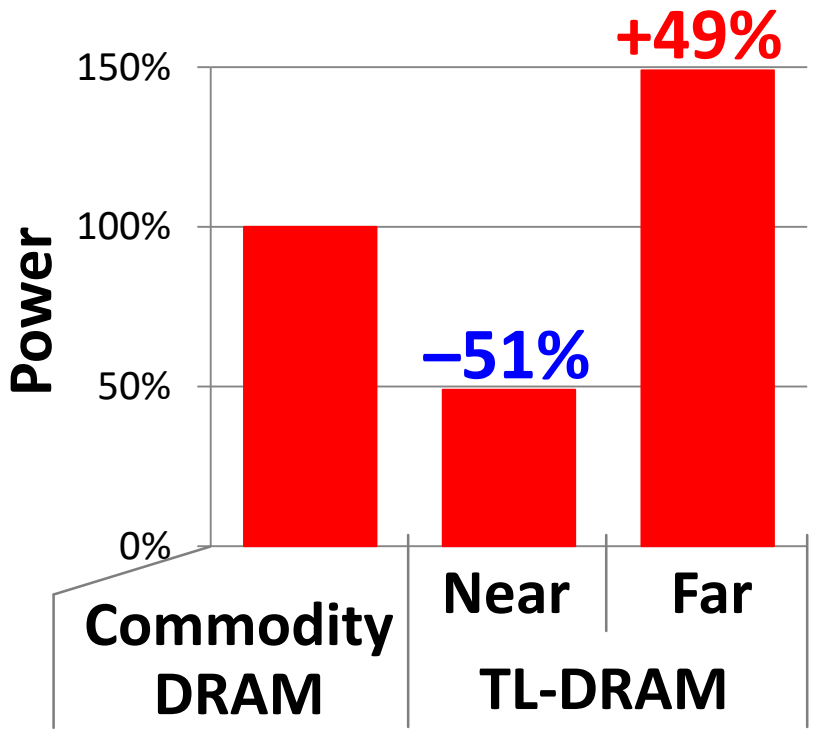
Latency, Power, and Area Evaluation

- **Commodity DRAM:** 512 cells/bitline
- **TL-DRAM:** 512 cells/bitline
  - Near segment: 32 cells
  - Far segment: 480 cells
- **Latency Evaluation**
  - SPICE simulation using circuit-level DRAM model
- **Power and Area Evaluation**
  - DRAM area/power simulator from Rambus
  - DDR3 energy calculator from Micron

Commodity DRAM vs. TL-DRAM [HPCA 2013]

- **DRAM Latency** (tRC)
- **DRAM Power**

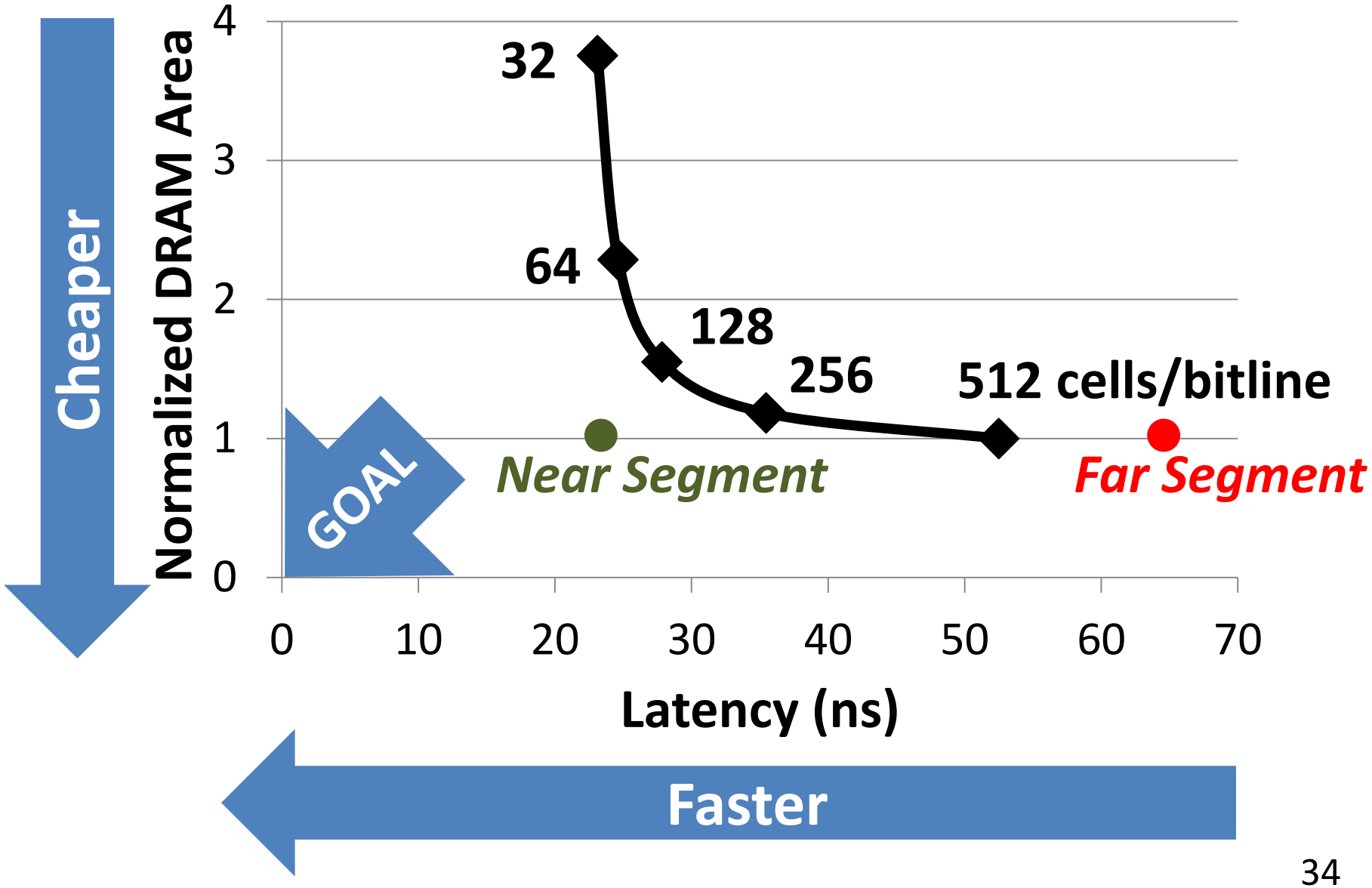




- **DRAM Area Overhead**

  ~3%: mainly due to the isolation transistors

Trade-Off: Area (Die-Area) vs. Latency



Leveraging Tiered-Latency DRAM

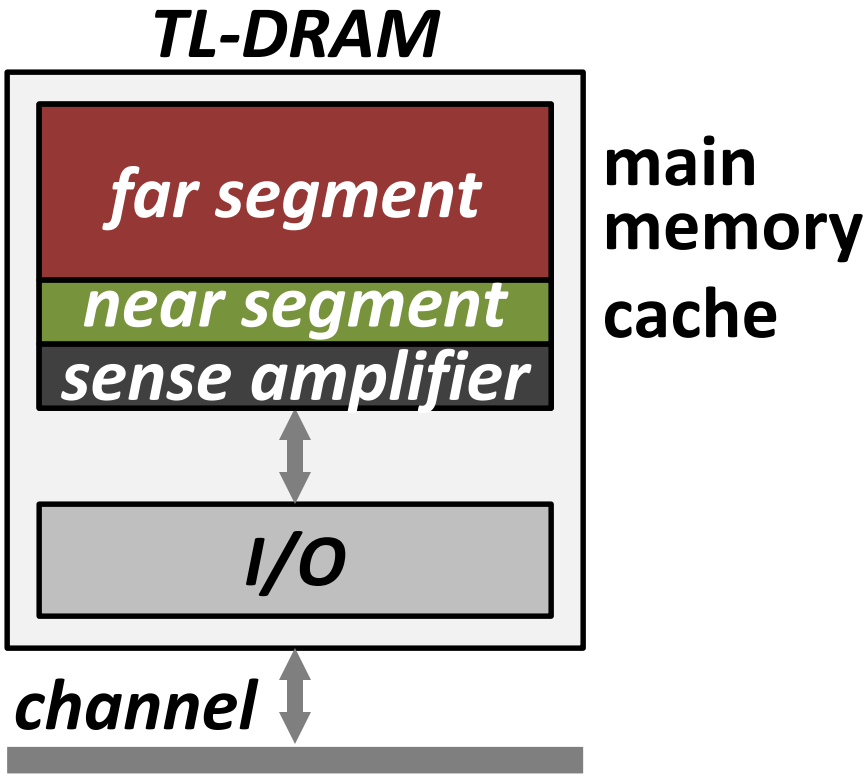
- TL-DRAM is a ***substrate*** that can be leveraged by the hardware and/or software

- Many potential uses

1. Use near segment as hardware-managed ***inclusive*** cache to far segment
2. Use near segment as hardware-managed ***exclusive*** cache to far segment
3. Profile-based page mapping by operating system
4. Simply replace DRAM with TL-DRAM

Lee+, "Tiered-Latency DRAM: A Low Latency and Low Cost DRAM Architecture," HPCA 2013.

Near Segment as Hardware-Managed Cache

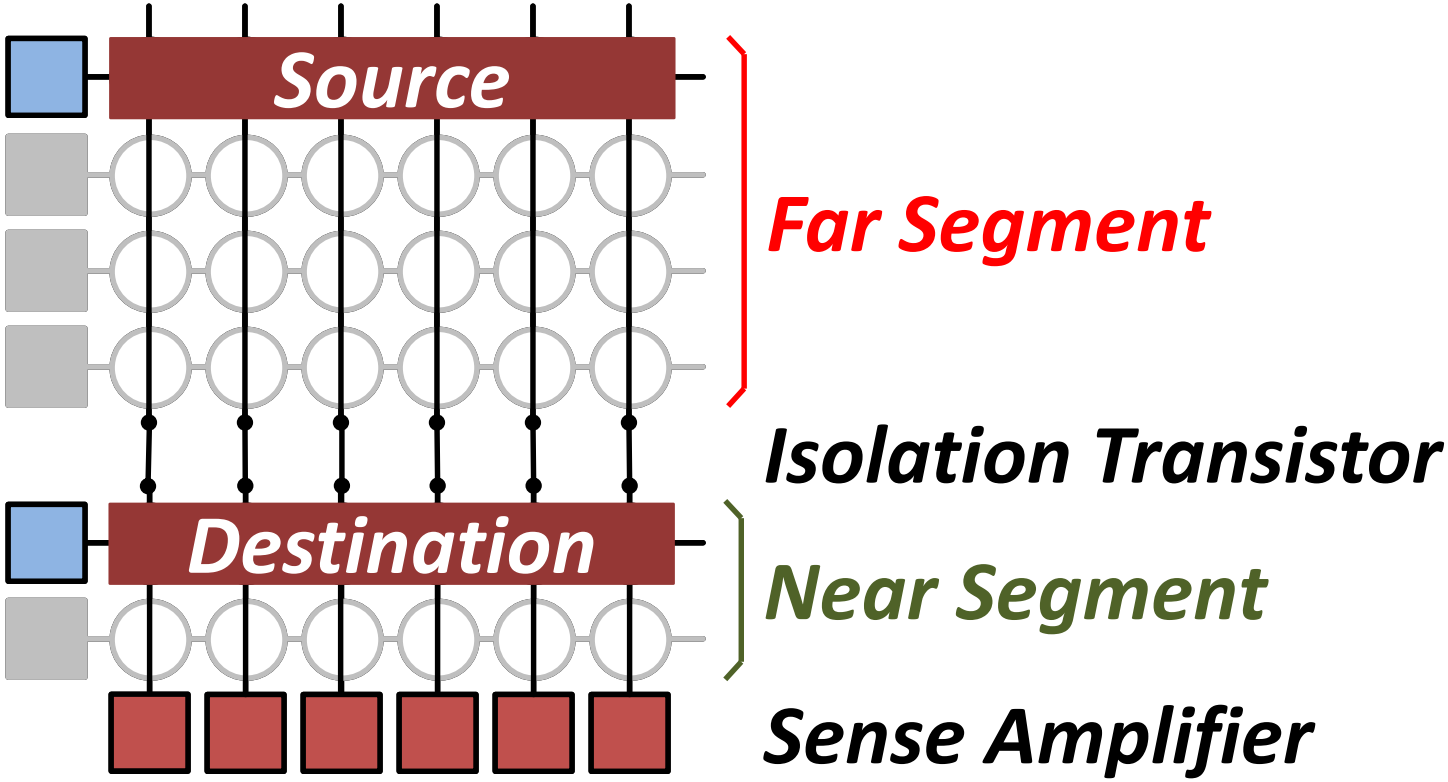


- **Challenge 1:** How to efficiently migrate a row between segments?
- **Challenge 2:** How to efficiently manage the cache?

Inter-Segment Migration

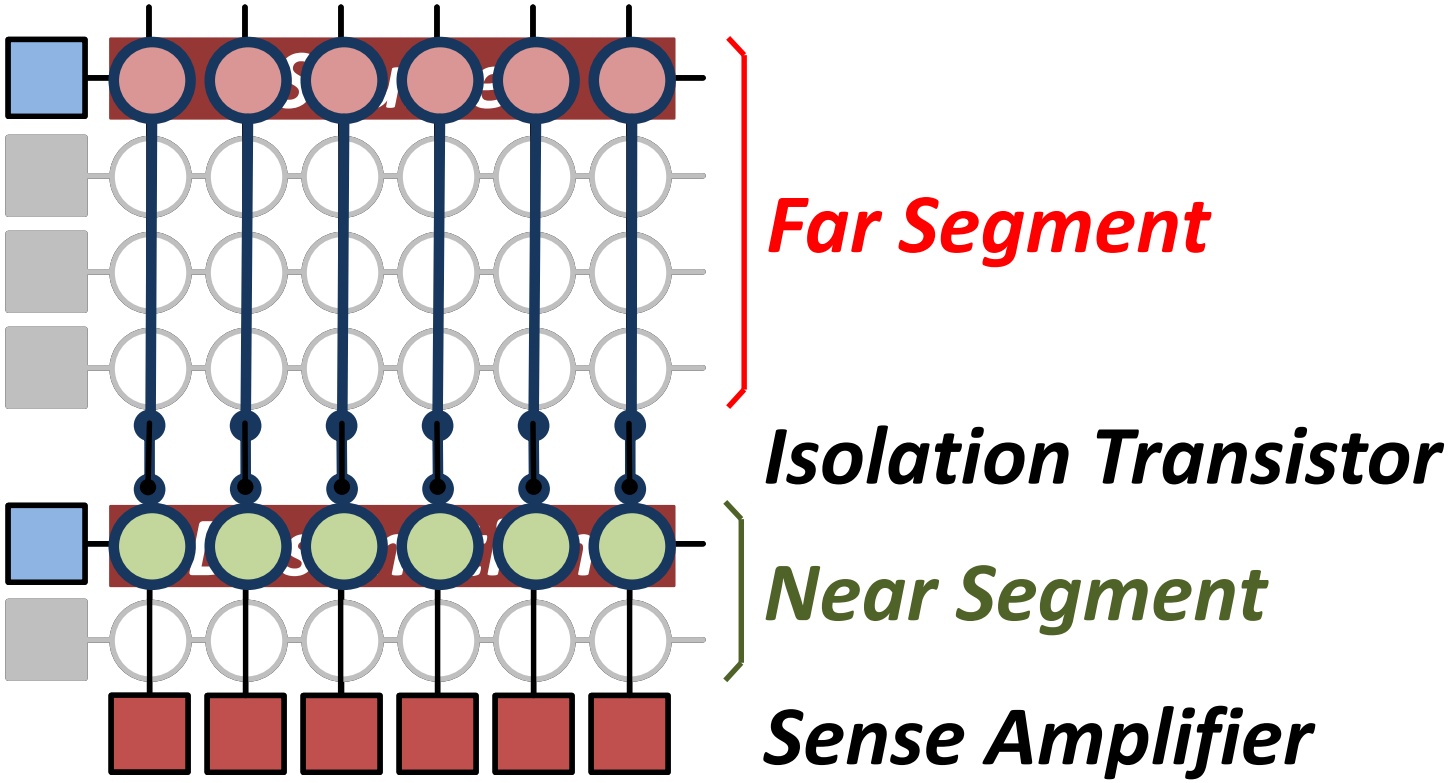
- **Goal:** Migrate source row into destination row
- **Naïve way:** Memory controller reads the source row *byte by byte* and writes to destination row *byte by byte*

→ High latency



Inter-Segment Migration

- **Our way:**
  - Source and destination cells ***share bitlines***
  - Transfer data from source to destination across ***shared bitlines*** concurrently



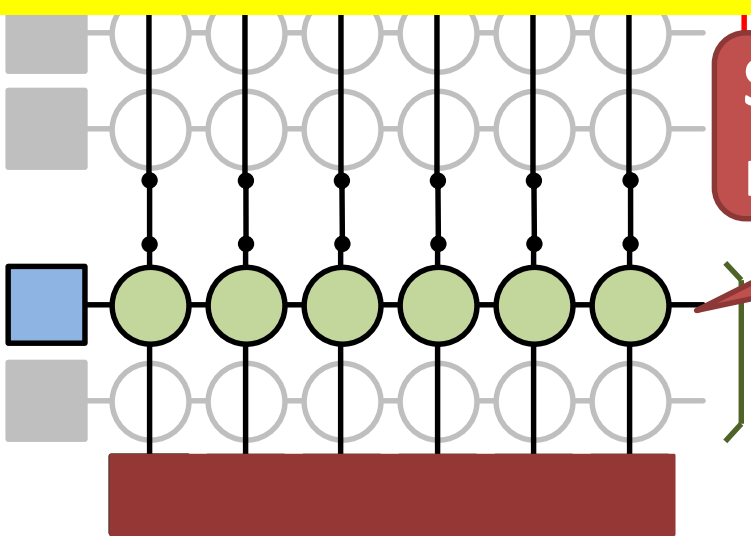
Inter-Segment Migration

- **Our way:**
  - Source and destination cells ***share bitlines***
  - Transfer data from so
    shared bitlines concu

Step 1: Activate source row

Migration is overlapped with source row access

Additional ~4ns over row access latency

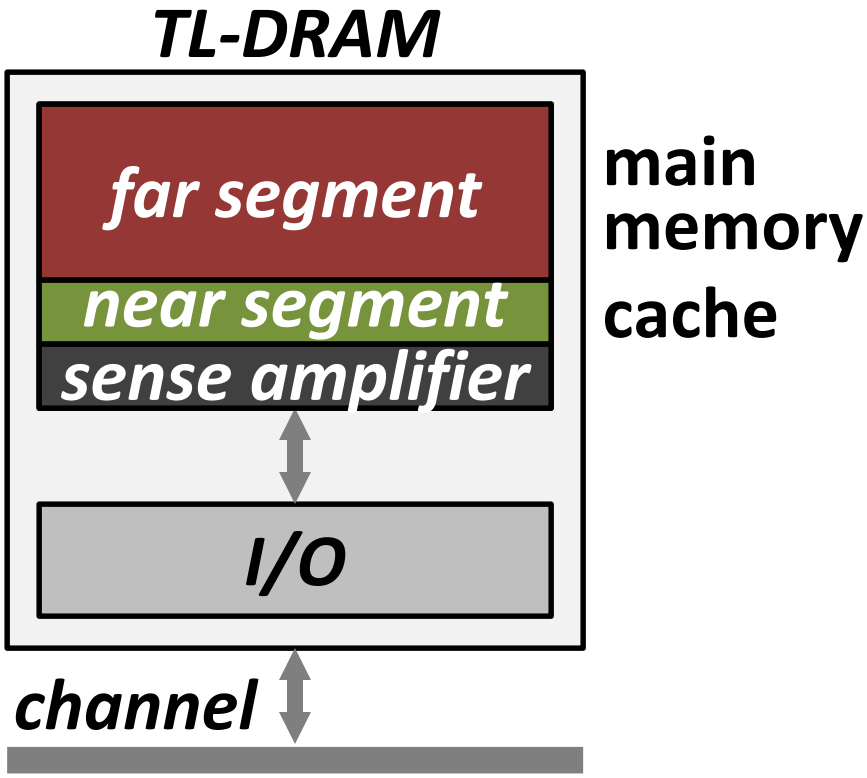


Step 2: Activate destination row to connect cell and bitline

Near Segment

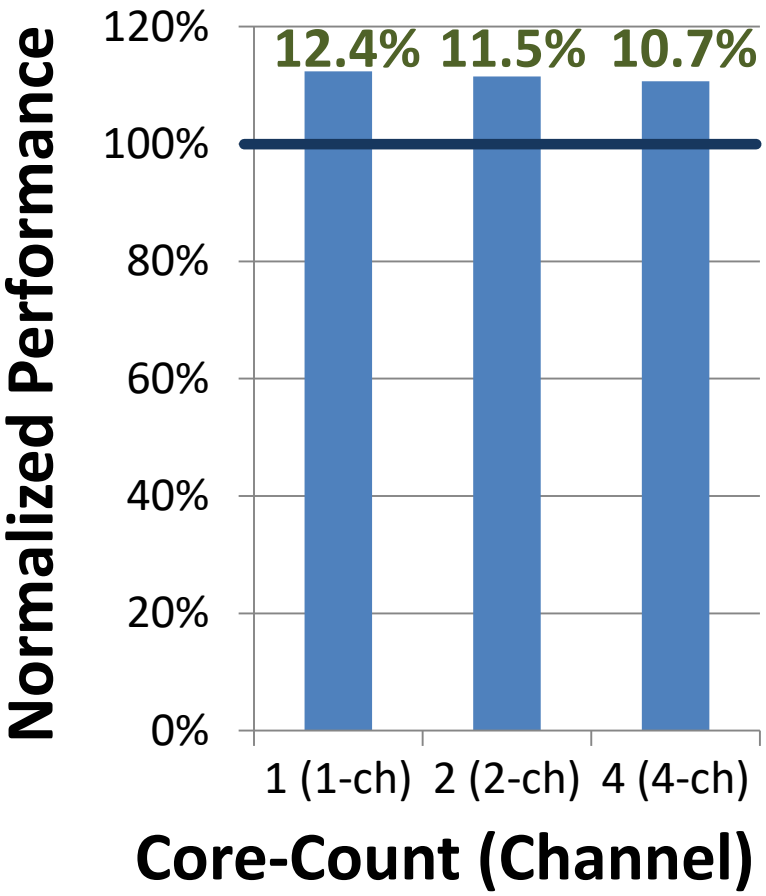
Sense Amplifier

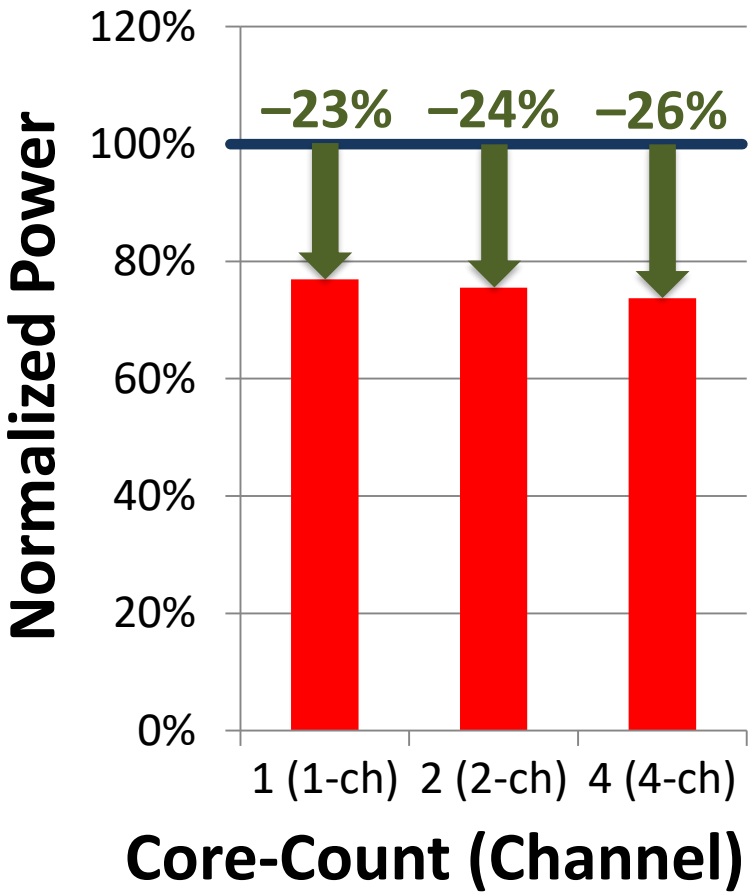
Near Segment as Hardware-Managed Cache



- **Challenge 1:** How to efficiently migrate a row between segments?
- **Challenge 2:** How to efficiently manage the cache?

Performance & Power Consumption

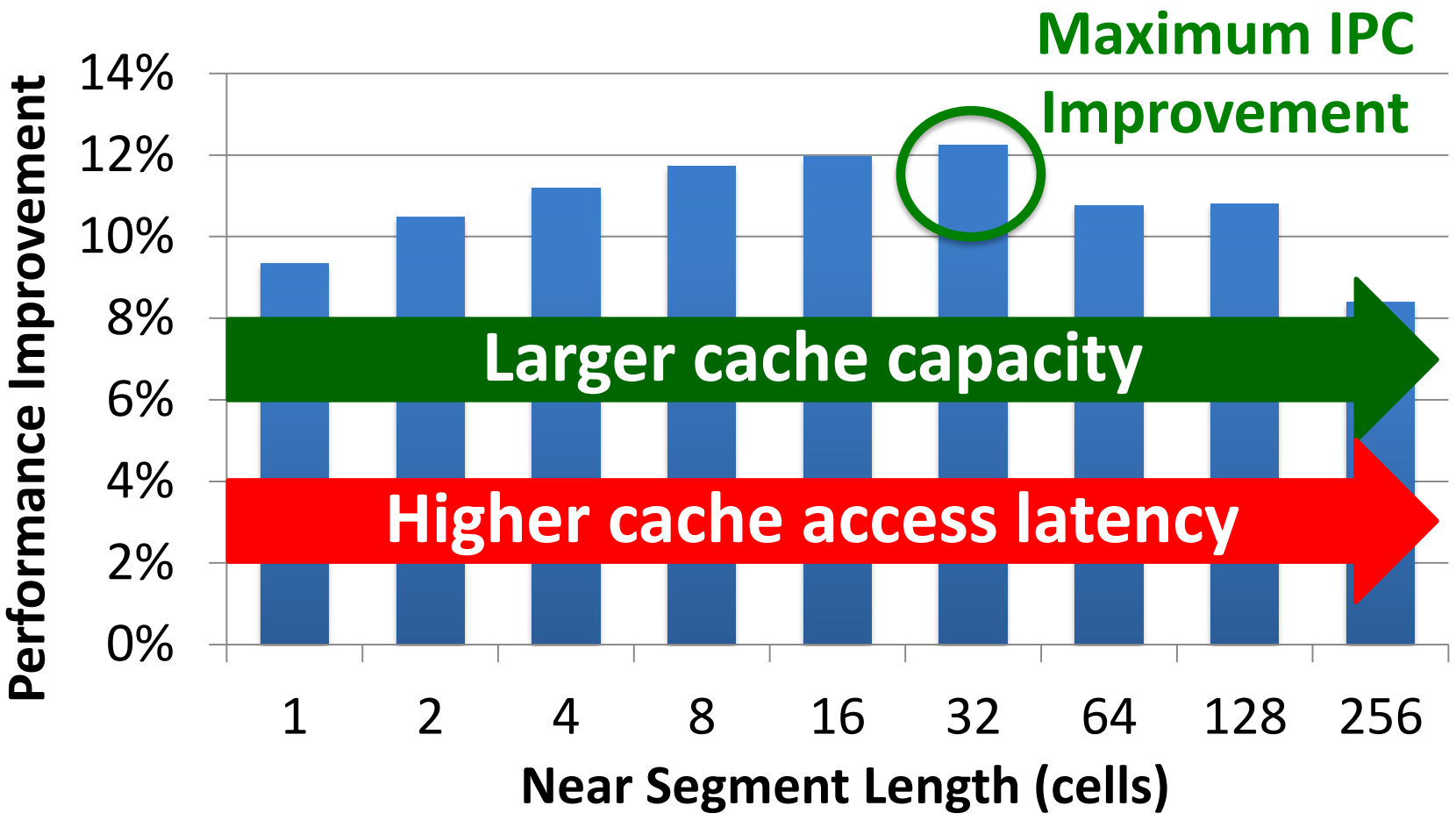




Using near segment as a cache improves performance and reduces power consumption

Lee+, "Tiered-Latency DRAM: A Low Latency and Low Cost DRAM Architecture," HPCA 2013.

Single-Core: Varying Near Segment Length



By adjusting the near segment length, we can trade off cache capacity for cache latency

More on TL-DRAM

- Donghyuk Lee, Yoongu Kim, Vivek Seshadri, Jamie Liu, Lavanya Subramanian, and Onur Mutlu,
  "Tiered-Latency DRAM: A Low Latency and Low Cost DRAM Architecture"
  *Proceedings of the 19th International Symposium on High-Performance Computer Architecture (**HPCA**)*, Shenzhen, China, February 2013. Slides (pptx)

Tiered-Latency DRAM: A Low Latency and Low Cost DRAM Architecture

Donghyuk Lee Yoongu Kim Vivek Seshadri Jamie Liu Lavanya Subramanian Onur Mutlu
Carnegie Mellon University

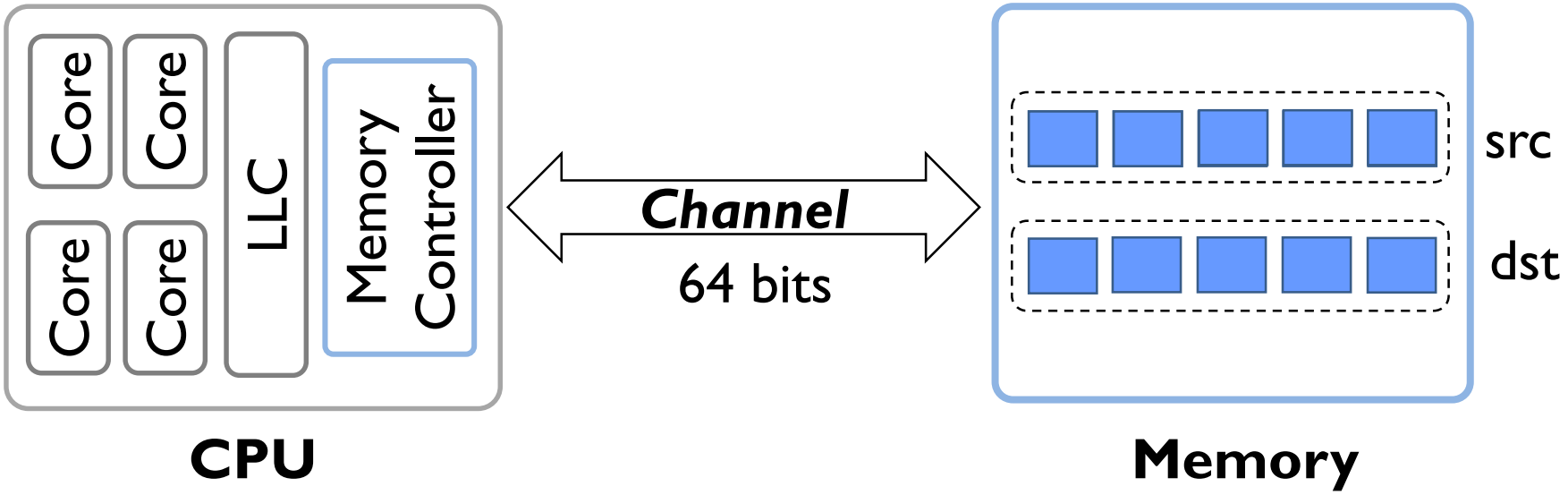
LISA: Low-Cost Inter-Linked Subarrays

[HPCA 2016]

Problem: Inefficient Bulk Data Movement

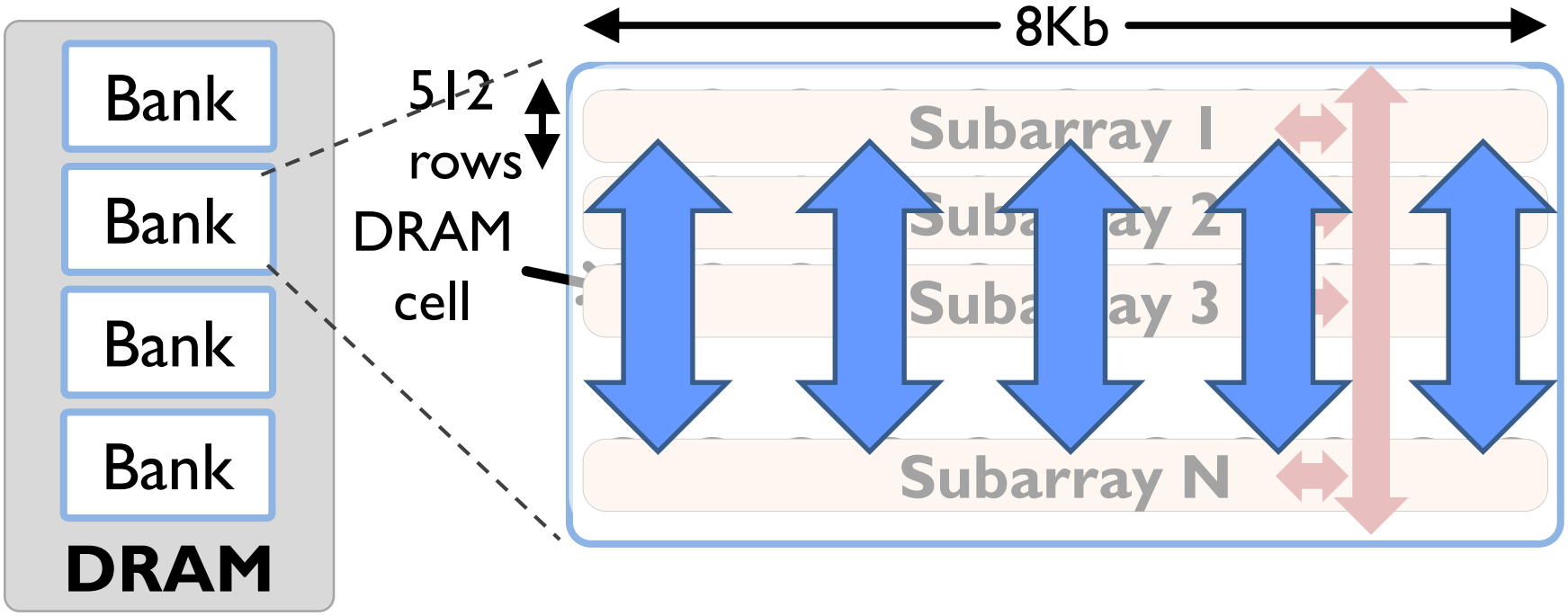
Bulk data movement is a key operation in many applications

– *memmove* & *memcpy:* 5% cycles in Google's datacenter [Kanev+ ISCA'15]



Long latency and high energy

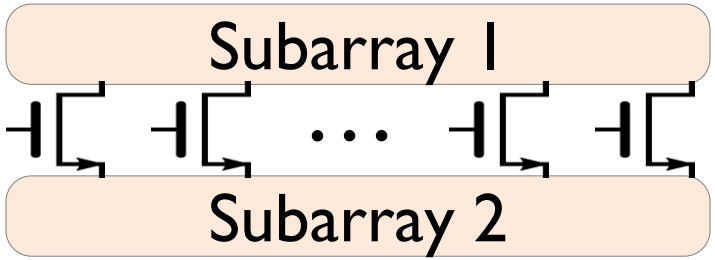
Moving Data Inside DRAM?



Goal: Provide a new substrate to enable wide connectivity between subarrays

Key Idea and Applications

- **Low-cost Inter-linked subarrays (LISA)**
  - Fast bulk data movement between subarrays
  - Wide datapath via isolation transistors: 0.8% DRAM chip area



- LISA is a **versatile substrate** → new applications

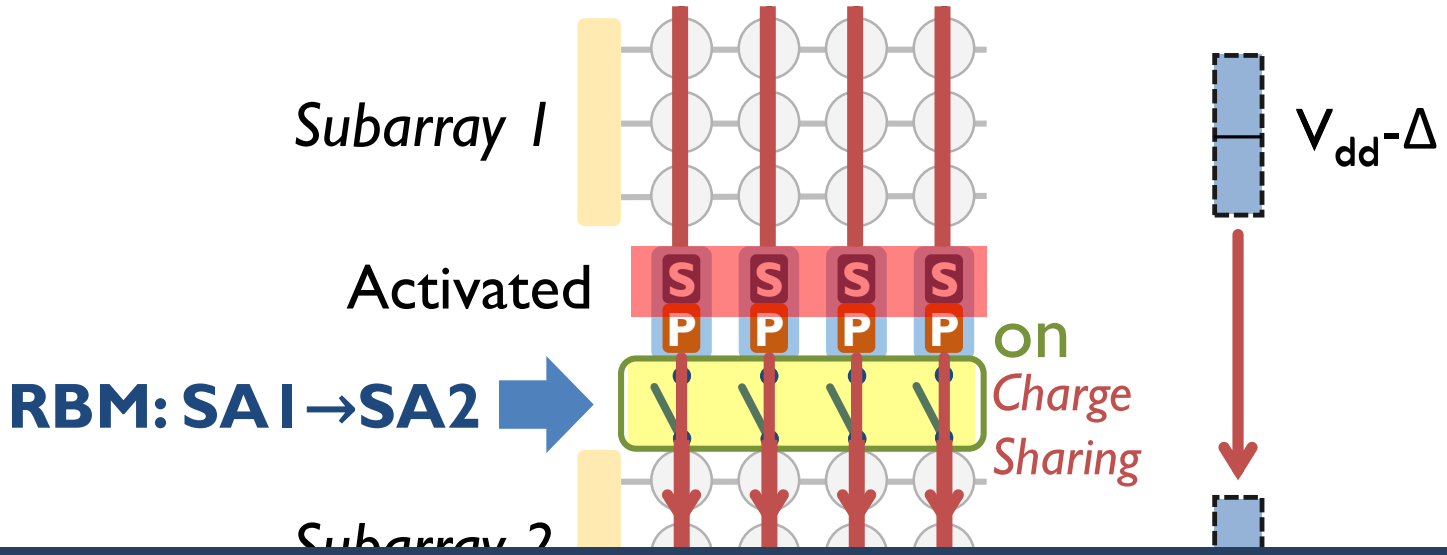
  Fast bulk data copy: Copy latency 1.363ms→0.148ms (9.2x)
  → 66% speedup, -55% DRAM energy

  In-DRAM caching: Hot data access latency 48.7ns→21.5ns (2.2x)
  → 5% speedup

  Fast precharge: Precharge latency 13.1ns→5.0ns (2.6x)
  → 8% speedup

New DRAM Command to Use LISA

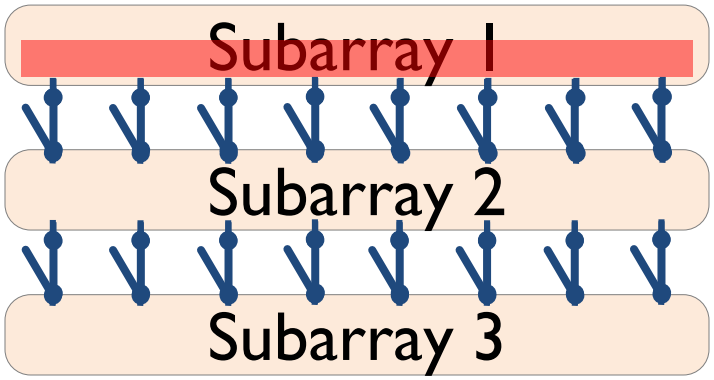
Row Buffer Movement (RBM): Move a row of data in an activated row buffer to a precharged one



RBM transfers an entire row b/w subarrays

RBM Analysis

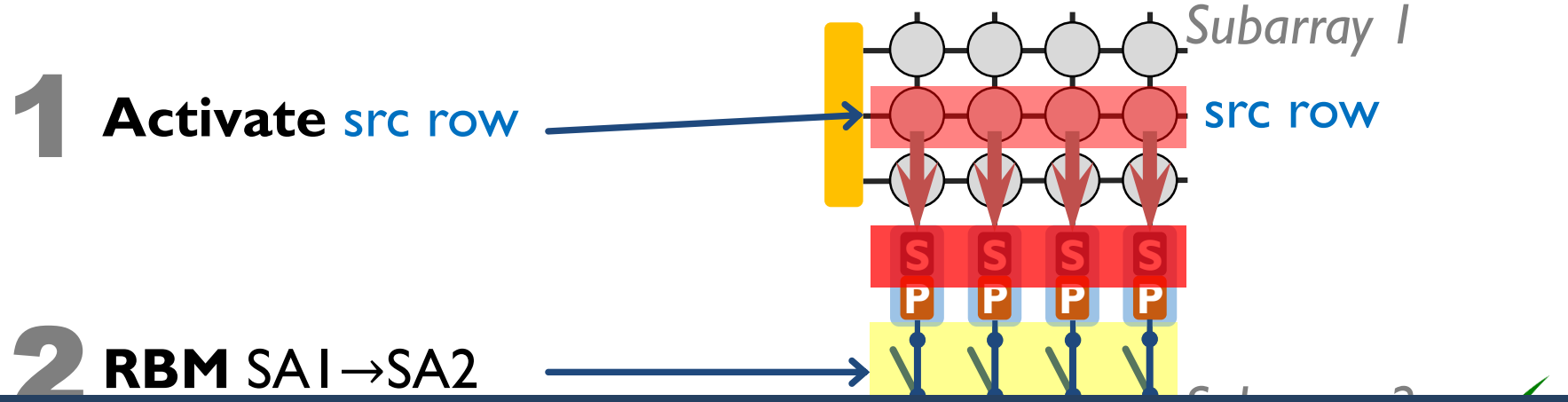
- The range of RBM depends on the DRAM design
  - Multiple RBMs to move data across > 3 subarrays



- Validated with SPICE using worst-case cells
  - NCSU FreePDK 45nm library
- **4KB data in 8ns** (w/ 60% guardband)
  → **500 GB/s, 26x** bandwidth of a DDR4-2400 channel
- **0.8%** DRAM chip area overhead [O+ ISCA'14]

1. Rapid Inter-Subarray Copying (RISC)

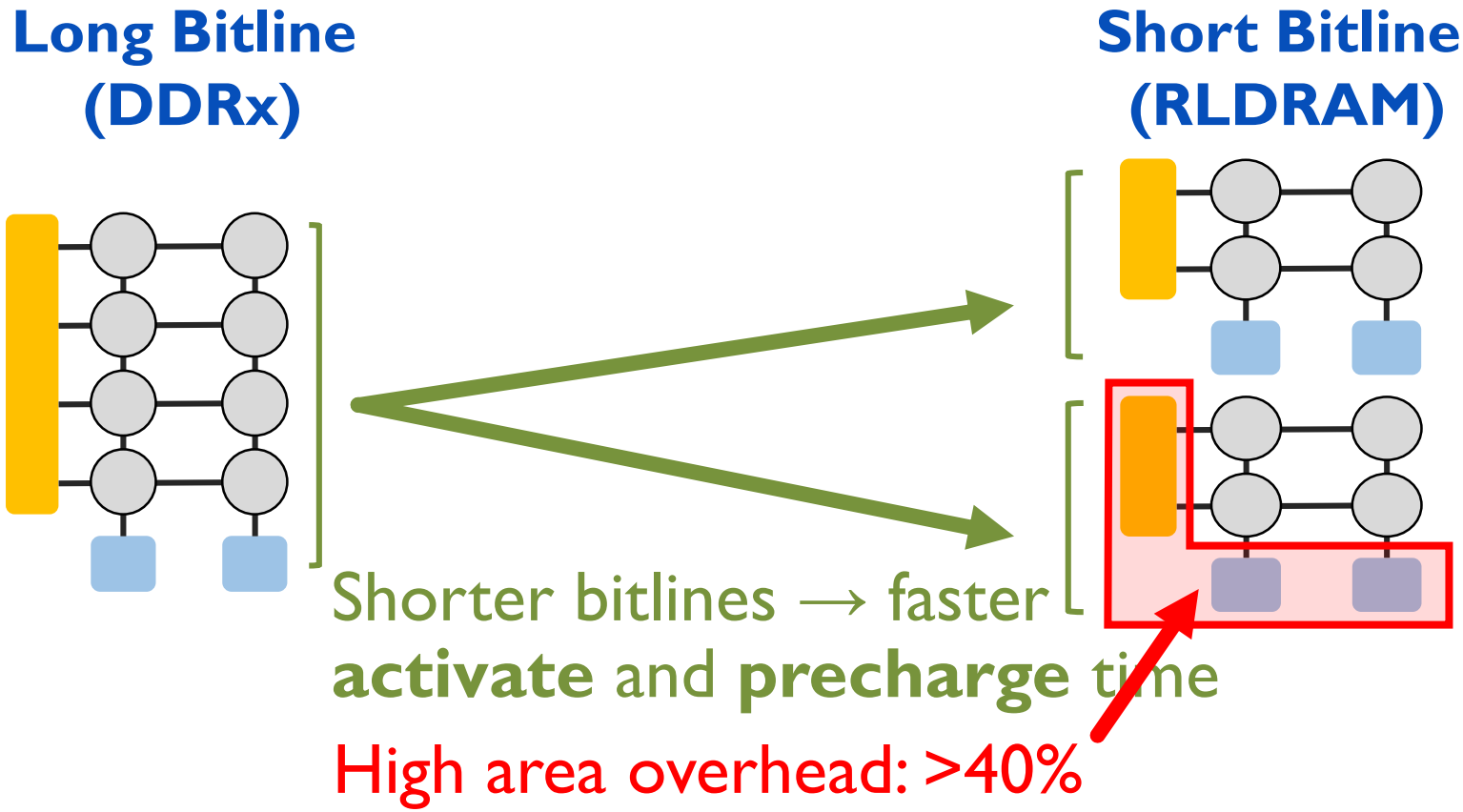
- **Goal:** Efficiently copy a row across subarrays
- **Key idea:** Use *RBM* to form a new command sequence



Reduces row-copy latency by 9.2x, DRAM energy by 48.1x

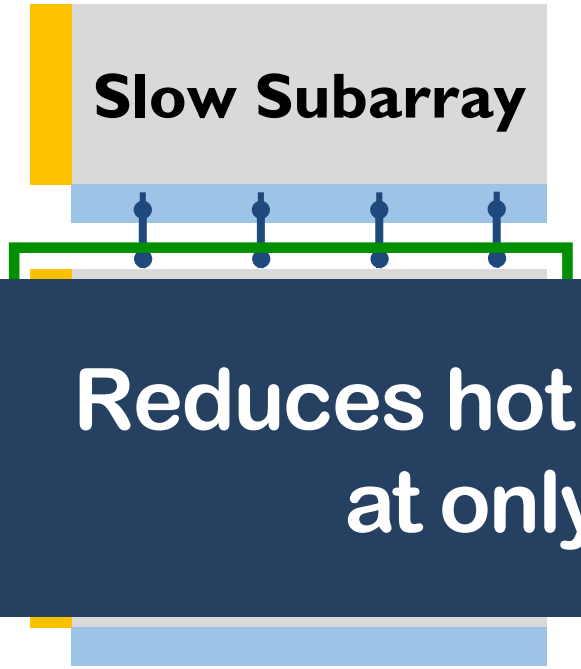
2. Variable Latency DRAM (VILLA)

- **Goal**: Reduce DRAM latency with low area overhead
- **Motivation**: Trade-off between area and latency



2. Variable Latency DRAM (VILLA)

- **Key idea**: Reduce access latency of hot data via a **heterogeneous DRAM** design [Lee+ HPCA'13, Son+ ISCA'13]
- **VILLA**: Add fast subarrays as a **cache** in each bank

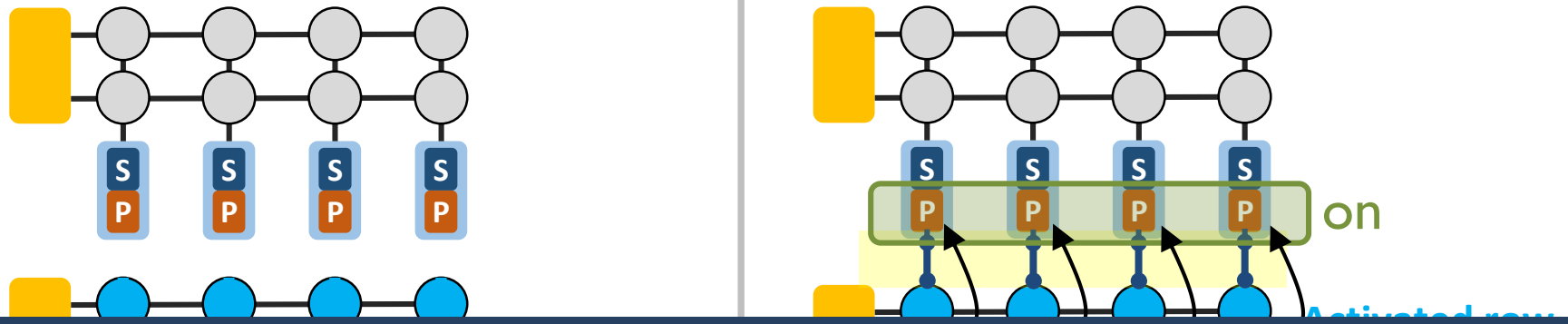


Challenge: VILLA cache requires frequent movement of data rows

Reduces hot data access latency by 2.2x at only 1.6% area overhead

3. Linked Precharge (LIP)

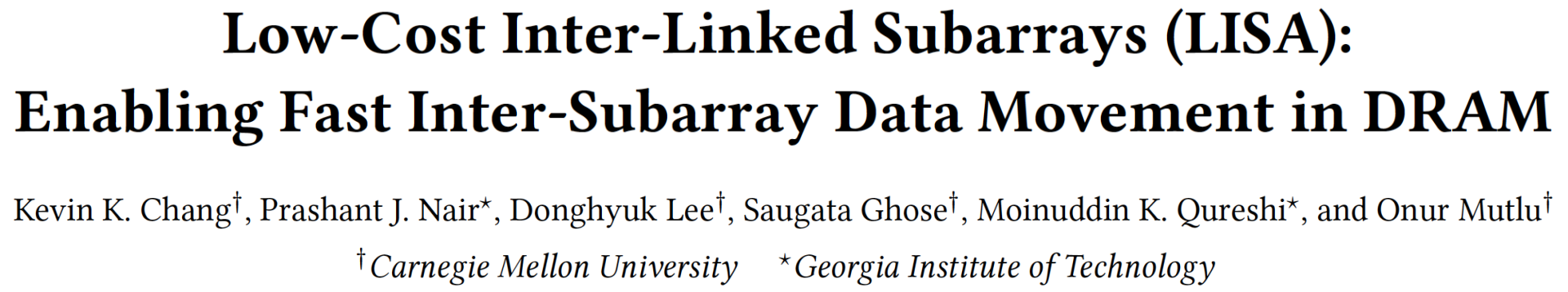
- **Problem**: The precharge time is limited by the strength of one precharge unit
- **Linked Precharge (LIP)**: LISA precharges a subarray using multiple precharge units



Reduces precharge latency by 2.6x (43% guardband)

More on LISA

- Kevin K. Chang, Prashant J. Nair, Saugata Ghose, Donghyuk Lee, Moinuddin K. Qureshi, and Onur Mutlu,
  "Low-Cost Inter-Linked Subarrays (LISA): Enabling Fast Inter-Subarray Data Movement in DRAM"
  *Proceedings of the 22nd International Symposium on High-Performance Computer Architecture (**HPCA**)*, Barcelona, Spain, March 2016.
  [Slides (pptx) (pdf)]
  [Source Code]



Low-Cost Inter-Linked Subarrays (LISA): Enabling Fast Inter-Subarray Data Movement in DRAM

Kevin K. Chang†, Prashant J. Nair⋆, Donghyuk Lee†, Saugata Ghose†, Moinuddin K. Qureshi⋆, and Onur Mutlu†

†*Carnegie Mellon University* ⋆*Georgia Institute of Technology*

What Causes the Long DRAM Latency?

Why the Long Memory Latency?

- Reason 1: Design of DRAM Micro-architecture
  - Goal: Maximize capacity/area, not minimize latency

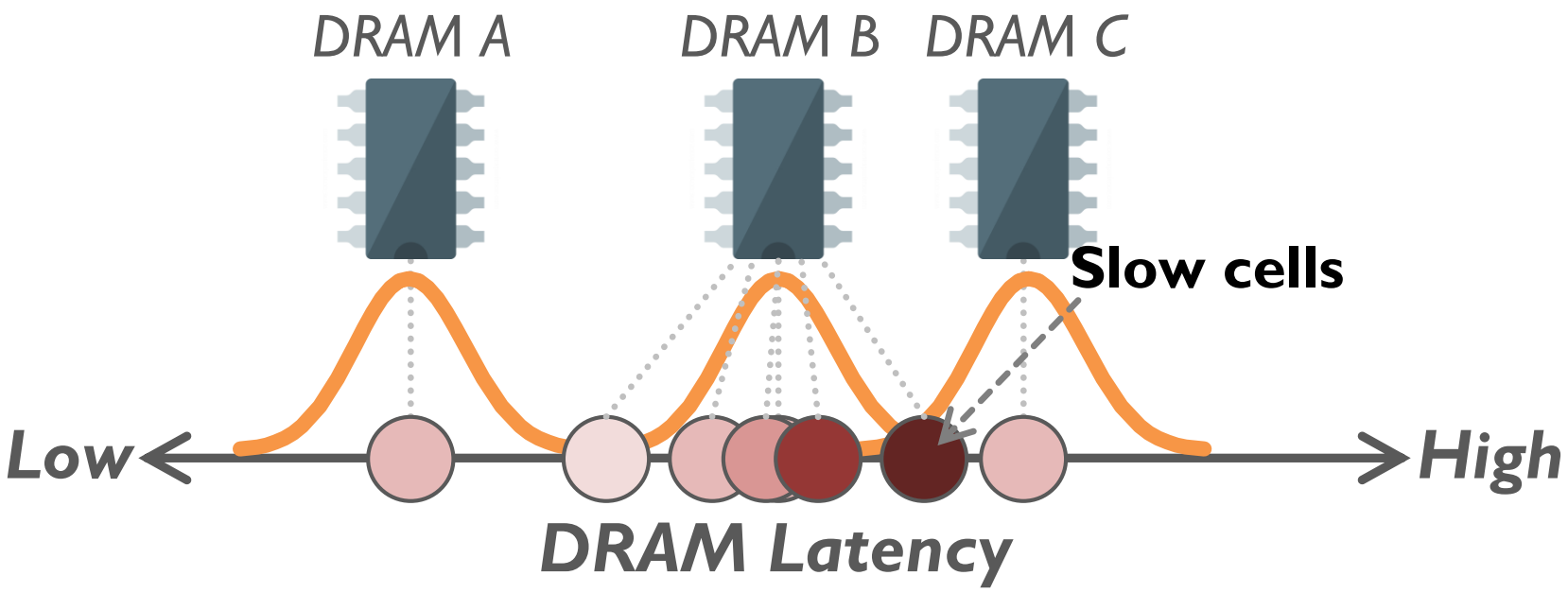
- Reason 2: "One size fits all" approach to latency specification
  - Same latency parameters for all temperatures
  - Same latency parameters for all DRAM chips
  - Same latency parameters for all parts of a DRAM chip
  - Same latency parameters for all supply voltage levels
  - Same latency parameters for all application data
  - …

Tackling the Fixed Latency Mindset

- Reliable operation latency is actually very heterogeneous
  - Across temperatures, chips, parts of a chip, voltage levels, …
- Idea: Dynamically find out and use the lowest latency one can reliably access a memory location with
  - Adaptive-Latency DRAM [HPCA 2015]
  - Flexible-Latency DRAM [SIGMETRICS 2016]
  - Design-Induced Variation-Aware DRAM [SIGMETRICS 2017]
  - Voltron [SIGMETRICS 2017]
  - DRAM Latency PUF [HPCA 2018]
  - …
- We would like to find sources of latency heterogeneity and exploit them to minimize latency

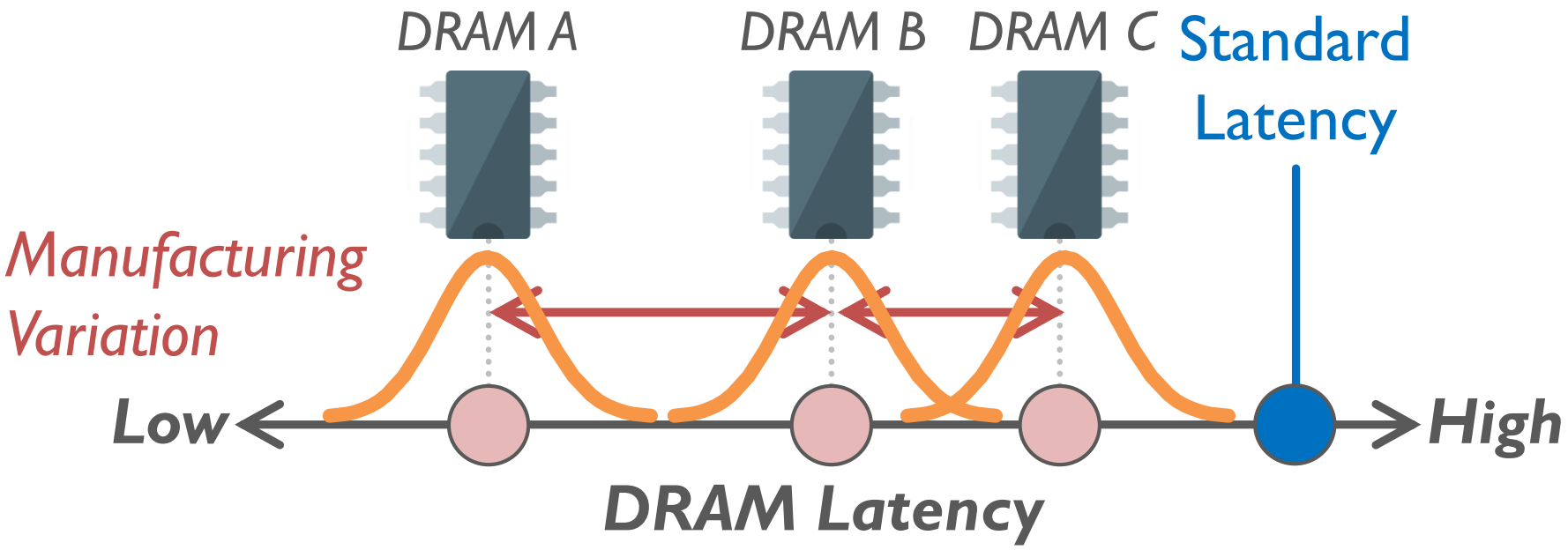
Latency Variation in Memory Chips

Heterogeneous manufacturing & operating conditions →
latency variation in timing parameters



Why is Latency High?

- DRAM latency: Delay as specified in DRAM standards
  - Doesn't reflect true DRAM device latency
- Imperfect manufacturing process → latency variation
- **High standard latency** chosen to increase yield

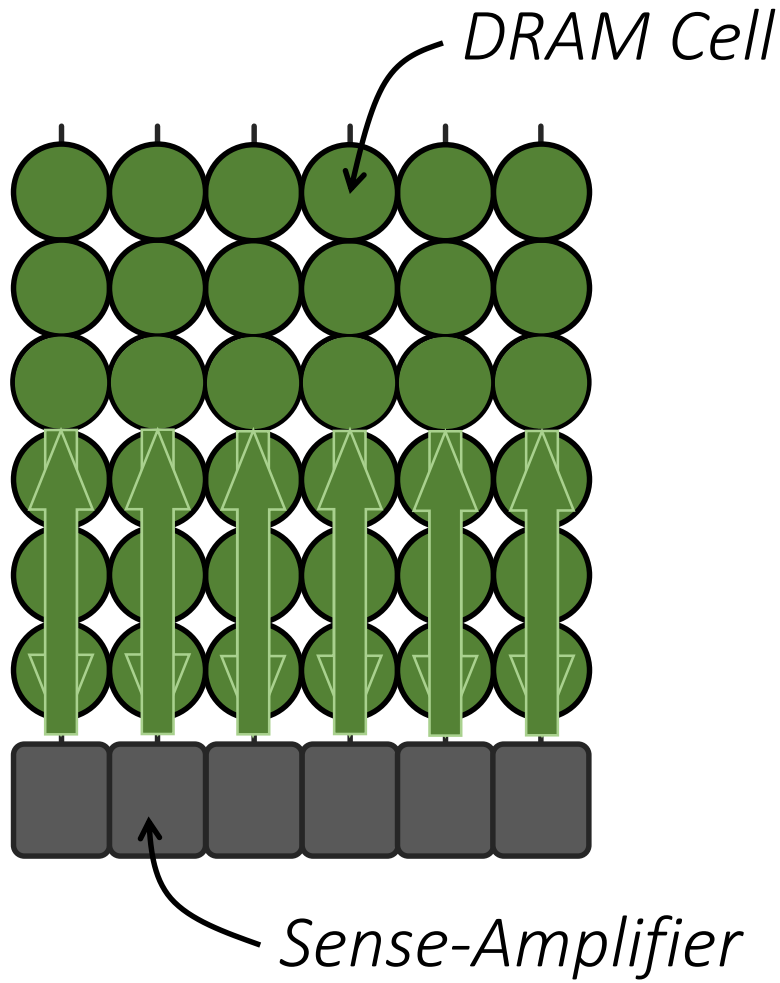


What Causes the Long Memory Latency?

- **Conservative timing margins!**
- DRAM timing parameters are set to cover the worst case
- Worst-case temperatures
  - 85 degrees vs. common-case
  - to enable a wide range of operating conditions
- Worst-case devices
  - DRAM cell with smallest charge across any acceptable device
  - to tolerate process variation at acceptable yield
- This leads to large timing margins for the common case

Understanding and Exploiting Variation in DRAM Latency

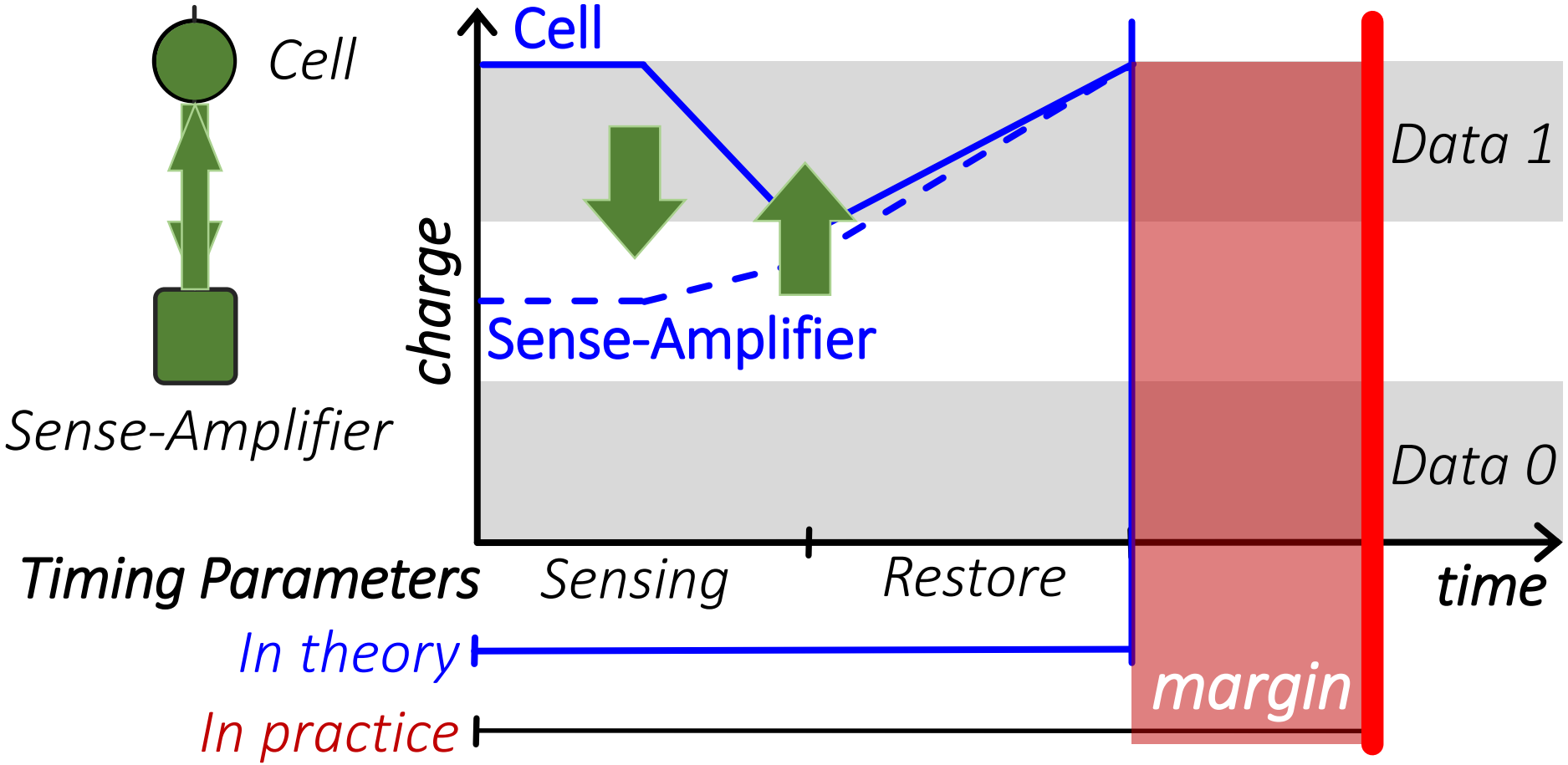
DRAM Stores Data as Charge



Three steps of charge movement

1. Sensing
2. Restore
3. Precharge

DRAM Charge over Time



Why does DRAM need the extra timing margin?

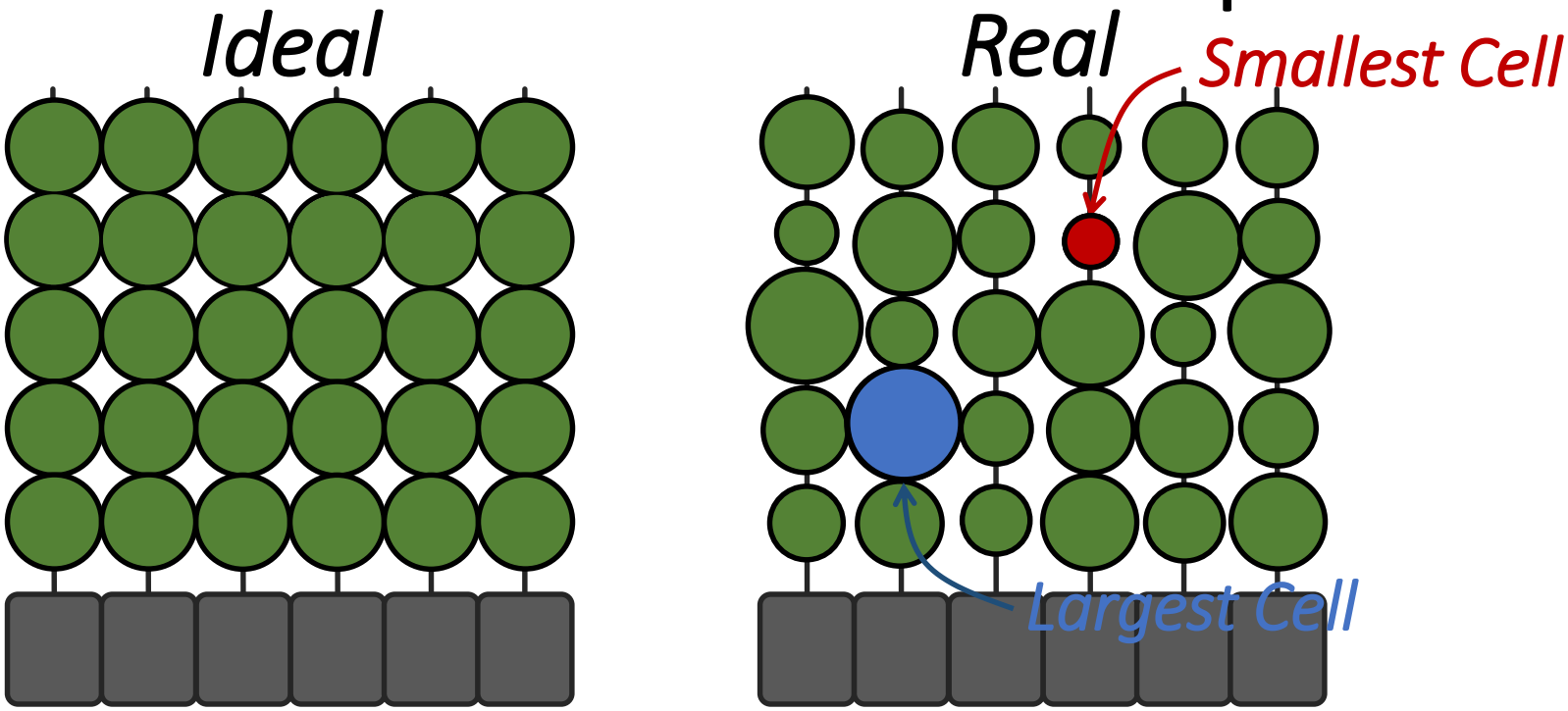
Two Reasons for Timing Margin

1. Process Variation

- DRAM cells are not equal
- Leads to extra timing margin for a cell that can store a large amount of charge

2. Temperature Dependence

DRAM Cells are Not Equal



Same Size ➔
Same Charge ➔
Same Latency

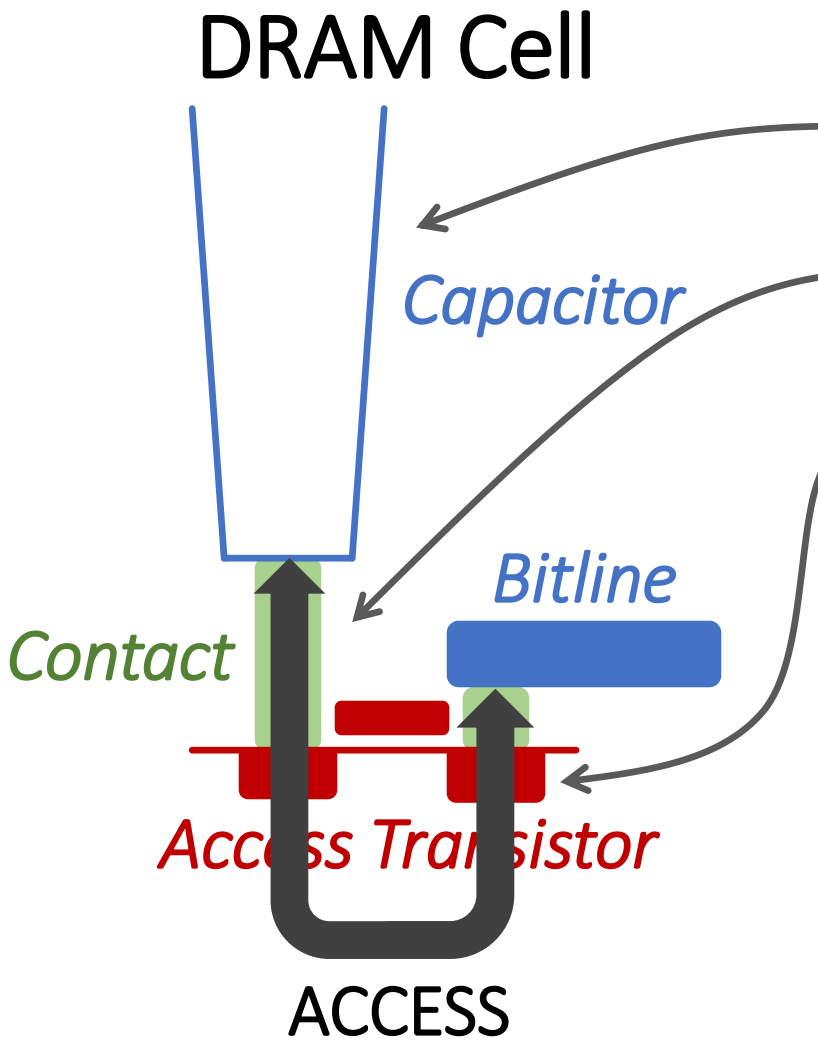
Different Size ➔
Different Charge ➔
Different Latency

Large variation in cell size

Large variation in charge

Large variation in access latency

Process Variation



1. Cell Capacitance
2. Contact Resistance
3. Transistor Performance

Small cell can store small charge

- *Small cell capacitance*
- *High contact resistance*
- *Slow access transistor*

➔ ***High access latency***

Two Reasons for Timing Margin

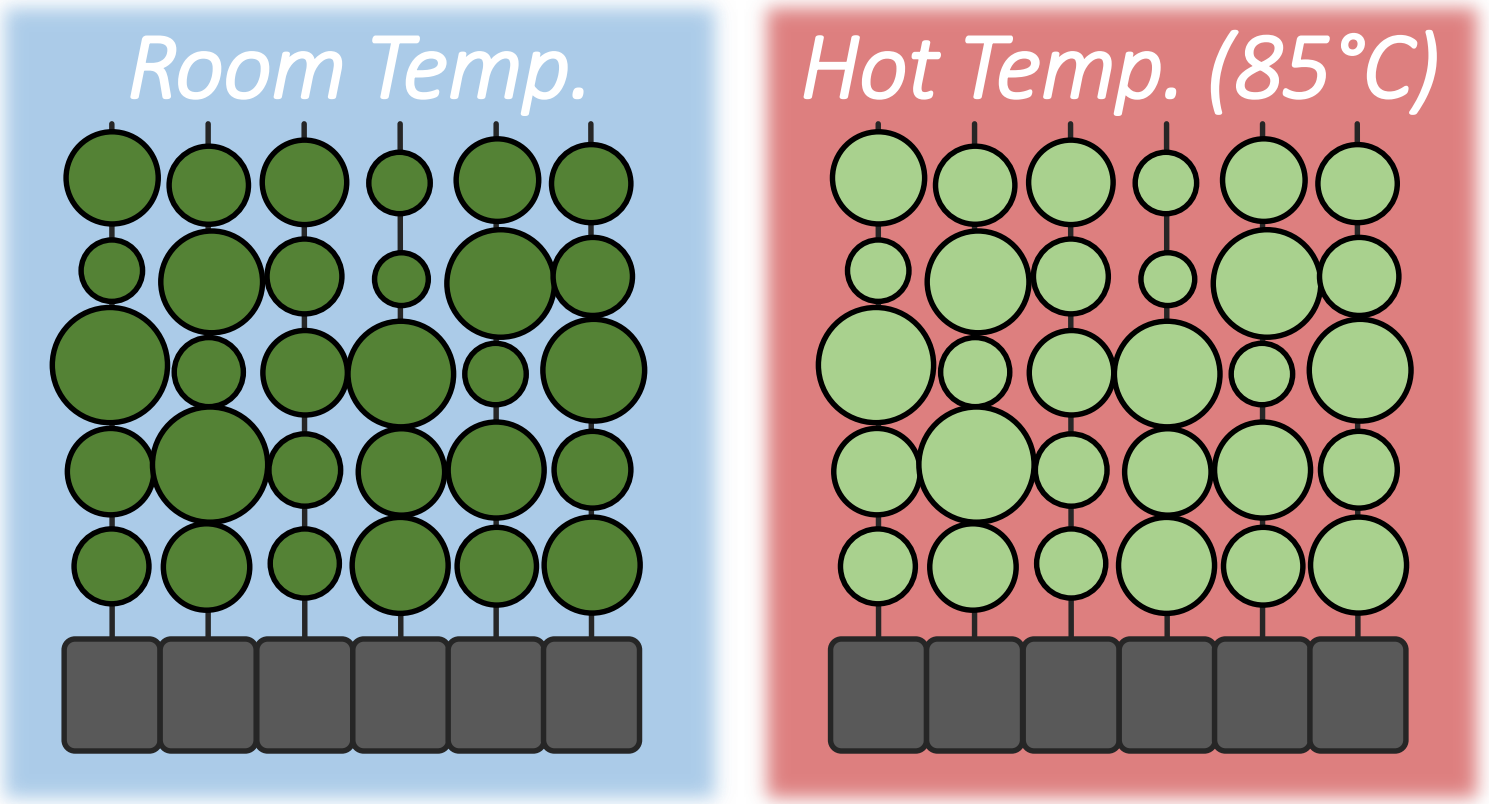
1. Process Variation

- DRAM cells are not equal
- Leads to extra timing margin for a cell that can store a large amount of charge

2. Temperature Dependence

- DRAM leaks more charge at higher temperature
- Leads to extra timing margin for cells that operate at low temperature

Charge Leakage Temperature



Cells store small charge at high temperature and large charge at low temperature

→ Large variation in access latency

DRAM Timing Parameters

- *DRAM timing parameters are dictated by* ***the worst-case***
  - The smallest cell with the smallest charge **in all DRAM products**
  - Operating at **the highest temperature**

- *Large timing margin for the common-case*

Adaptive-Latency DRAM [HPCA 2015]

- Idea: Optimize DRAM timing for the common case
  - Current temperature
  - Current DRAM module

- Why would this reduce latency?

  - A DRAM cell can store much more charge in the common case (low temperature, strong cell) than in the worst case

  - More charge in a DRAM cell
    → Faster sensing, charge restoration, precharging
    → Faster access (read, write, refresh, …)

Extra Charge → Reduced Latency

1. **Sensing**

   Sense **cells with extra charge** faster

   → Lower sensing latency

2. **Restore**

   No need to fully restore **cells with extra charge**

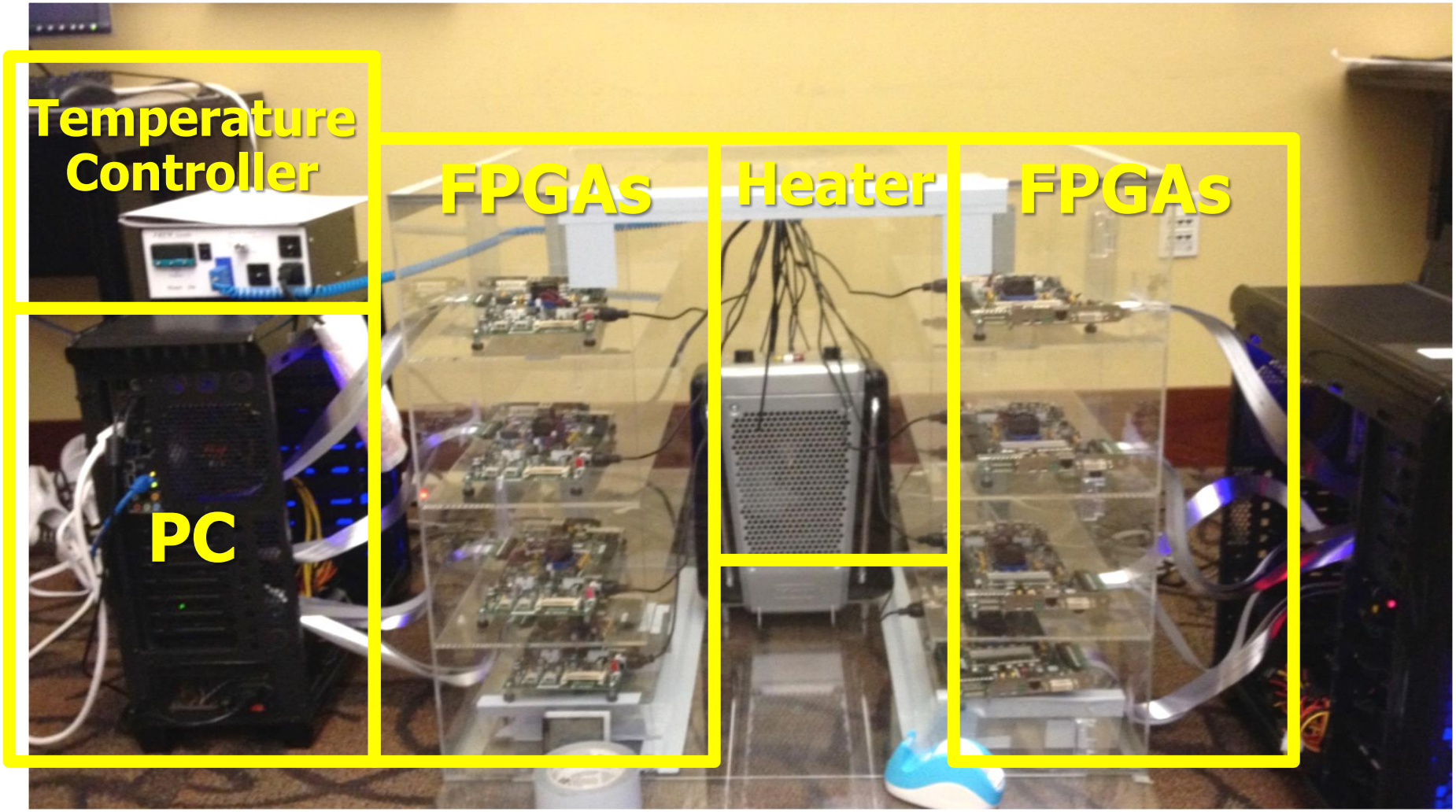
   → Lower restoration latency

3. **Precharge**

   No need to fully precharge bitlines for **cells with extra charge**

   → Lower precharge latency

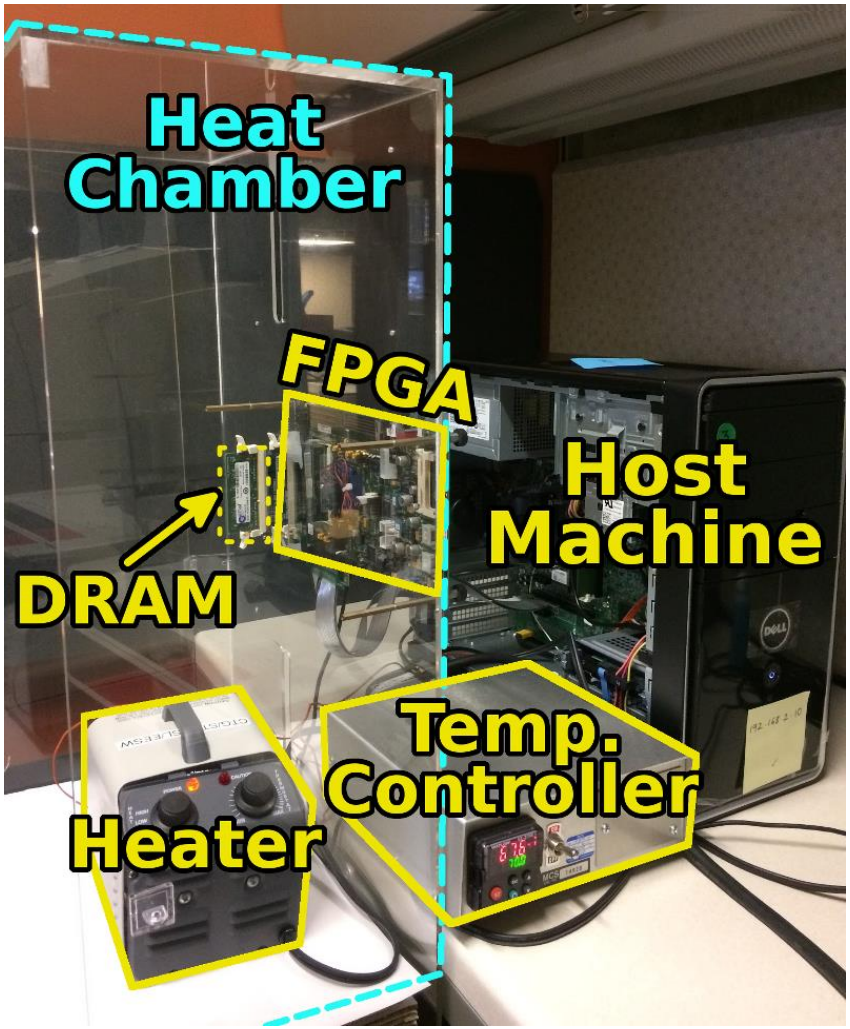
DRAM Characterization Infrastructure



Kim+, "Flipping Bits in Memory Without Accessing Them: An Experimental Study of DRAM Disturbance Errors," ISCA 2014.

DRAM Characterization Infrastructure

- Hasan Hassan et al., **SoftMC: A Flexible and Practical Open-Source Infrastructure for Enabling Experimental DRAM Studies**, HPCA 2017.



- **Flexible**
- **Easy to Use (C++ API)**
- **Open-source**

  github.com/CMU-SAFARI/SoftMC

SoftMC: Open Source DRAM Infrastructure

- https://github.com/CMU-SAFARI/SoftMC

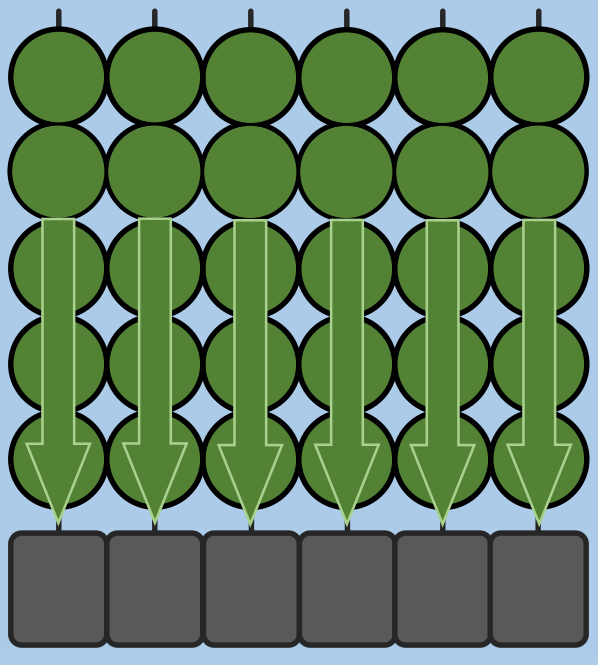
SoftMC: A Flexible and Practical Open-Source Infrastructure for Enabling Experimental DRAM Studies

Hasan Hassan[1,2,3] Nandita Vijaykumar[3] Samira Khan[4,3] Saugata Ghose[3] Kevin Chang[3]
Gennady Pekhimenko[5,3] Donghyuk Lee[6,3] Oguz Ergin[2] Onur Mutlu[1,3]

[1]*ETH Zürich* [2]*TOBB University of Economics & Technology* [3]*Carnegie Mellon University*
[4]*University of Virginia* [5]*Microsoft Research* [6]*NVIDIA Research*

Observation 1. Faster Sensing

Typical DIMM at Low Temperature



More Charge

Strong Charge Flow

Faster Sensing

115 DIMM Characterization

Timing
(tRCD)

17% ↓

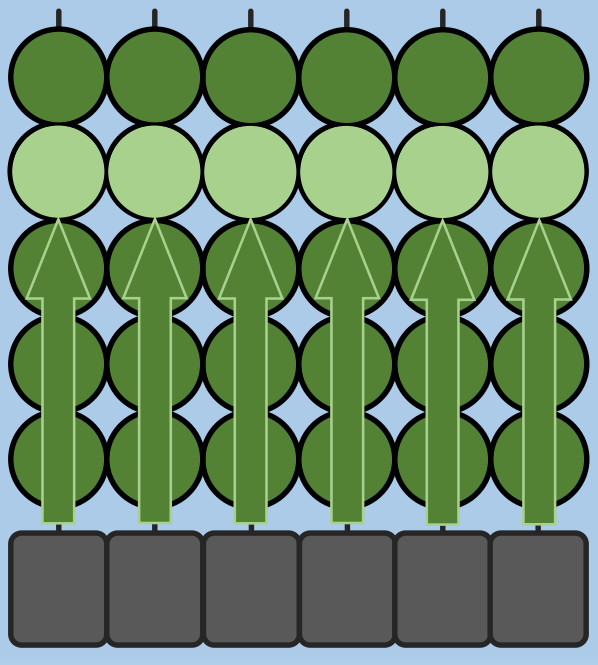
No Errors

Typical DIMM at Low Temperature

➔ *More charge* ➔ *Faster sensing*

Observation 2. Reducing Restore Time

Typical DIMM at Low Temperature



Less Leakage ➔ Extra Charge

No Need to Fully Restore Charge

115 DIMM Characterization

Read (tRAS)

37% ↓

Write (tWR)

54% ↓

No Errors

Typical DIMM at lower temperature

➔ *More charge* ➔ *Restore time reduction*

AL-DRAM

- *Key idea*
  - **Optimize DRAM timing parameters online**
- *Two components*
  - DRAM manufacturer provides multiple sets of reliable DRAM timing parameters at different temperatures for each DIMM
  - System monitors DRAM temperature & uses appropriate DRAM timing parameters

Lee+, "Adaptive-Latency DRAM: Optimizing DRAM Timing for the Common-Case," HPCA 2015.

DRAM Temperature

- *DRAM temperature measurement*
  - Server cluster: Operates at under 34°C
  - Desktop: Operates at under 50°C
  - *DRAM standard optimized for 85°C*

DRAM operates at low temperatures in the common-case

- *Previous works – Maintain low DRAM temperature*
  - David+ ICAC 2011
  - Liu+ ISCA 2007
  - Zhu+ ITHERM 2008

Latency Reduction Summary of 115 DIMMs

- *Latency reduction for read & write (55°C)*
  - *Read Latency:* ***32.7%***
  - *Write Latency:* ***55.1%***

- *Latency reduction for each timing parameter (55°C)*
  - *Sensing:* ***17.3%***
  - *Restore:* ***37.3%*** *(read),* ***54.8%*** *(write)*
  - *Precharge:* ***35.2%***

Lee+, "Adaptive-Latency DRAM: Optimizing DRAM Timing for the Common-Case," HPCA 2015.

AL-DRAM: Real System Evaluation

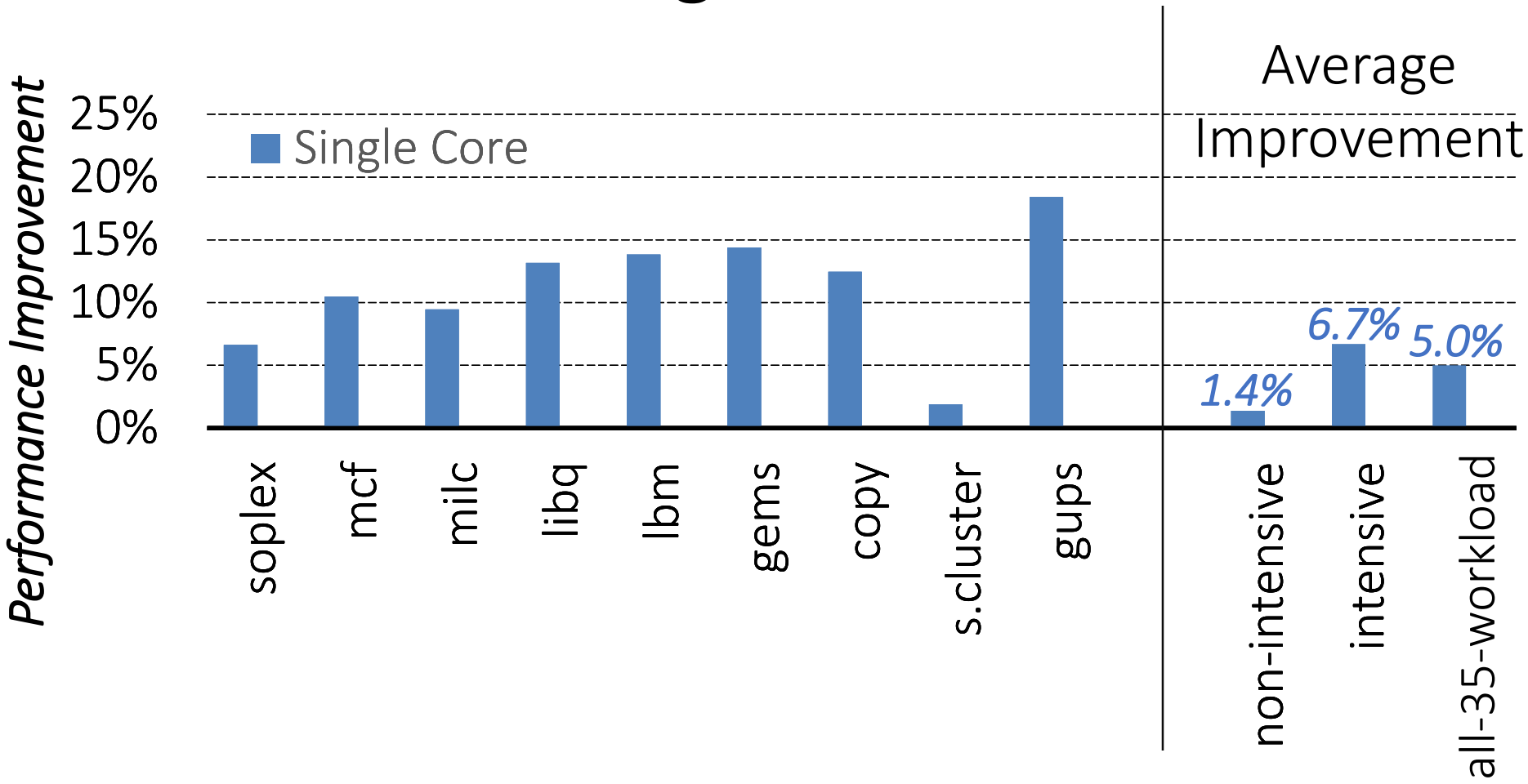
- *System*
  - *CPU: AMD 4386 (8 Cores, 3.1GHz, 8MB LLC)*

D18F2x200_dct[0]_mp[1:0] DDR3 DRAM Timing 0

Reset: 0F05_0505h. See 2.9.3 [DCT Configuration Registers].

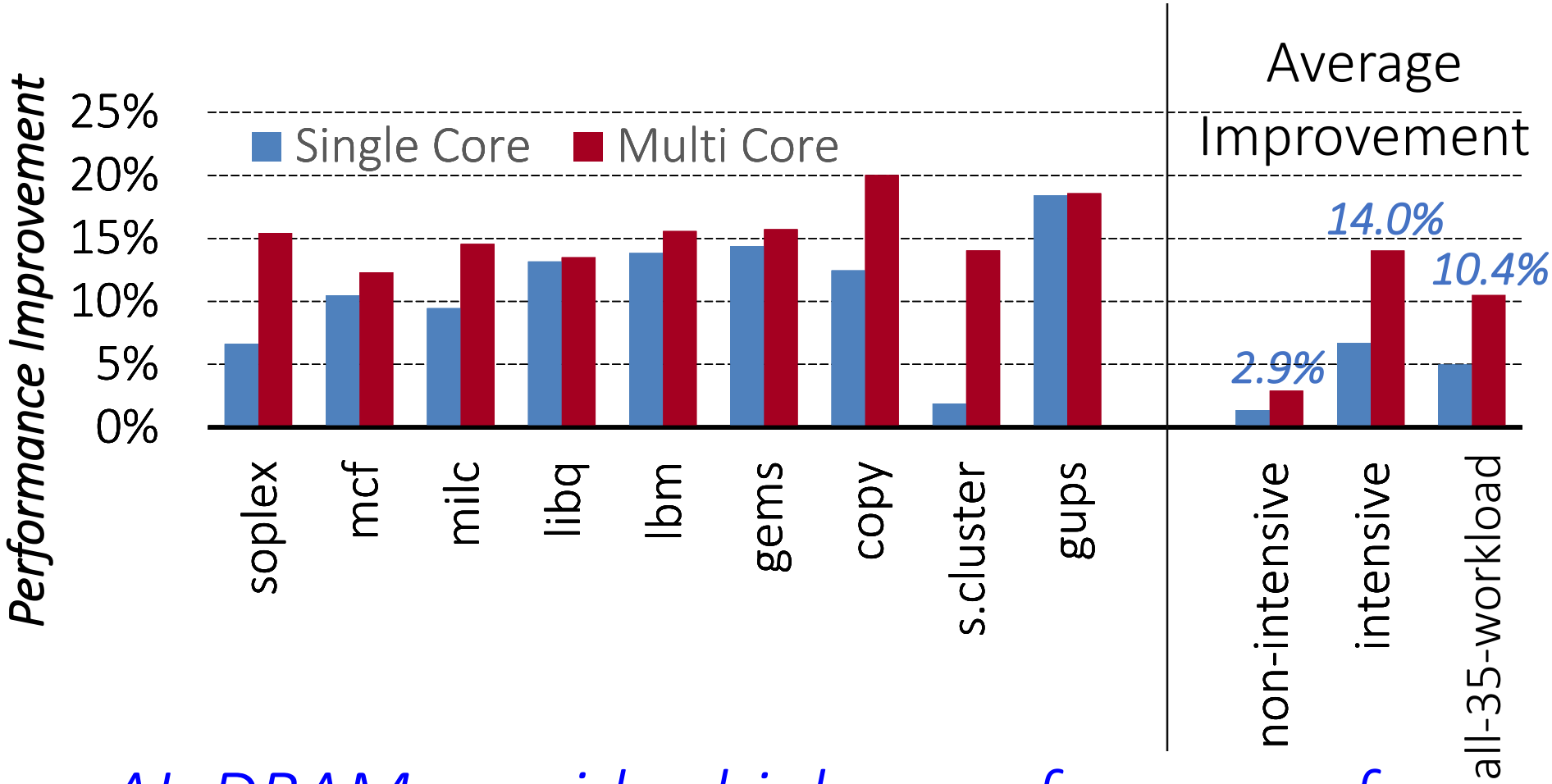
Bits	Description
31:30	Reserved.
29:24	**Tras: row active strobe**. Read-write. BIOS: See 2.9.7.5 [SPD ROM-Based Configuration]. Specifies the minimum time in memory clock cycles from an activate command to a precharge command, both to the same chip select bank. Bits — Description 07h-00h — Reserved 2Ah-08h — <Tras> clocks 3Fh-2Bh — Reserved
23:21	Reserved.
20:16	**Trp: row precharge time**. Read-write. BIOS: See 2.9.7.5 [SPD ROM-Based Configuration]. Specifies the minimum time in memory clock cycles from a precharge command to an activate command or auto refresh command, both to the same bank.

AL-DRAM: Single-Core Evaluation



*AL-DRAM **improves performance** on a real system*

AL-DRAM: Multi-Core Evaluation



AL-DRAM provides higher performance for

multi-programmed & multi-threaded workloads

Reducing Latency Also Reduces Energy

- AL-DRAM reduces DRAM power consumption by 5.8%
- Major reason: reduction in row activation time

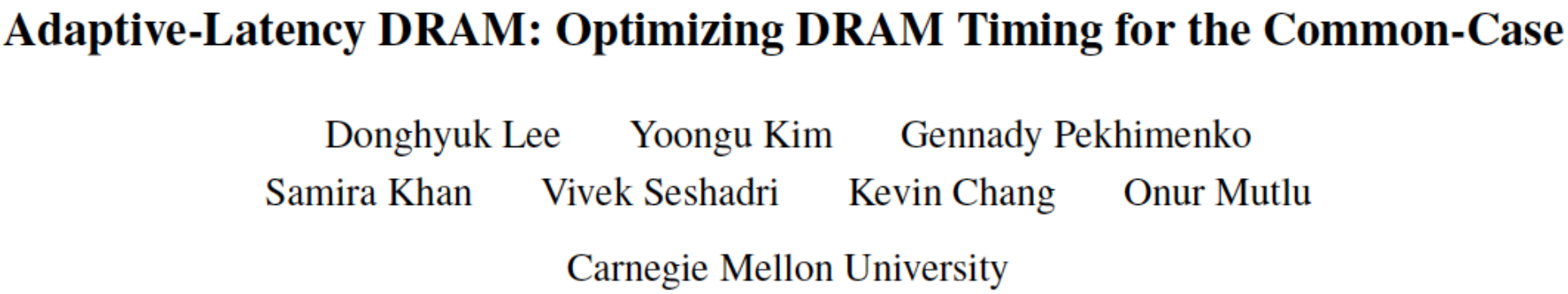
AL-DRAM: Advantages & Disadvantages

- Advantages
  - + Simple mechanism to reduce latency
  - + Significant system performance and energy benefits
    - + Benefits higher at low temperature
  - + Low cost, low complexity

- Disadvantages
  - - Need to determine reliable operating latencies for different temperatures and different DIMMs → higher testing cost
    - (might not be that difficult for low temperatures)

More on AL-DRAM

- Donghyuk Lee, Yoongu Kim, Gennady Pekhimenko, Samira Khan, Vivek Seshadri, Kevin Chang, and Onur Mutlu,
  "Adaptive-Latency DRAM: Optimizing DRAM Timing for the Common-Case"
  *Proceedings of the 21st International Symposium on High-Performance Computer Architecture (**HPCA**)*, Bay Area, CA, February 2015.
  [Slides (pptx) (pdf)] [Full data sets]



Adaptive-Latency DRAM: Optimizing DRAM Timing for the Common-Case

Donghyuk Lee Yoongu Kim Gennady Pekhimenko
Samira Khan Vivek Seshadri Kevin Chang Onur Mutlu

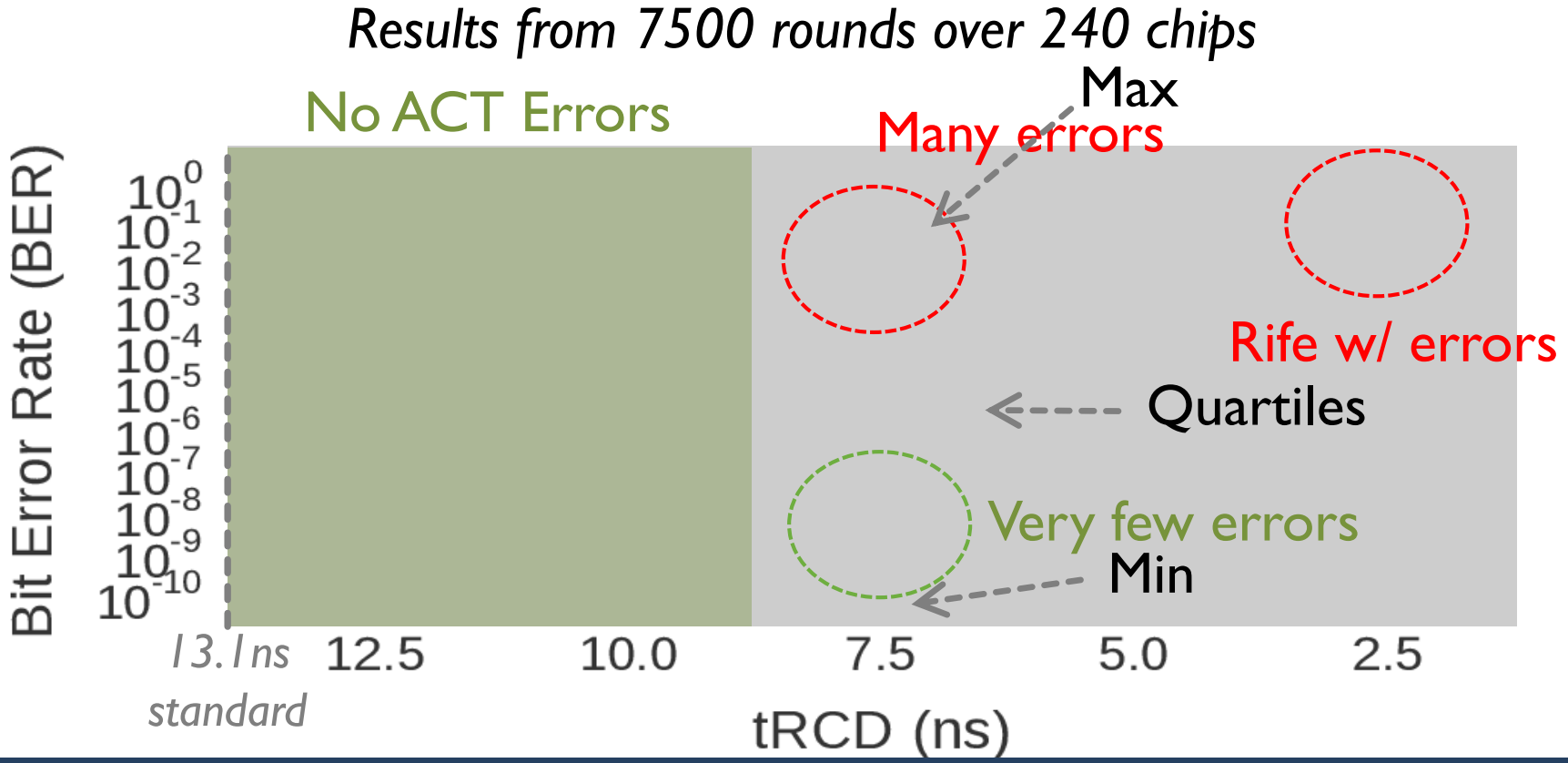
Carnegie Mellon University

Different Types of Latency Variation

- AL-DRAM exploits latency variation
  - Across time (different temperatures)
  - Across chips

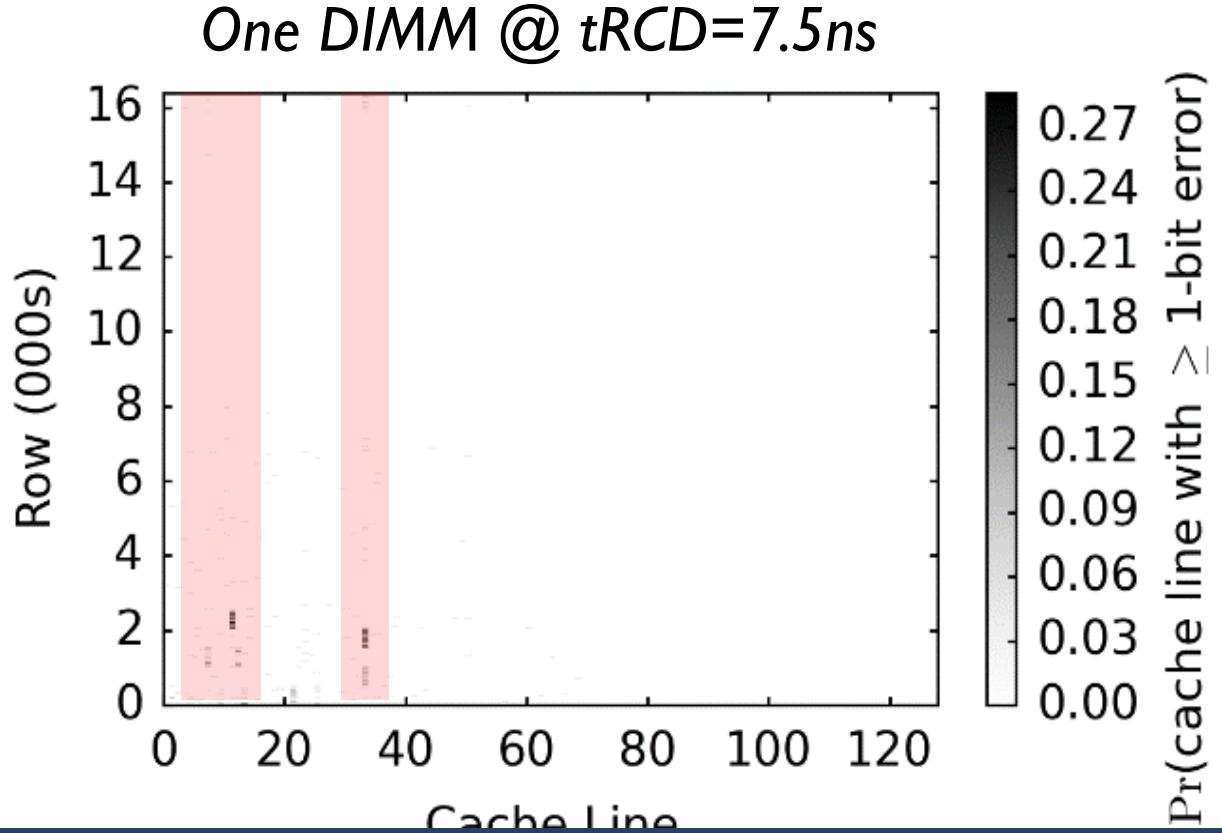
- Is there also latency variation within a chip?
  - Across different parts of a chip

Variation in Activation Errors



Modern DRAM chips exhibit significant variation in activation latency

Spatial Locality of Activation Errors



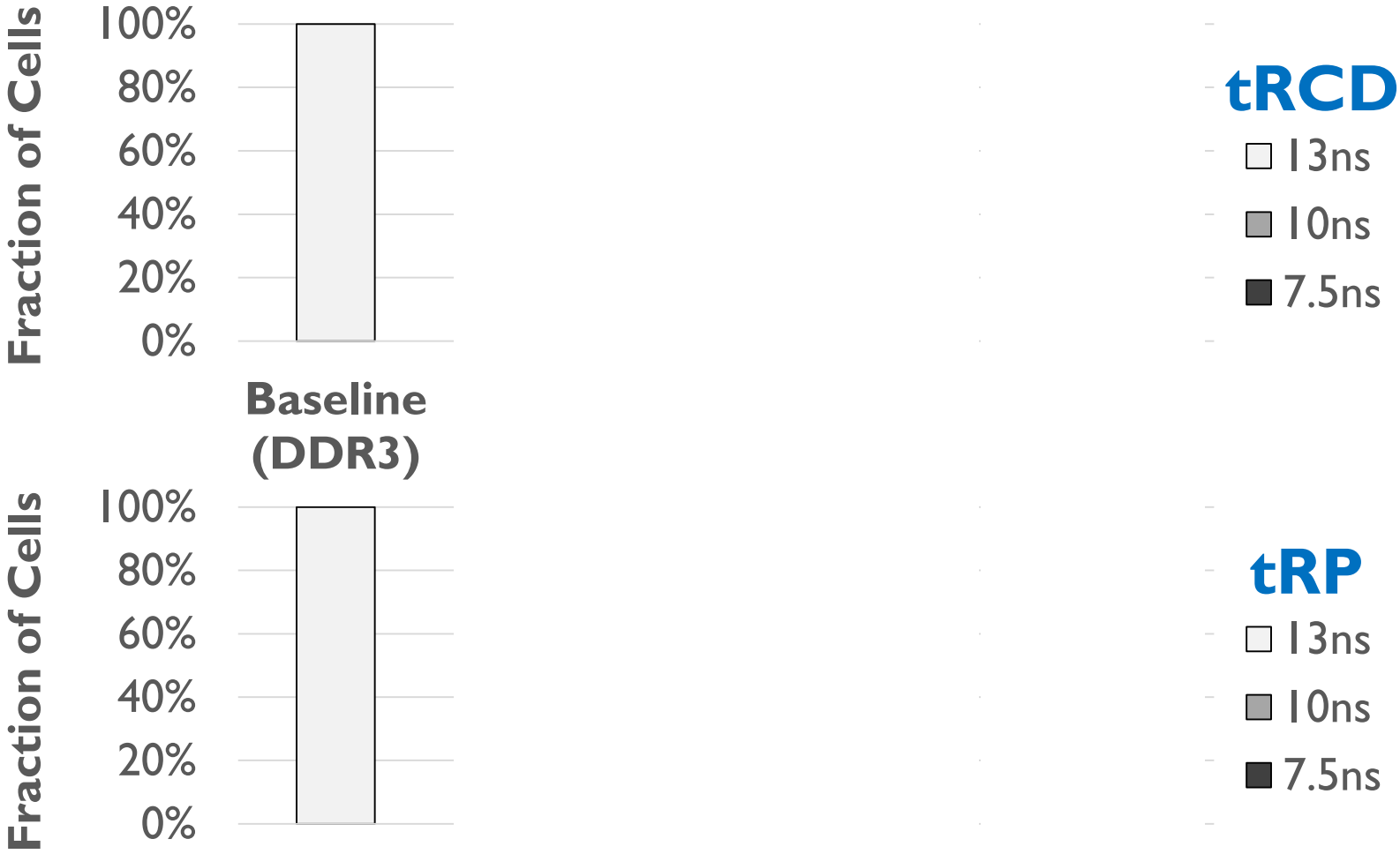
Activation errors are concentrated at certain columns of cells

Mechanism to Reduce DRAM Latency

- **Observation:** DRAM timing errors (slow DRAM cells) are concentrated on certain regions
- **Flexible-LatencY (FLY) DRAM**
  - A software-transparent design that reduces latency
- **Key idea**:
  1) Divide memory into regions of different latencies
  2) *Memory controller:* Use lower latency for regions without slow cells; higher latency for other regions

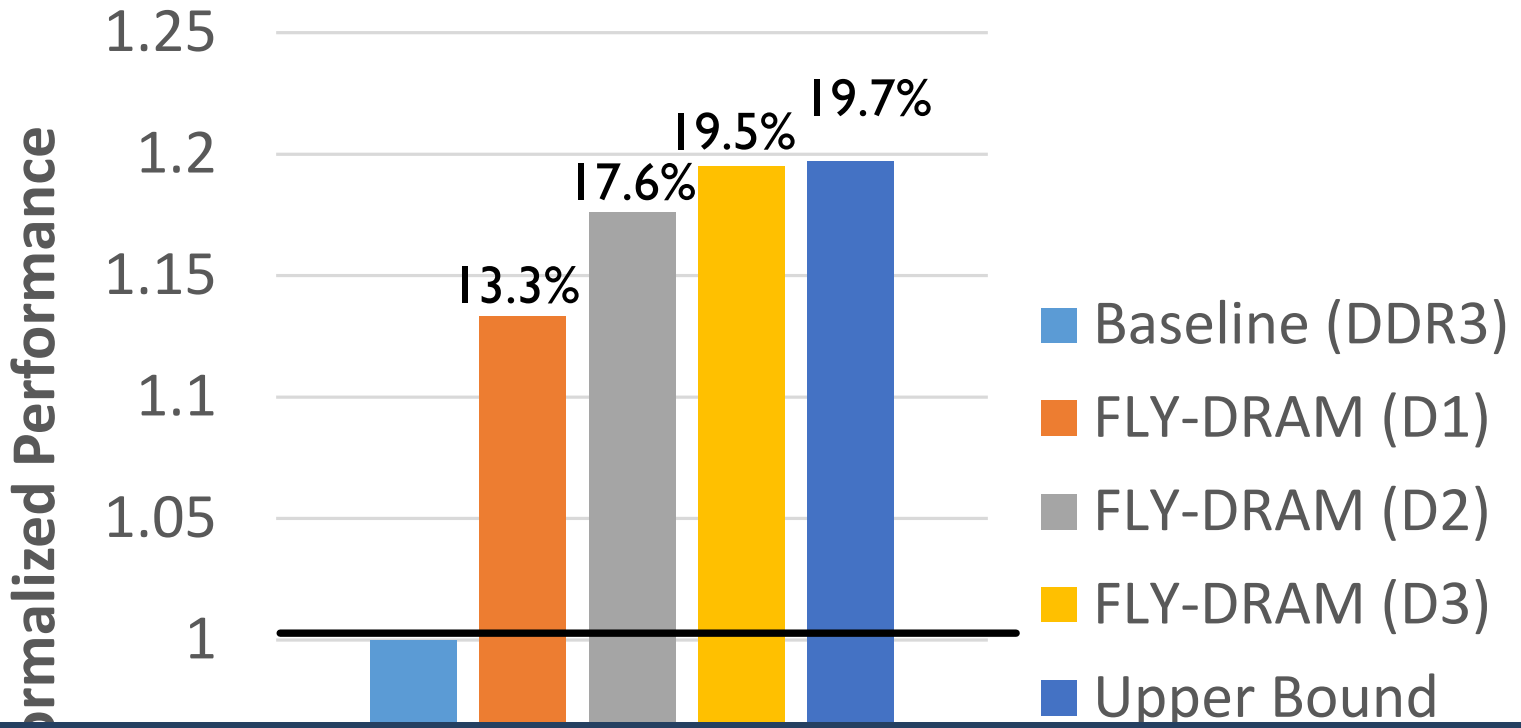
Chang+, "**Understanding Latency Variation in Modern DRAM Chips: Experimental Characterization, Analysis, and Optimization"**," SIGMETRICS 2016.

FLY-DRAM Configurations



Chang+, "**Understanding Latency Variation in Modern DRAM Chips: Experimental Characterization, Analysis, and Optimization**," SIGMETRICS 2016.

Results



FLY-DRAM improves performance by exploiting spatial latency variation in DRAM

Chang+, "**Understanding Latency Variation in Modern DRAM Chips: Experimental Characterization, Analysis, and Optimization**," SIGMETRICS 2016.

FLY-DRAM: Advantages & Disadvantages

- Advantages

  + Reduces latency significantly

    + Exploits significant within-chip latency variation

- Disadvantages

  - Need to determine reliable operating latencies for different parts of a chip → higher testing cost

  - Slightly more complicated controller

Analysis of Latency Variation in DRAM Chips

- Kevin Chang, Abhijith Kashyap, Hasan Hassan, Samira Khan, Kevin Hsieh, Donghyuk Lee, Saugata Ghose, Gennady Pekhimenko, Tianshi Li, and Onur Mutlu,
  "Understanding Latency Variation in Modern DRAM Chips: Experimental Characterization, Analysis, and Optimization"
  *Proceedings of the ACM International Conference on Measurement and Modeling of Computer Systems (**SIGMETRICS**)*, Antibes Juan-Les-Pins, France, June 2016.
  [Slides (pptx) (pdf)]
  [Source Code]

Understanding Latency Variation in Modern DRAM Chips: Experimental Characterization, Analysis, and Optimization

Kevin K. Chang[1] Abhijith Kashyap[1] Hasan Hassan[1,2]
Saugata Ghose[1] Kevin Hsieh[1] Donghyuk Lee[1] Tianshi Li[1,3]
Gennady Pekhimenko[1] Samira Khan[4] Onur Mutlu[5,1]

[1]Carnegie Mellon University [2]TOBB ETÜ [3]Peking University [4]University of Virginia [5]ETH Zürich

Computer Architecture

Lecture 10b: Memory Latency

Prof. Onur Mutlu
ETH Zürich

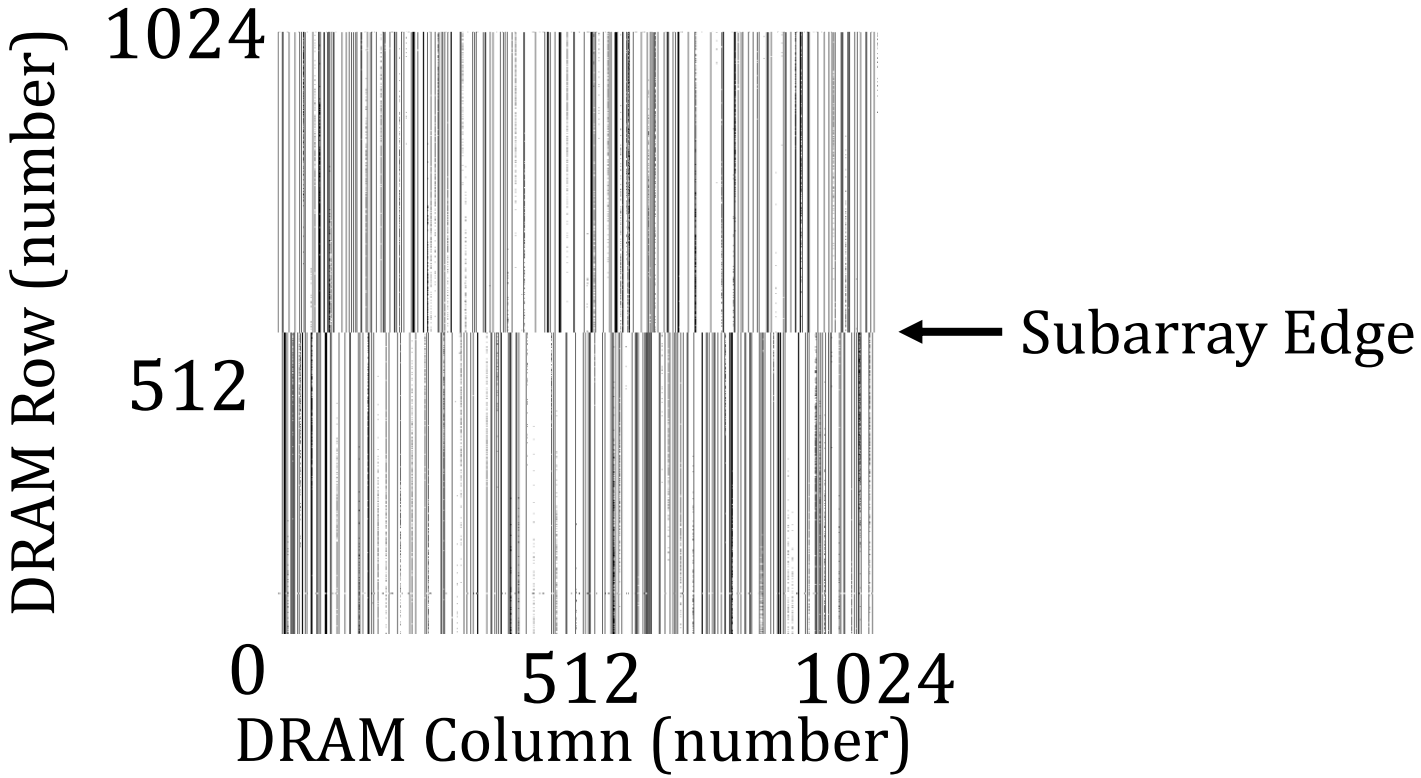
Fall 2018

18 October 2018

We did not cover the following slides in lecture.
These are for your benefit.

Spatial Distribution of Failures

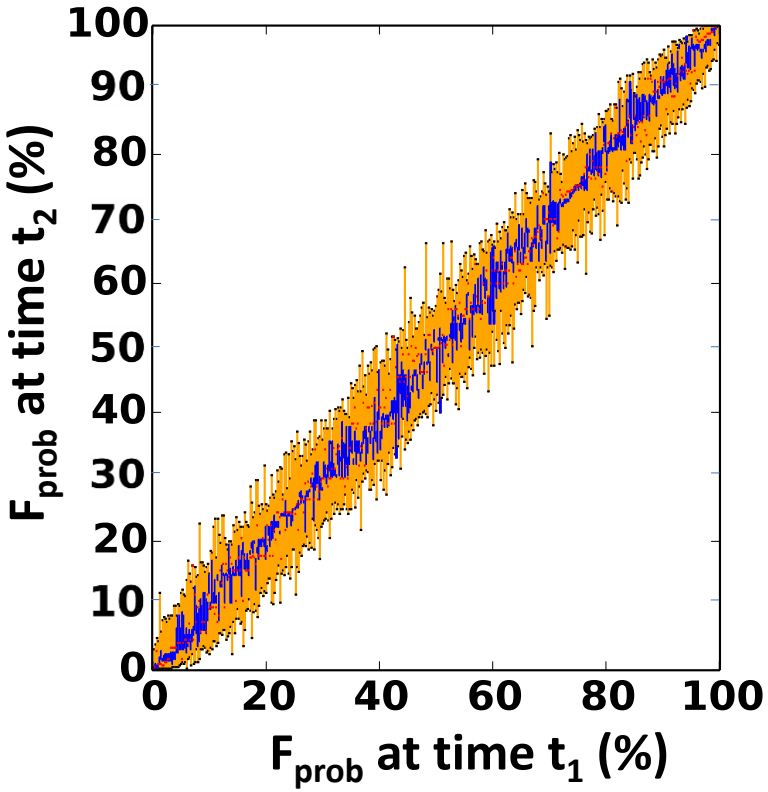
How are activation failures spatially distributed in DRAM?



Activation failures are **highly constrained** to local bitlines

Short-term Variation

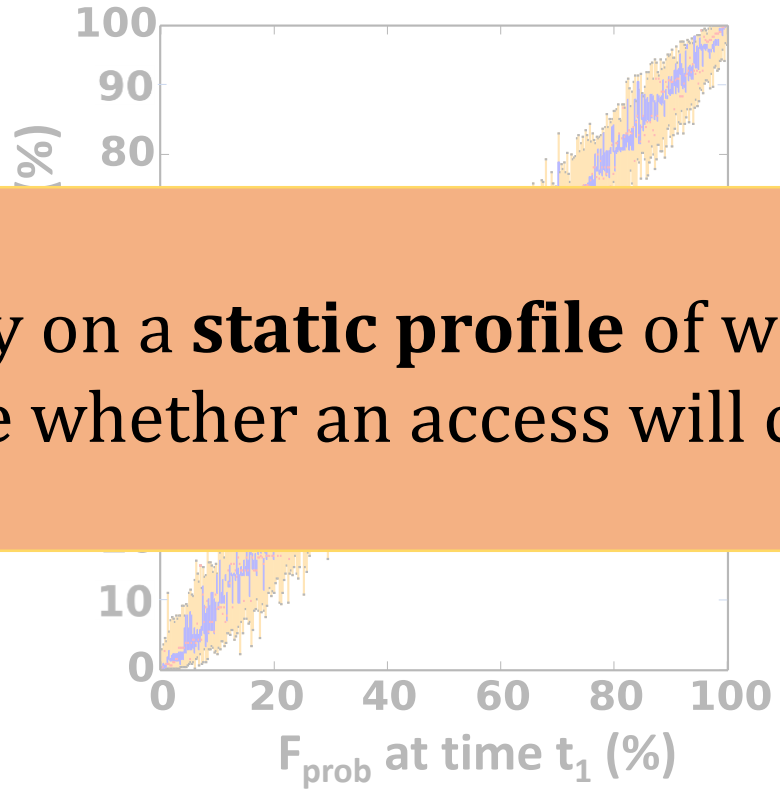
Does a bitline's probability of failure change over time?



A **weak bitline** is likely to remain **weak** and
a **strong bitline** is likely to remain **strong** over time

Short-term Variation

Does a bitline's probability of failure change over time?

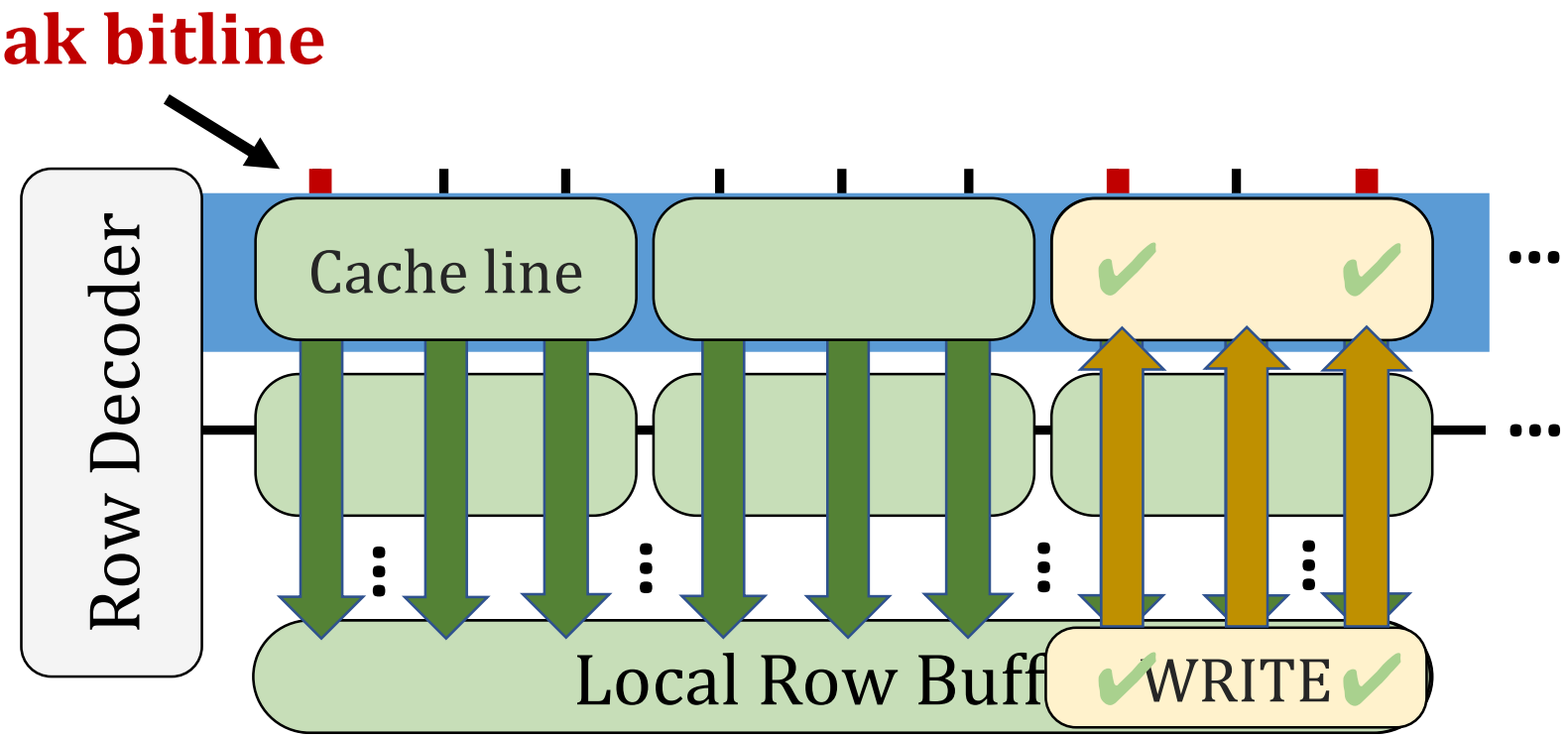


We can rely on a **static profile** of weak bitlines to determine whether an access will cause failures

A **weak bitline** is likely to remain **weak** and a **strong bitline** is likely to remain **strong** over time

Write Operations

How are write operations affected by reduced $\mathbf{t_{RCD}}$?



We can reliably issue write operations with significantly reduced $\mathbf{t_{RCD}}$ (e.g., by 77%)

Solar-DRAM

Uses a **static profile of weak subarray columns**

- Identifies subarray columns as weak or strong
- Obtained in a one-time profiling step

Three Components

1. Variable-latency cache lines (VLC)
2. Reordered subarray columns (RSC)
3. Reduced latency for writes (RLW)

Solar-DRAM

Uses a **static profile of weak subarray columns**

- Identifies subarray columns as weak or strong
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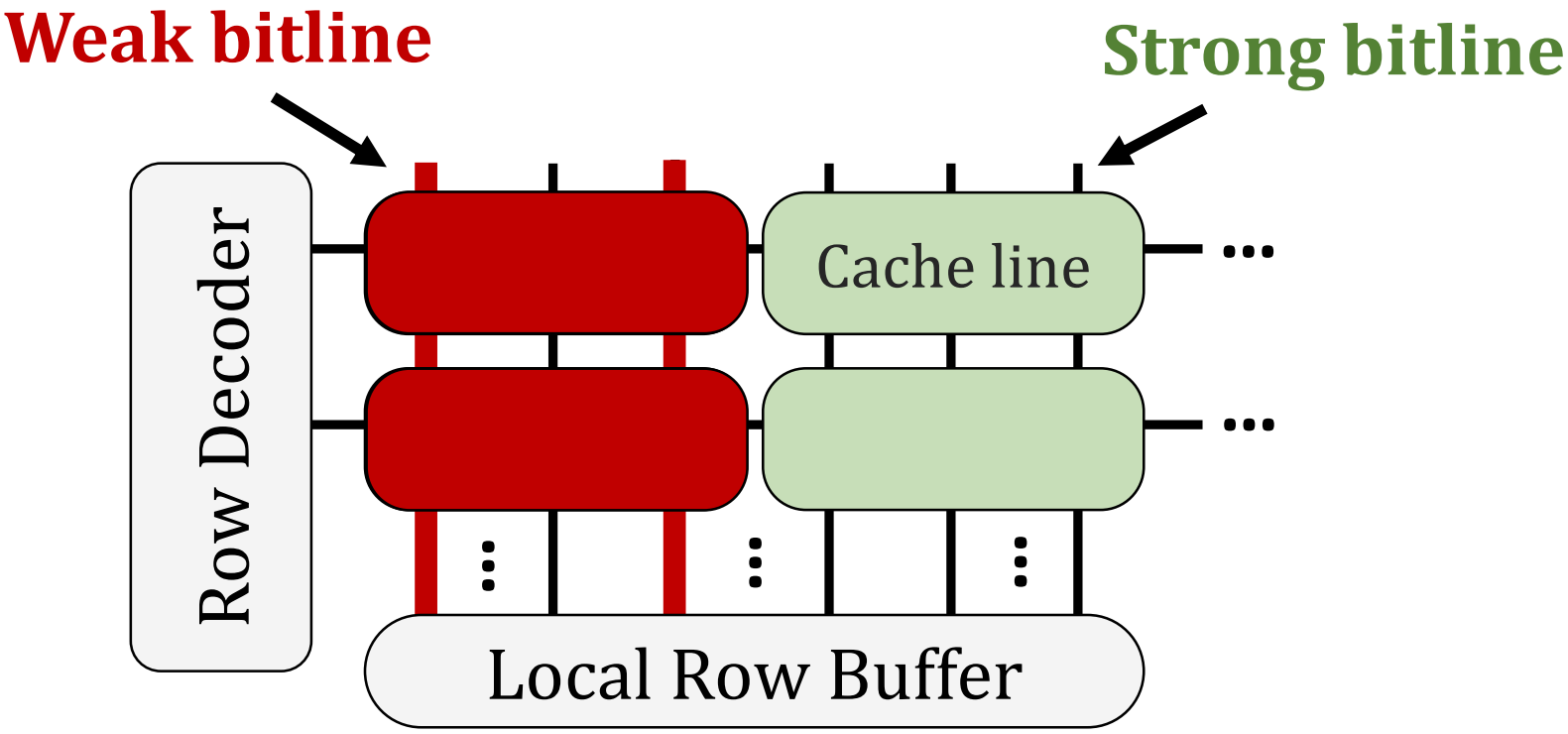
Three Components

1. Variable-latency cache lines (VLC)
2. Reordered subarray columns (RSC)
3. Reduced latency for writes (RLW)

Solar-DRAM: VLC (I)



Identify cache lines comprised of **strong bitlines**

Access such cache lines with a **reduced t_{RCD}**

Solar-DRAM

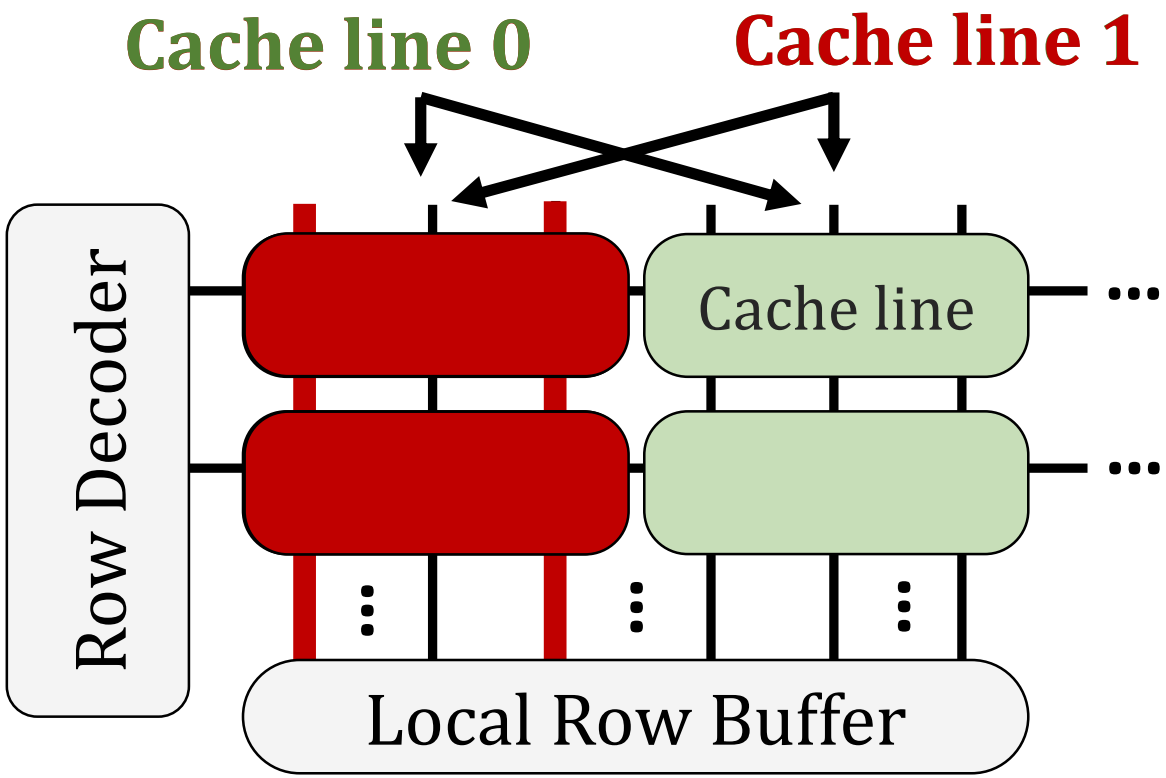
Uses a **static profile of weak subarray columns**

- Identifies subarray columns as weak or strong
- Obtained in a one-time profiling step

Three Components

1. Variable-latency cache lines (VLC)
2. Reordered subarray columns (RSC)
3. Reduced latency for writes (RLW)

Solar-DRAM: RSC (II)



Remap cache lines across DRAM at the memory controller level so cache line 0 will likely map to a **strong** cache line

Solar-DRAM

Uses a **static profile of weak subarray columns**

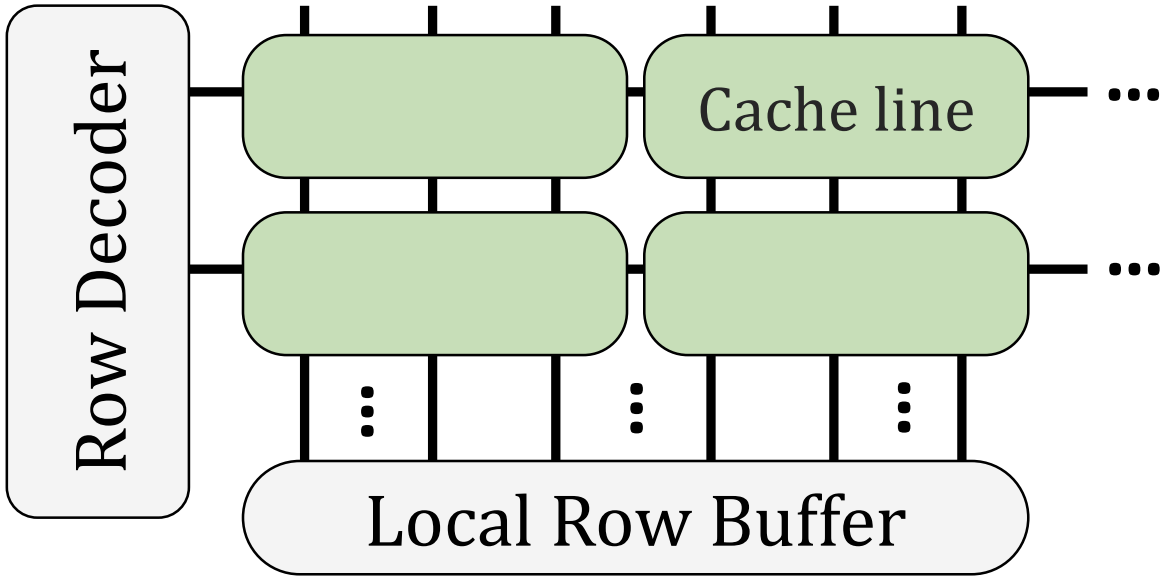
- Identifies subarray columns as weak or strong
- Obtained in a one-time profiling step

Three Components

1. Variable-latency cache lines (VLC)
2. Reordered subarray columns (RSC)
3. Reduced latency for writes (RLW)

Solar-DRAM: RLW (III)

All bitlines are strong when issuing writes



Write to all locations in DRAM with a significantly reduced $\mathbf{t_{RCD}}$ (e.g., by 77%)

More on Solar-DRAM

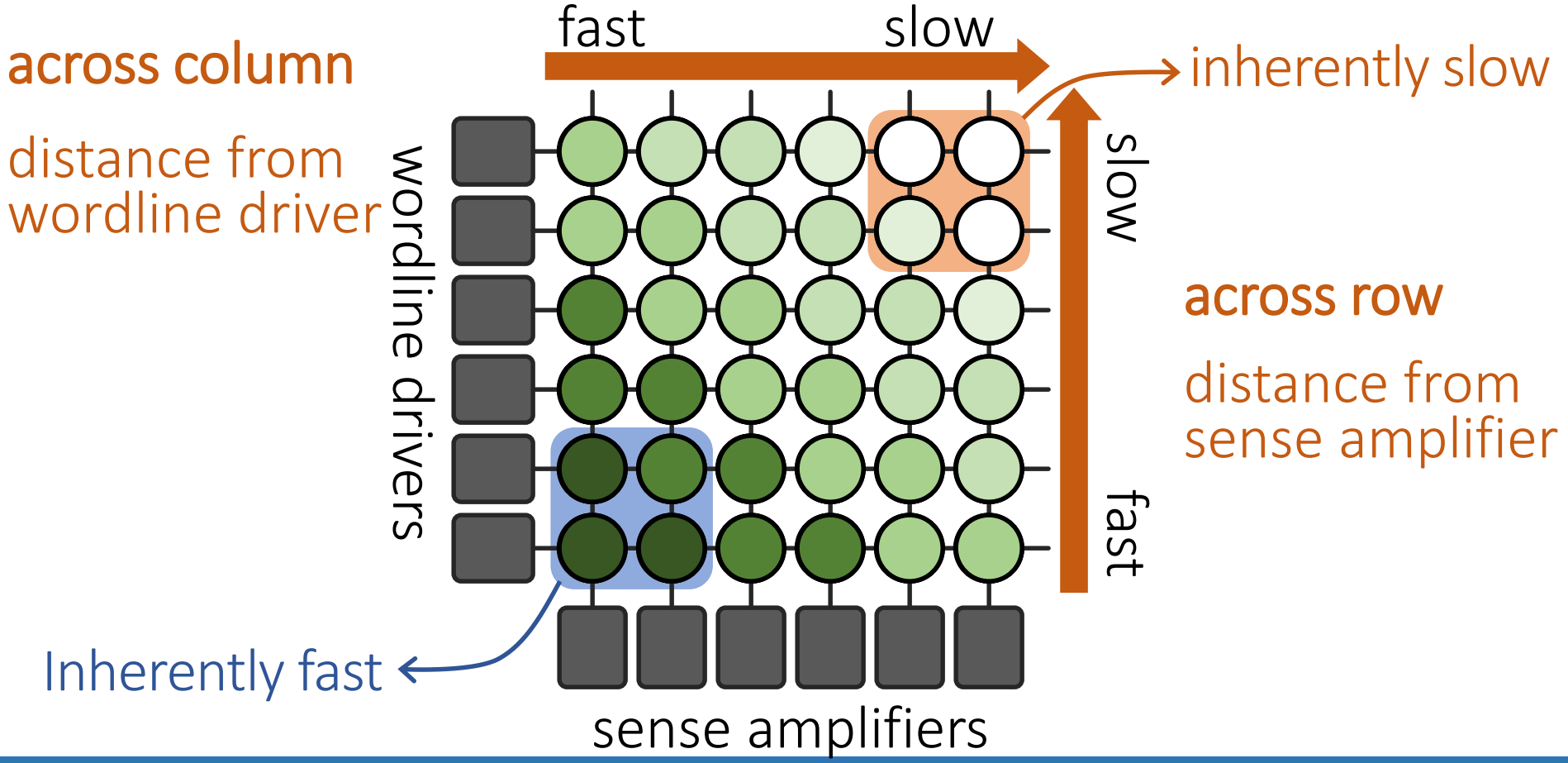
- Jeremie S. Kim, Minesh Patel, Hasan Hassan, and Onur Mutlu,
  "Solar-DRAM: Reducing DRAM Access Latency by Exploiting the Variation in Local Bitlines"
  *Proceedings of the 36th IEEE International Conference on Computer Design (**ICCD**)*, Orlando, FL, USA, October 2018.

Solar-DRAM: Reducing DRAM Access Latency by Exploiting the Variation in Local Bitlines

Jeremie S. Kim[‡§] Minesh Patel[§] Hasan Hassan[§] Onur Mutlu[§‡]
[‡]Carnegie Mellon University [§]ETH Zürich

Why Is There Spatial Latency Variation Within a Chip?

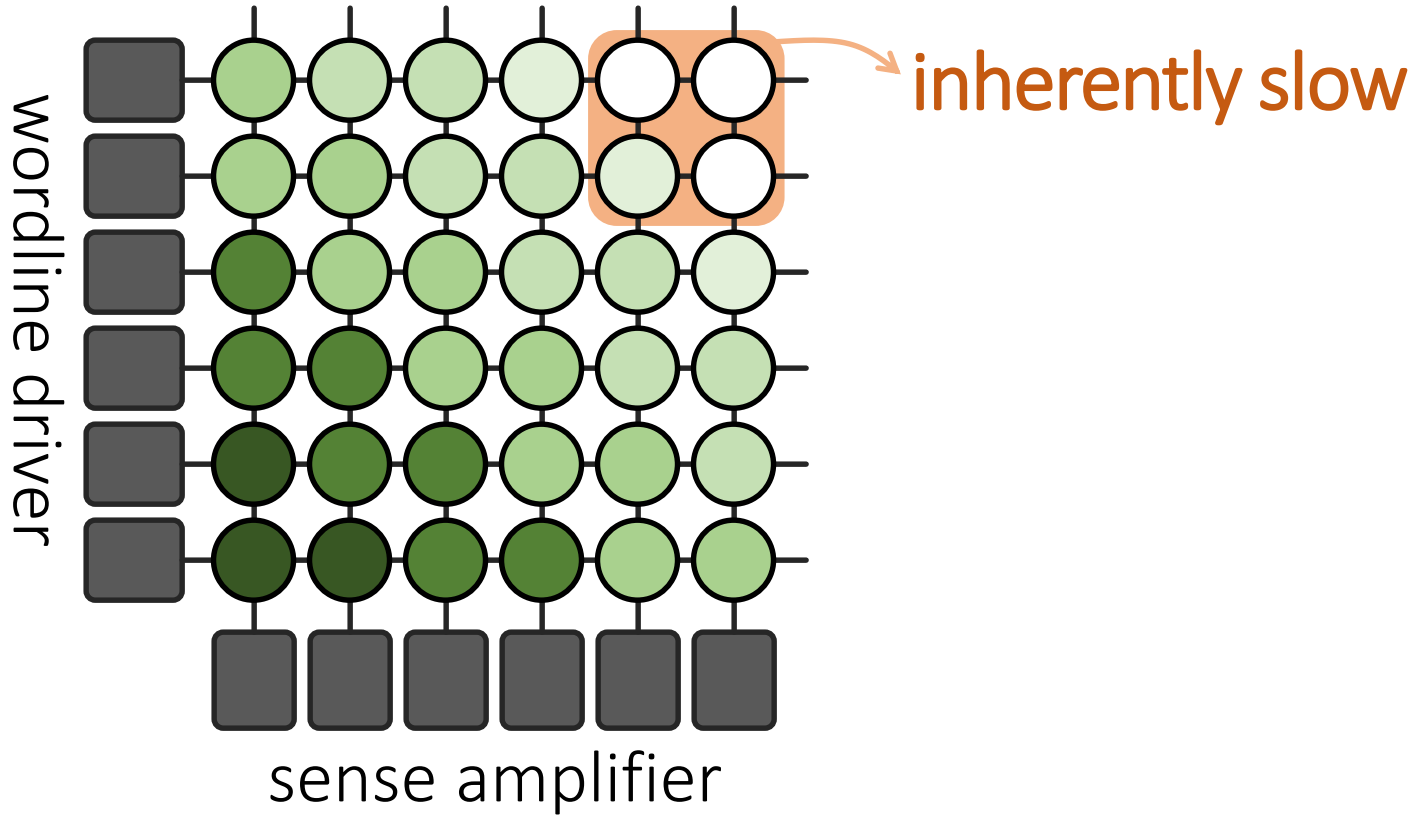
What Is Design-Induced Variation?



Systematic variation in cell access times caused by the ***physical organization*** of DRAM

DIVA Online **Profiling**

Design-**I**nduced-**V**ariation-**A**ware



Profile *only slow regions* to determine min. latency

→ *Dynamic* & *low cost* latency optimization

DIVA Online **Profiling**

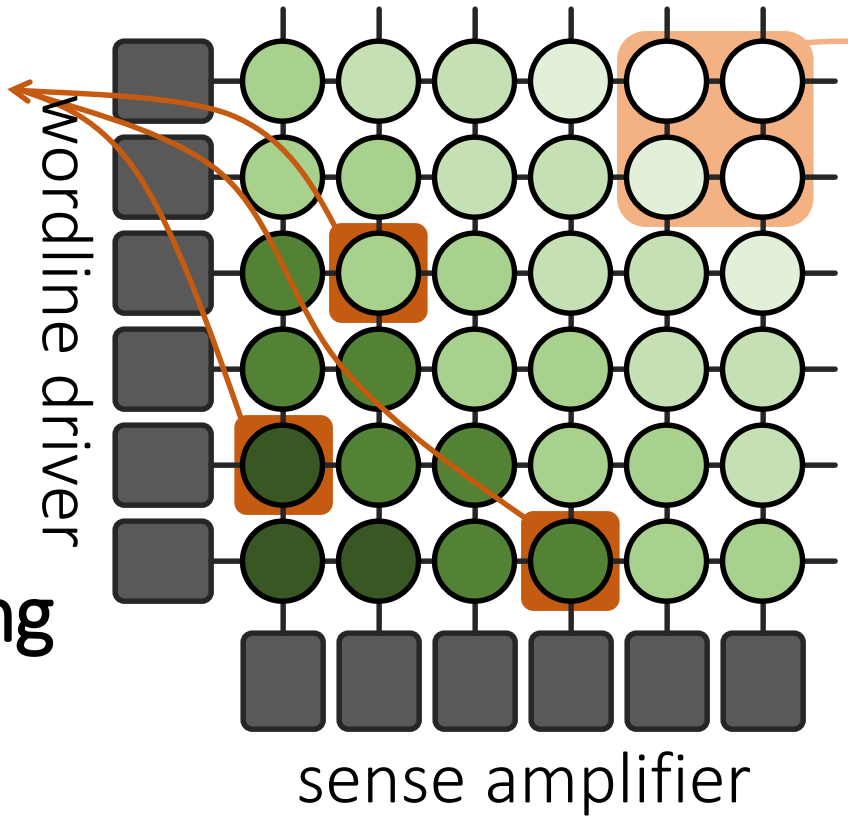
Design-**I**nduced-**V**ariation-**A**ware

slow cells

process variation

random error

error-correcting code



inherently slow

design-induced variation

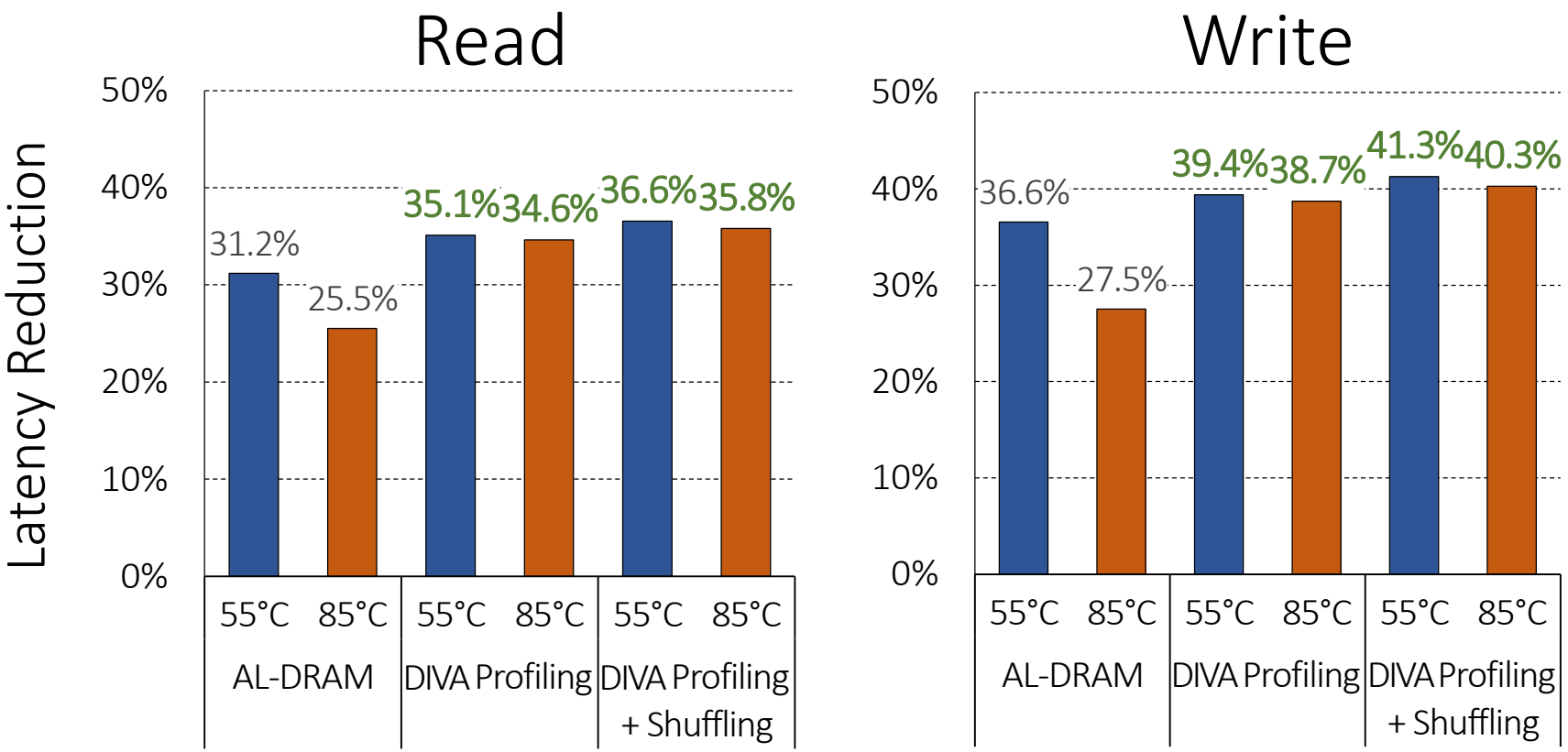
localized error

online profiling

Combine error-correcting codes & online profiling

→ Reliably reduce DRAM latency

DIVA-DRAM Reduces Latency



DIVA-DRAM ***reduces latency more aggressively*** and uses ECC to correct random slow cells

DIVA-DRAM: Advantages & Disadvantages

- Advantages

++ Automatically finds the lowest reliable operating latency at system runtime (lower production-time testing cost)

+ Reduces latency more than prior methods (w/ ECC)

+ Reduces latency at high temperatures as well

- Disadvantages

- Requires knowledge of inherently-slow regions

- Requires ECC (Error Correcting Codes)

- Imposes overhead during runtime profiling

Design-Induced Latency Variation in DRAM

- Donghyuk Lee, Samira Khan, Lavanya Subramanian, Saugata Ghose, Rachata Ausavarungnirun, Gennady Pekhimenko, Vivek Seshadri, and Onur Mutlu,
  "Design-Induced Latency Variation in Modern DRAM Chips: Characterization, Analysis, and Latency Reduction Mechanisms"
  *Proceedings of the ACM International Conference on Measurement and Modeling of Computer Systems (**SIGMETRICS**)*, Urbana-Champaign, IL, USA, June 2017.

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